

# INTERNATIONAL STANDARD



**Superconductivity –  
Part 7: Electronic characteristic measurements – Surface resistance of  
high-temperature superconductors at microwave frequencies**

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Part 7: Electronic characteristic measurements – Surface resistance of  
high-temperature superconductors at microwave frequencies**

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## CONTENTS

|                                                                                                                                        |    |
|----------------------------------------------------------------------------------------------------------------------------------------|----|
| FOREWORD .....                                                                                                                         | 5  |
| INTRODUCTION .....                                                                                                                     | 7  |
| 1 Scope .....                                                                                                                          | 8  |
| 2 Normative references .....                                                                                                           | 8  |
| 3 Terms and definitions .....                                                                                                          | 8  |
| 4 Requirements .....                                                                                                                   | 9  |
| 5 Apparatus .....                                                                                                                      | 9  |
| 5.1 Measurement system .....                                                                                                           | 9  |
| 5.2 Measurement apparatus for $R_S$ .....                                                                                              | 10 |
| 5.3 Dielectric rods .....                                                                                                              | 12 |
| 6 Measurement procedure .....                                                                                                          | 13 |
| 6.1 Specimen preparation .....                                                                                                         | 13 |
| 6.2 Set-up .....                                                                                                                       | 13 |
| 6.3 Measurement of reference level .....                                                                                               | 14 |
| 6.4 Measurement of the frequency response of resonators .....                                                                          | 14 |
| 6.5 Determination of surface resistance of the superconductor and $\varepsilon'$ and $\tan \delta$ of the standard sapphire rods ..... | 16 |
| 7 <del>Precision and accuracy</del> Uncertainty of the test method .....                                                               | 17 |
| 7.1 Surface resistance .....                                                                                                           | 17 |
| 7.2 Temperature .....                                                                                                                  | 18 |
| 7.3 Specimen and holder support structure .....                                                                                        | 19 |
| 7.4 Specimen protection .....                                                                                                          | 19 |
| 7.5 Uncertainty of surface resistance measured by standard two-resonator method .....                                                  | 19 |
| 8 Test report .....                                                                                                                    | 19 |
| 8.1 Identification of test specimen .....                                                                                              | 19 |
| 8.2 Report of $R_S$ values .....                                                                                                       | 19 |
| 8.3 Report of test conditions .....                                                                                                    | 20 |
| Annex A (informative) Additional information relating to Clauses 1 to 8 .....                                                          | 21 |
| A.1 Scope .....                                                                                                                        | 21 |
| A.1.1 General .....                                                                                                                    | 21 |
| A.1.2 Cylindrical cavity method [10] [17] .....                                                                                        | 21 |
| A.1.3 Parallel-plates resonator method [18] [19] .....                                                                                 | 21 |
| A.1.4 Microstrip-line resonance method [20] [21] .....                                                                                 | 21 |
| A.1.5 Dielectric resonator method [22] [23] [24] [25] .....                                                                            | 21 |
| A.1.6 Image-type dielectric resonator method [26] [27] .....                                                                           | 22 |
| A.1.7 Two-resonator method [28] [29] .....                                                                                             | 23 |
| A.2 Requirements .....                                                                                                                 | 23 |
| A.3 Theory and calculation equations .....                                                                                             | 23 |
| A.4 Apparatus .....                                                                                                                    | 27 |
| A.5 Dimensions of the standard sapphire rods .....                                                                                     | 27 |
| A.6 Dimension of the closed type resonator .....                                                                                       | 29 |
| <del>A.7 Precision and accuracy of the test method</del> .....                                                                         |    |
| A.7 Sapphire rod reproducibility .....                                                                                                 | 31 |
| A.8 Test results .....                                                                                                                 | 32 |

|                                                                                                                                                                                 |                                                                             |    |
|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------|----|
| A.9                                                                                                                                                                             | Reproducibility of measurement method .....                                 | 32 |
| A.10                                                                                                                                                                            | $\tan \delta$ deviation effect of sapphire rods on surface resistance ..... | 33 |
| Annex B (informative) Evaluation of relative combined standard uncertainty for surface resistance measurement .....                                                             |                                                                             | 36 |
| B.1                                                                                                                                                                             | Practical surface resistance measurement .....                              | 36 |
| B.2                                                                                                                                                                             | Determination of surface resistance of the superconductor .....             | 37 |
| B.3                                                                                                                                                                             | Combined standard uncertainty .....                                         | 38 |
| B.3.1                                                                                                                                                                           | General .....                                                               | 38 |
| B.3.2                                                                                                                                                                           | Calculation of $c_2$ to $c_5$ (12 GHz resonance at 20 K) .....              | 38 |
| B.3.3                                                                                                                                                                           | Determination of $u_1$ to $u_5$ .....                                       | 39 |
| B.3.4                                                                                                                                                                           | Combined relative standard uncertainty .....                                | 41 |
| Bibliography .....                                                                                                                                                              |                                                                             | 43 |
| Figure 1 – Schematic diagram of measurement system for temperature dependence of $R_s$ using a cryocooler .....                                                                 |                                                                             | 10 |
| Figure 2 – Typical measurement apparatus for $R_s$ .....                                                                                                                        |                                                                             | 11 |
| Figure 3 – Insertion attenuation, $IA$ , resonant frequency, $f_0$ , and half power bandwidth, $\Delta f$ , measured at $T$ kelvin .....                                        |                                                                             | 14 |
| Figure 4 – Reflection scattering parameters ( $S_{11}$ and $S_{22}$ ) .....                                                                                                     |                                                                             | 16 |
| Figure 5 – Term definitions in Table 4 .....                                                                                                                                    |                                                                             | 18 |
| Figure A.1 – Schematic configuration of several measurement methods for the surface resistance .....                                                                            |                                                                             | 22 |
| Figure A.2 – Configuration of a cylindrical dielectric rod resonator short-circuited at both ends by two parallel superconductor films deposited on dielectric substrates ..... |                                                                             | 24 |
| Figure A.3 – Computed results of the $u$ - $v$ and $W$ - $v$ relations for $TE_{01p}$ mode .....                                                                                |                                                                             | 25 |
| Figure A.4 – Configuration of standard dielectric rods for measurement of $R_s$ and $\tan \delta$ .....                                                                         |                                                                             | 26 |
| Figure A.5 – Three types of dielectric resonators .....                                                                                                                         |                                                                             | 27 |
| Figure A.6 – Mode chart to design $TE_{011}$ resonator short-circuited at both ends by parallel superconductor films [28] .....                                                 |                                                                             | 28 |
| Figure A.7 – Mode chart to design $TE_{013}$ resonator short-circuited at both ends by parallel superconductor films [28] .....                                                 |                                                                             | 29 |
| Figure A.8 – Mode chart for $TE_{011}$ closed-type resonator [28] .....                                                                                                         |                                                                             | 30 |
| Figure A.9 – Mode chart for $TE_{013}$ closed-type resonator [28] .....                                                                                                         |                                                                             | 31 |
| Figure A.10 – Temperature-dependent $R_s$ of YBCO film with a thickness of 500 nm and size of 25 mm square .....                                                                |                                                                             | 32 |
| Figure A.11 – Temperature dependent $R_s$ of YBCO film when $R_s$ was measured three times .....                                                                                |                                                                             | 33 |
| Figure B.1 – Schematic diagram of $TE_{011}$ and $TE_{013}$ mode resonance .....                                                                                                |                                                                             | 36 |
| Figure B.2 – Typical frequency characteristics of $TE_{011}$ mode resonance .....                                                                                               |                                                                             | 37 |
| Figure B.3 – Frequency characteristics of a resonator approximated by a Lorentz distribution .....                                                                              |                                                                             | 41 |
| Table 1 – Typical dimensions of pairs of <del>standard</del> single-crystal sapphire rods for 12 GHz, 18 GHz and 22 GHz .....                                                   |                                                                             | 12 |
| Table 2 – Dimensions of superconductor film for 12 GHz, 18 GHz, and 22 GHz .....                                                                                                |                                                                             | 13 |

|                                                                                                                 |    |
|-----------------------------------------------------------------------------------------------------------------|----|
| Table 3 – Specifications for vector network analyzer .....                                                      | 17 |
| Table 4 – Specifications for sapphire rods .....                                                                | 18 |
| Table A.1 – Standard deviation of the surface resistance calculated from the results of<br>Figure A.11 .....    | 33 |
| Table A.2 – Relationship between $x$ , defined by Equation (A.12), and $y$ , defined by<br>Equation (A.13)..... | 34 |

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## INTERNATIONAL ELECTROTECHNICAL COMMISSION

## SUPERCONDUCTIVITY –

**Part 7: Electronic characteristic measurements –  
Surface resistance of high-temperature  
superconductors at microwave frequencies**

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International Standard IEC 61788-7 has been prepared by IEC technical committee 90: Superconductivity.

This third edition cancels and replaces the second edition, published in 2006. This edition constitutes a technical revision.

This edition includes the following significant technical changes with respect to the previous edition:

- a) informative Annex B, relative combined standard uncertainty for surface resistance measurement has been added;
- b) precision and accuracy statements have been converted to uncertainty;
- c) reproducibility in surface resistant measurement has been added.

The text of this International Standard is based on the following documents:

| FDIS        | Report on voting |
|-------------|------------------|
| 90/447/FDIS | 90/452/RVD       |

Full information on the voting for the approval of this International Standard can be found in the report on voting indicated in the above table.

This document has been drafted in accordance with the ISO/IEC Directives, Part 2.

A list of all parts of the IEC 61788 series, published under the general title *Superconductivity*, can be found on the IEC website.

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## INTRODUCTION

Since the discovery of some Perovskite-type Cu-containing oxides, extensive research and development (R & D) work on high-temperature ~~oxide~~ superconductors (HTS) has been, and is being, done worldwide, and its application to high-field magnet machines, low-loss power transmission, electronics and many other technologies is in progress.

In various fields of electronics, especially in telecommunication fields, microwave passive devices such as filters using ~~oxide superconductors~~ HTS are being developed and are undergoing on-site testing [1][2]<sup>1</sup>.

Superconductor materials for microwave resonators [3], filters [4], antennas [5] and delay lines [6] have the advantage of very low loss characteristics. The parameters of superconductor materials needed for the design of microwave low loss components are the surface resistance, ( $R_s$ ) and the temperature dependence of the  $R_s$ . Knowledge of this parameter is of primary importance for the development of new materials on the supplier side and for the design of superconductor microwave components on the customer side.

~~Recent advances in high  $T_c$  superconductor (HTS) thin films with  $R_s$~~   $R_s$  of high quality HTS films is generally several orders of magnitude lower than that of normal metals [7] [8] [9] [10], ~~have~~ which has increased the need for a reliable characterization technique to measure this property [3,4]. Traditionally, the  $R_s$  of niobium or any other low-temperature superconducting material was measured by first fabricating an entire three-dimensional resonant cavity and then measuring its  $Q$ -value [11]. The  $R_s$  could be calculated by solving the electro-magnetic field (EM) distribution inside the cavity. Another technique involves placing a small sample inside a larger cavity. This technique has many forms but usually involves the uncertainty introduced by extracting the loss contribution due to the HTS films from the experimentally measured total loss of the cavity.

The best HTS samples are epitaxial films grown on flat crystalline substrates and no high-quality films have been grown on any curved surface so far. What is needed is a technique that: can use these small flat samples; requires no sample preparation; does not damage or change the film; is highly repeatable; has great sensitivity (down to 1/1 000 the  $R_s$  of copper); has great dynamic range (up to the  $R_s$  of copper); can reach high internal powers with only modest input powers; and has broad temperature coverage (4,2 K to 150 K).

The dielectric resonator method is selected among several methods ~~[5,6,7]~~ to determine the surface resistance at microwave frequencies because it is considered to be the most popular and practical at present. Especially, the sapphire resonator is an excellent tool for measuring the  $R_s$  of HTS materials ~~[8,9]~~ [12] [13] [14].

The test method given in this document can also be applied to other superconductor bulk plates including low  $T_c$  materials.

This document is intended to provide an appropriate and agreeable technical base for the time being to engineers working in the fields of electronics and superconductivity technology.

The test method covered in this document is based on the VAMAS (Versailles Project on Advanced Materials and Standards) pre-standardization work on the thin film properties of superconductors.

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<sup>1</sup> Numbers in square brackets refer to the bibliography.

## SUPERCONDUCTIVITY –

### Part 7: Electronic characteristic measurements – Surface resistance of **high-temperature** superconductors at microwave frequencies

#### 1 Scope

This part of IEC 61788 describes measurement of the surface resistance ( $R_s$ ) of superconductors at microwave frequencies by the standard two-resonator method. The object of measurement is the temperature dependence of  $R_s$  at the resonant frequency.

The applicable measurement range of  $R_s$  for this method is as follows:

- Frequency: 8 GHz <  $f$  < 30 GHz
- Measurement resolution: 0,01 mΩ at 10 GHz

The  $R_s$  data at the measured frequency, and that scaled to 10 GHz, assuming the  $f^2$  rule for comparison, is reported.

#### 2 Normative references

The following documents are referred to in the text in such a way that some or all of their content constitutes requirements of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

IEC 60050-815, *International Electrotechnical Vocabulary (IEV) – Part 815: Superconductivity*

#### 3 Terms and definitions

For the purposes of this document, the terms and definitions given in IEC 60050-815 apply.

ISO and IEC maintain terminological databases for use in standardization at the following addresses:

- IEC Electropedia: available at <http://www.electropedia.org/>
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~~In general, surface impedance  $Z_s$  for conductors, including superconductors, is defined as the ratio of the electric field  $E_t$  to the magnetic field  $H_t$ , tangential to a conductor surface:~~

$$\del{Z_s = E_t / H_t = R_s + jX_s}$$

~~where  $R_s$  is the surface resistance and  $X_s$  is the surface reactance.~~

## 4 Requirements

The  $R_s$  of a superconductor film shall be measured by applying a microwave signal to a dielectric resonator with the superconductor film specimen and then measuring the attenuation of the resonator at each frequency. The frequency shall be swept around the resonant frequency as the centre, and the attenuation–frequency characteristics shall be recorded to obtain the  $Q$ -value, which corresponds to the loss.

The target ~~precision~~ relative combined standard uncertainty of this method ~~is a coefficient of variation (standard deviation divided by the average of the surface resistance determinations) that~~ is less than 20 % for the measurement temperature range from ~~30~~ 20 K to 80 K.

It is the responsibility of the user of this document to ~~consult and~~ establish appropriate safety and health practices and to determine the applicability of regulatory limitations prior to use.

Hazards exist in this type of measurement. The use of a cryogenic system is essential to cool the superconductors to allow transition into the superconducting state. Direct contact of skin with cold apparatus components can cause immediate freezing, as can direct contact with a spilled cryogen. The use of an RF generator is also essential to measure high-frequency properties of materials. If its power is too high, direct contact to human bodies can cause an immediate burn.

## 5 Apparatus

### 5.1 Measurement system

Figure 1 shows a schematic diagram of the system required for the microwave measurement. The system consists of a network analyzer system for transmission measurement, a measurement apparatus, and a thermometer for monitoring the measuring temperature.

An incident power generated from a suitable microwave source such as a synthesized sweeper is applied to the dielectric resonator fixed in the measurement apparatus. The transmission characteristics are shown on the display of the network analyzer. ~~The measurement apparatus is fixed in a temperature-controlled cryocooler.~~

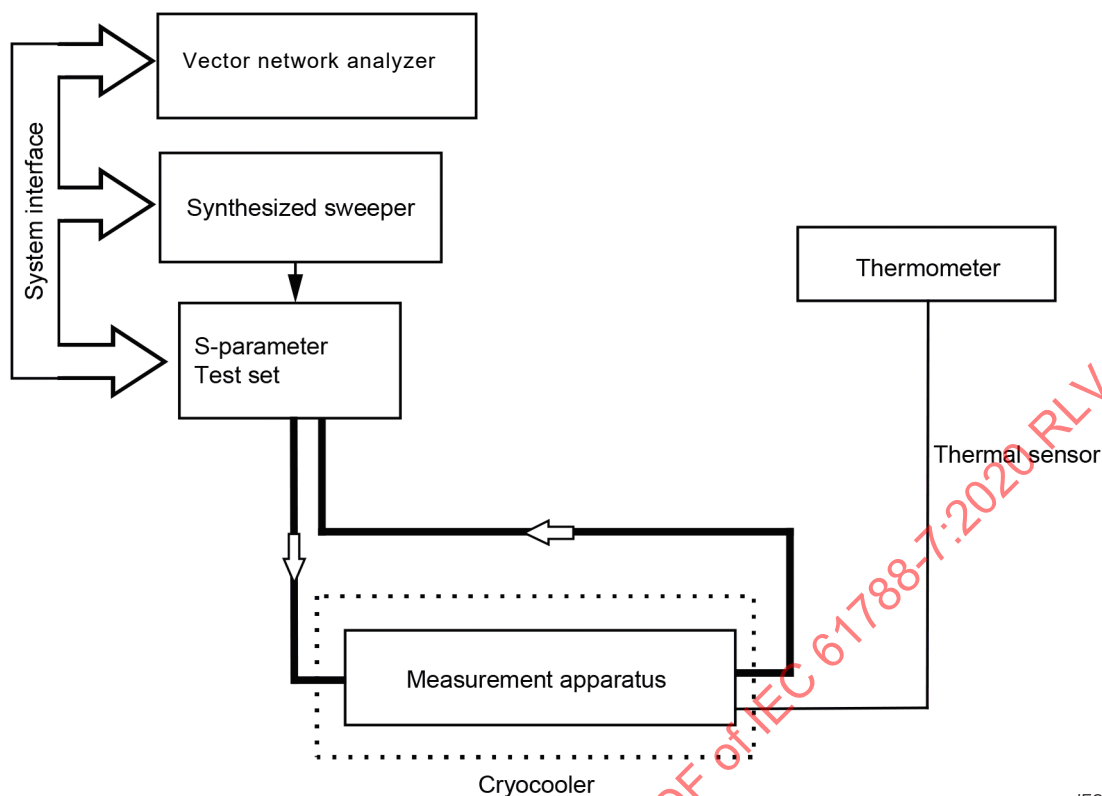


**Figure 1 – Schematic diagram of measurement system for temperature dependence of  $R_s$  using a cryocooler**

~~The measurement apparatus is fixed in a temperature-controlled cryocooler.~~

For the measurement of  $R_s$  for superconductor films, a vector network analyzer is recommended. A vector network analyzer has better measurement accuracy than a scalar network analyser due to its wide dynamic range. The performance requirements of the vector network analyzer are specified in 7.1.

## 5.2 Measurement apparatus for $R_s$

Figure 2 shows a schematic of a typical measurement apparatus (closed type resonator) for the  $R_s$  of ~~superconductor~~ HTS films deposited on a substrate with a flat surface. The upper ~~superconductor~~ HTS film is pressed down by a spring, which is made of phosphor bronze. The plate type spring ~~is recommended to~~ should be used for the improvement of measurement accuracy uncertainty. This type of spring reduces the friction between the spring and the other part of the apparatus, and allows the smooth movement of superconductor films due to the thermal expansion of the dielectric rod. In order to minimize the measurement ~~error~~ uncertainty, the sapphire rod and the copper ring shall be ~~set in coaxial~~ arranged coaxially.

Two semi-rigid cables for measuring transmission characteristics of the resonator shall be attached on both sides of the resonator in an axial symmetrical position ( $\phi = 0$  and  $\pi$ , where  $\phi$  is the rotational angle around the central axis of the sapphire rod). Each of the two semi-rigid cables shall have a small loop at the ends. The plane of the loop shall be set parallel to that of the superconductor films in order to suppress the unwanted Transverse Magnetic Wave Modes ( $TM_{mn0}$  modes). The coupling loops shall be carefully checked for cracks in the spot weld joint that may have developed upon repeated thermal cycling. These cables can move right and left to adjust the insertion attenuation ( $IA$ ). In this adjustment, coupling of unwanted cavity modes to the interested dielectric resonance mode shall be suppressed. Unwanted, parasitic coupling to the other modes reduces the high  $Q$ -value of the Transverse Electro-Magnetic Mode (TE mode) resonator. For suppressing the parasitic coupling, special attention shall be paid to

designing high- $Q$  resonators. Two other types of resonators along with the closed type shown in Figure 2 can be used. They are explained in A.4.

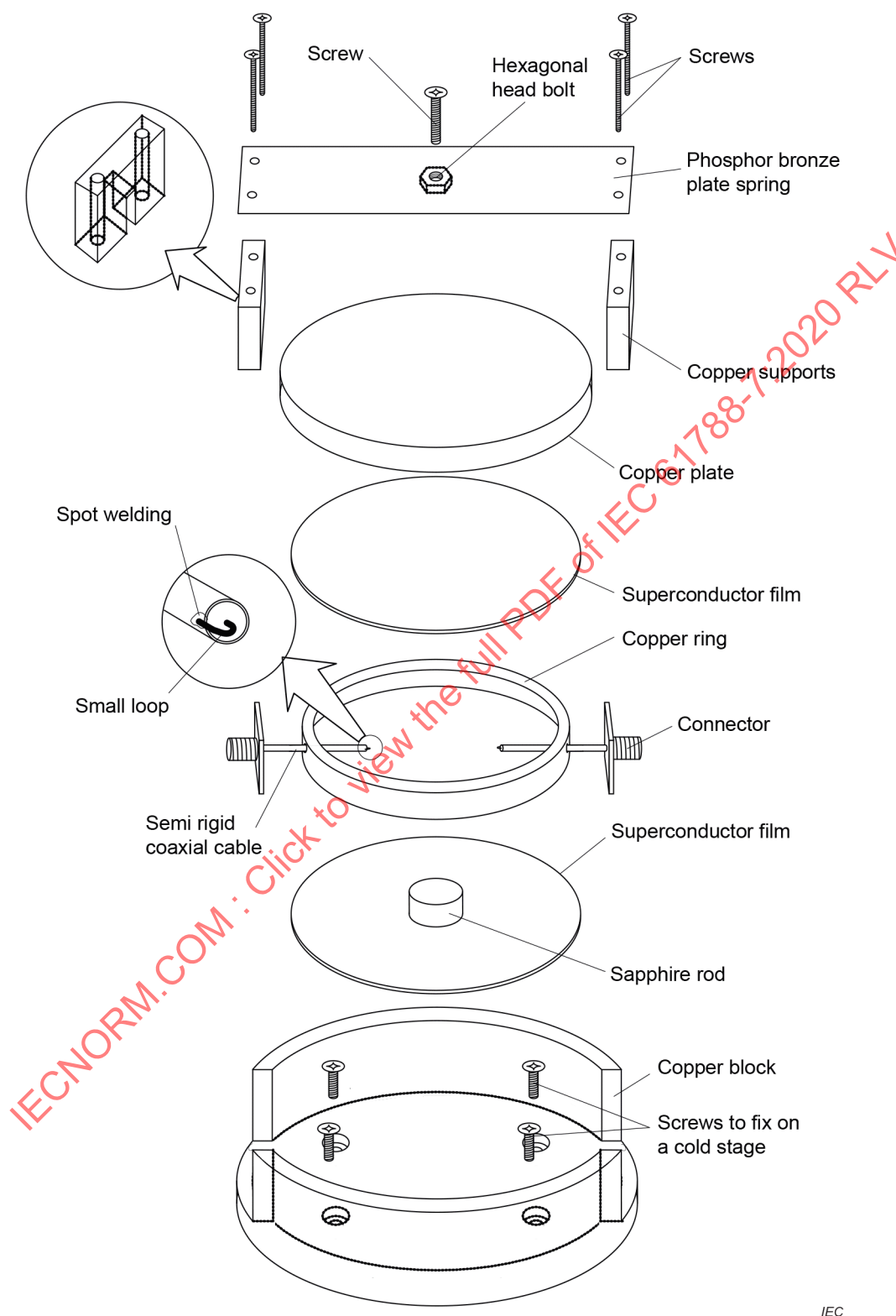


**Figure 2 – Typical measurement apparatus for  $R_s$**

A reference line made of a semi-rigid cable shall be used to measure the full transmission power level, i.e. the reference level. This cable has a length equal to the sum of the two cables of the measurement apparatus. Semi-rigid cable with an outer diameter of 1,20 mm is recommended.

In order to minimize the measurement ~~error~~ uncertainty, two superconductor films shall be set to be parallel to each other. To ensure that the two superconductor films remain in tight contact with the ends of the sapphire rod, without any air gap, both of the surfaces of the films and the ends of the rod shall be cleaned carefully.

### 5.3 Dielectric rods

Two dielectric rods with the same relative permittivity,  $\epsilon'$ , and loss factor,  $\tan \delta$ , preferably cut from one cylindrical dielectric rod, are required. These two rods, standard dielectric rods, shall have the same diameter but different heights: one ~~has a~~ shall have height three times longer than the other.

It is preferable to use ~~standard~~ dielectric rods with low  $\tan \delta$  to achieve the requisite measurement ~~accuracy~~ uncertainty on  $R_s$ . Recommended dielectric rods are single-crystal sapphire rods with  $\tan \delta$  less than  ~~$10^{-6}$~~   $2 \times 10^{-7}$  at 77 K. Specifications on the sapphire rods are described in 7.1. In order to minimize the measurement error in  $R_s$  of the superconductor films, both ends of the sapphire rods shall be polished parallel to each other and perpendicular to the axis. Specifications for the sapphire rods are given in Clause 7.

The diameter and the heights of the standard sapphire rods shall be carefully designed so that the  $TE_{011}$  and  $TE_{013}$  modes do not couple to other TM, HE and EH modes, since the coupling between TE mode and other modes causes the degradation of unloaded  $Q$ . A design guideline for the standard sapphire rods is described in Clause A.5. Table 1 shows typical examples of dimensions of the standard sapphire rods for 12 GHz, 18 GHz, and 22 GHz resonance. ~~At higher frequencies the unloaded  $Q$  value will be lower, which makes the measurement easier, and the error will be lower.~~ In the  $R_s$  measurement at 22 GHz, the required film diameter can be set to 20 mm, and the measured  $Q_L$  is small, therefore the effect of the dielectric loss of sapphire rod can be reduced.

**Table 1 – Typical dimensions of pairs of ~~standard~~ single-crystal sapphire rods for 12 GHz, 18 GHz and 22 GHz**

| Frequency<br>GHz |                                   | Diameter  | Height    |
|------------------|-----------------------------------|-----------|-----------|
|                  |                                   | $d$<br>mm | $h$<br>mm |
| 12               | Short rod ( $TE_{011}$ resonator) | 11,4      | 5,7       |
|                  | Long rod ( $TE_{013}$ resonator)  | 11,4      | 17,1      |
| 18               | Short rod ( $TE_{011}$ resonator) | 7,6       | 3,8       |
|                  | Long rod ( $TE_{013}$ resonator)  | 7,6       | 11,4      |
| 22               | Short rod ( $TE_{011}$ resonator) | 6,2       | 3,1       |
|                  | Long rod ( $TE_{013}$ resonator)  | 6,2       | 9,3       |

| Frequency<br>GHz |                                   | Diameter, $d$<br>mm | Height, $h$<br>mm |
|------------------|-----------------------------------|---------------------|-------------------|
| 12               | Short rod ( $TE_{011}$ resonator) | $11,40 \pm 0,05$    | $5,70 \pm 0,05$   |
|                  | Long rod ( $TE_{013}$ resonator)  | $11,40 \pm 0,05$    | $17,10 \pm 0,05$  |
| 18               | Short rod ( $TE_{011}$ resonator) | $7,60 \pm 0,05$     | $3,80 \pm 0,05$   |
|                  | Long rod ( $TE_{013}$ resonator)  | $7,60 \pm 0,05$     | $11,40 \pm 0,05$  |
| 22               | Short rod ( $TE_{011}$ resonator) | $6,20 \pm 0,05$     | $3,10 \pm 0,05$   |
|                  | Long rod ( $TE_{013}$ resonator)  | $6,20 \pm 0,05$     | $9,30 \pm 0,05$   |

## 6 Measurement procedure

### 6.1 Specimen preparation

From ~~error~~ uncertainty estimation, the film diameter shall be about three times larger than that of the sapphire rods. In this configuration, the ~~reduction~~ increase in ~~precision~~ uncertainty of  $R_s$  due to the different radiation losses between  $TE_{011}$  and  $TE_{013}$  mode can be considered negligible, given the target ~~precision~~ relative combined standard uncertainty of 20 %. The film thickness shall be about ~~three~~ two times larger than the ~~London~~ magnetic-field penetration depth value at ~~each~~ the maximum temperature in the measurement temperature range. If the film thickness is much less than ~~three~~ two times the ~~London~~ magnetic-field penetration depth, the measured  $R_s$  should mean the effective surface resistance.

Table 2 shows dimensions of the superconductor films recommended for the standard sapphire rods of 12 GHz, 18 GHz, and 22 GHz.

**Table 2 – Dimensions of superconductor film for 12 GHz, 18 GHz, and 22 GHz**

| Standard dielectric rod |           | Superconductor film |               |
|-------------------------|-----------|---------------------|---------------|
| Frequency               | Diameter  | Diameter            | Thickness     |
| GHz                     | $d$<br>mm | $d'$<br>mm          | $\mu\text{m}$ |
| 12                      | 11,4      | >35                 | $\approx 0,5$ |
| 18                      | 7,6       | >25                 | $\approx 0,5$ |
| 22                      | 6,2       | >20                 | $\approx 0,5$ |

| c-cut single-crystal sapphire rod |                  | Superconductor film |               |
|-----------------------------------|------------------|---------------------|---------------|
| Frequency                         | Diameter, $d$    | Diameter, $d'$      | Thickness     |
| GHz                               | mm               | mm                  | $\mu\text{m}$ |
| 12                                | $11,40 \pm 0,05$ | > 35                | $\approx 0,5$ |
| 18                                | $7,60 \pm 0,05$  | > 25                | $\approx 0,5$ |
| 22                                | $6,20 \pm 0,05$  | > 20                | $\approx 0,5$ |

In case of using closed type resonators, the dimensions of the superconductor films shall also be designed taking into account the dimension of the copper cylinder between the superconductor films. A design guideline for the dimension of the copper cylinder of the closed type resonator is described in Clause A.6.

### 6.2 Set-up

Set up the measurement equipment as shown in Figure 1. All of the measurement apparatus, standard sapphire rods, and superconductor films shall be kept in a clean and dry state as high humidity may degrade the unloaded  $Q$ -value. The specimen and the measurement apparatus shall be fixed in a temperature-controlled cryocooler. The specimen chamber shall be ~~generally~~ totally evacuated. The temperatures of the superconductor films and standard sapphire rods shall be measured by a diode thermometer, or a thermocouple. The temperatures of the upper and lower superconductor films and standard sapphire rods ~~must be kept as close as possible~~ shall not differ by more than 0,5 K. This can be achieved by covering the measurement apparatus with aluminium foil or filling the specimen chamber with helium gas.

### 6.3 Measurement of reference level

The level of full transmission power (reference level) shall be measured first. Fix the output power of the synthesized sweeper below 10 mW because the measurement ~~accuracy~~ **uncertainty** depends on the measuring signal level. Connect the reference line of semi-rigid cable between the input and output connectors. Then, measure the transmission power level over the entire measurement frequency and temperature range. The reference level can change several decibels when temperature of the apparatus is changed from room temperature to the lowest measurement temperature. Therefore, the temperature dependence of the reference level must be taken into account.

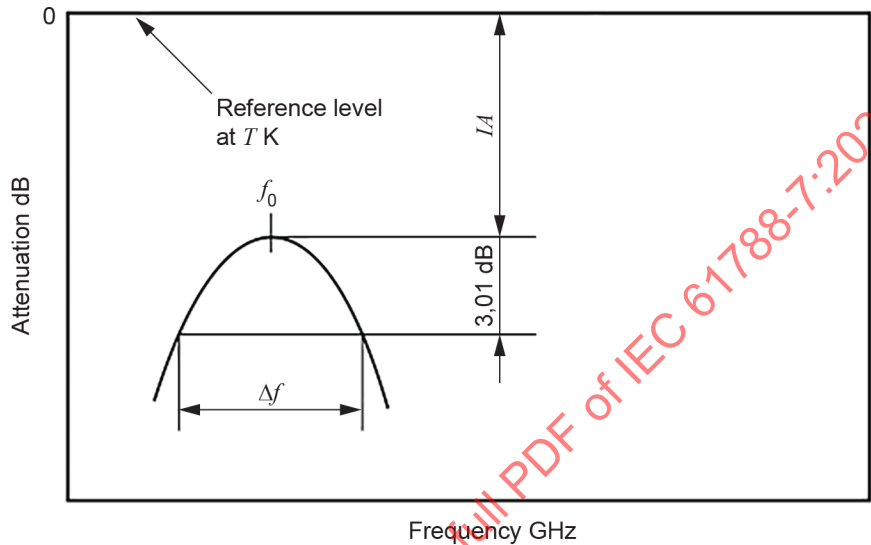


**Figure 3 – Insertion attenuation,  $IA$ , resonant frequency,  $f_0$ , and half power bandwidth,  $\Delta f$ , measured at  $T$  kelvin**

### 6.4 Measurement of the frequency response of resonators

The temperature dependence of the  $R_s$  can be obtained through the measurements of resonant frequency,  $f_0$ , and unloaded quality factor,  $Q_u$ , for  $TE_{011}$  and  $TE_{013}$  resonators, which shall be measured as follows.

- Connect the measurement apparatus between the input and output connectors (Figure 1). Insert the standard short sapphire rod near the centre of the lower superconductor film and fix the distance between the rod and each of the loops of the semi-rigid cables to be equal to each other, so that this transmission-type resonator can be under-coupled equally to both loops. Put down the upper superconductor film gently to touch the top face of the rod. Be careful not to damage the surface of the superconductor films by excessive pressure. Evacuate and cool down the specimen chamber below the critical temperature.
- Find the  $TE_{011}$  mode resonance peak of this resonator at a frequency nearly equal to the designed value of  $f_0$ .
- Narrow the frequency span on the display so that only the resonance peak of  $TE_{011}$  mode can be shown (Figure 3). Confirm that the insertion attenuation,  $IA$ , of this mode is larger than 20 dB from the reference level, which depends strongly on the temperature.
- Measure the temperature dependence of  $f_0$  and the half power band width  $\Delta f$ . The loaded  **$Q$ -value**,  $Q_L$ , of the  $TE_{011}$  resonator is given by

$$Q_L = \frac{f_0}{\Delta f} \quad (1)$$

- e) The unloaded  $Q$ -value,  $Q_u$ , shall be extracted from the  $Q_L$  by at least one of the two following techniques.

- 1) One technique for extracting the unloaded  $Q$ -value involves measuring the insertion attenuation  $IA$ .  $Q_u$  is given by

$$Q_u = \frac{Q_L}{1 - A_t}, A_t = 10^{-IA[\text{dB}]/20} \quad (2)$$

The  $IA$  of each temperature is determined as follows. In the  $R_s$  measurement system shown in Figure 2, a semi-rigid cable is connected instead of the measurement apparatus, and the measurement system is short-circuited to determine the reference level. Measure the reference level at each temperature and use it to determine  $IA$  at each temperature.

This technique of using insertion attenuation assumes that the coupling on both sides of the resonator is identical. The coupling loops are difficult to fabricate, the orientation of the loop is difficult to control, and any movement of the sapphire rod during measurement is not known. These assembly-dependent effects are also temperature dependent. This potential asymmetry in coupling can result in large errors in calculating the coupling factor if the coupling is strong ( $IA < 10$  dB). If the coupling is weak enough ( $IA > 20$  dB), asymmetry in the coupling becomes less important.

- 2) Another technique for extracting the unloaded  $Q$ -value involves measuring the reflection scattering parameters at the resonant frequency of both sides of the resonator.

$$Q_u = Q_L (1 + \beta_1 + \beta_2) \quad (3)$$

$$\beta_1 = \frac{1 - |S_{11}|}{|S_{11}| + |S_{22}|} \quad (4)$$

$$\beta_2 = \frac{1 - |S_{22}|}{|S_{11}| + |S_{22}|} \quad (5)$$

In the above equations Equations (4) and (5),  $S_{11}$  and  $S_{22}$  are the reflection scattering parameters as shown in Figure 4, and are measured in linear units of power, not relative dB.  $\beta_1$  and  $\beta_2$  are the coupling coefficients.

This technique of using the reflection scattering parameters has two advantages. It does not require the additional step of calibration of the reference level and it gives a measurement of the coupling values for both sides of the resonator. This also has two disadvantages. It only works for a narrow band resonance (which is fortunately the case) and is limited by the dynamic range of the network analyzer in measuring the reflection coefficients [15] [16].

A combination of the two techniques is ~~an excellent "double" check and is therefore recommended~~ useful for a "double" check.

- f) The  $f_0$  and  $Q_u$  measured for this short rod are denoted as  $f_{01}$  and  $Q_{u1}$  for  $TE_{011}$  mode resonance. By slowly changing the temperature of the cryocooler the temperature dependence of  $f_{01}$  and  $Q_{u1}$  shall be measured.
- g) After the temperature dependence measurement of  $f_{01}$  and  $Q_{u1}$  is finished, the measurement apparatus shall be heated up to room temperature.
- h) Then, replace the  $TE_{011}$  resonator in the apparatus with the  $TE_{013}$  resonator at room temperature, cool down the apparatus to a temperature lower than the critical temperature, and measure the temperature dependence of  $f_0$  and  $Q_u$  of its  $TE_{013}$  resonance mode, denoted as  $f_{03}$  and  $Q_{u3}$ , in a similar way to the  $TE_{011}$  resonator case. When the length of

the sapphire rod of the TE<sub>013</sub> resonator is precisely three times longer than that of the TE<sub>011</sub> resonator, the  $f_{03}$  of the TE<sub>013</sub> resonator must coincide with  $f_{01}$  of the TE<sub>011</sub> resonator. If carefully designed, the difference between  $f_{01}$  and  $f_{03}$  is usually very small ( $\sim 0,25\%$ ). We can ~~treat as  $f_0 = f_{01} = f_{03}$  in the calculations of 6.5~~ consider that the  $f_0$  in equation (9) can be replaced by  $f_{01}$  or  $f_{03}$ .

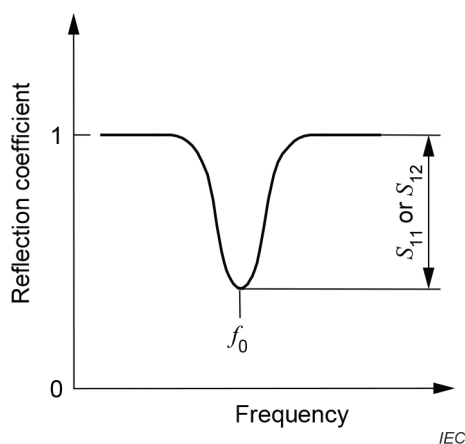


Figure 4 – Reflection scattering parameters ( $S_{11}$  and  $S_{22}$ )

#### 6.5 Determination of surface resistance of the superconductor and $\varepsilon'$ and $\tan \delta$ of the standard sapphire rods

~~Calculate the temperature dependence of the surface resistance  $R_s$  of the superconductor films, and  $\varepsilon'$  and  $\tan \delta$  of the standard sapphire rods using the temperature dependence of  $f_{01}$ ,  $Q_{u1}$ ,  $f_{03}$ , and  $Q_{u3}$  from Equations (6), (7) and (8).~~

Calculate the temperature dependence of the  $R_s$  of the superconductor films, and  $\varepsilon'$  and  $\tan \delta$  of the standard sapphire rods using the temperature dependence of  $Q_{u1}$  and  $Q_{u3}$ .  $Q_{u1}$  and  $Q_{u3}$  can be calculated using equations (1) and (2). If the measured temperatures for  $Q_{u3}$  appear to be slightly different from those for  $Q_{u1}$ , interpolation can be used for preparing adjusted temperature values for the former at the same temperatures for the later. Equations (6) to (12) are established in the open type cavity, but when the superconductor film size is three times larger than sapphire rod diameter, these equations can be used for closed type cavity.

$$R_s = \frac{30\pi^2 \times 3}{(3-1)} \left( \frac{2h_0}{\lambda_0} \right)^3 \frac{\varepsilon' + W}{1+W} \left( \frac{1}{Q_{u1}} - \frac{1}{Q_{u3}} \right) \quad (6)$$

$$\varepsilon' = \left( \frac{\lambda_0}{\pi d} \right)^2 (u^2 + v^2) + 1 \quad (7)$$

$$\tan \delta = \frac{1 + \frac{W}{\varepsilon'}}{(3-1)} \left( \frac{3}{Q_{u3}} - \frac{1}{Q_{u1}} \right) \quad (8)$$

where

$$\lambda_0 = \frac{c}{f_0} \quad (9)$$

$$W = \frac{J_1^2(u) K_0(v) K_2(v) - K_1^2(v)}{K_1^2(v) J_1^2(u) - J_0(u) J_2(u)} \quad (10)$$

$$v^2 = \left( \frac{\pi d}{\lambda_0} \right)^2 \left[ \left( \frac{\lambda_0}{2h_0} \right)^2 - 1 \right] \quad (11)$$

$$v^2 = \left( \frac{\pi d}{\lambda_0} \right)^2 \left[ \left( \frac{3\lambda_0}{2h_0} \right)^2 - 1 \right] \quad (11)$$

$$u \frac{J_0(u)}{J_1(u)} = -v \frac{K_0(v)}{K_1(v)} \quad (12)$$

In the equations,  $\lambda_0$  is the free space resonant wavelength,  $c$  is the ~~velocity~~ speed of light in vacuum ( $c = 2,997\,9 \times 10^8$  m/s),  $h_0$  is the height of the short standard dielectric rod. The value  $u^2$  is given by the transcendental Equation (12) using the value of  $v^2$ , where  $J_n(u)$  is the Bessel function of the first kind, and  $K_n(v)$  is the modified Bessel function of the second kind. The derivations of the equations are described in Clause A.3.

Generally the thermal expansion coefficient of the rods must be known to determine the temperature dependence of their sizes. However, the thermal expansion effect of the sapphire rods can be neglected for the target ~~precision of the~~ relative standard uncertainty of  $R_s$  (20 %).

It is noted that the measured  $R_s$  means the effective surface resistance if the film thickness is ~~not much larger~~ less than two times the temperature-dependent penetration depth.

## 7 ~~Precision and accuracy~~ Uncertainty of the test method

### 7.1 Surface resistance

The surface resistance ( $R_s$ ) shall be determined from the  $Q$ -value measured with a dielectric resonator technique.

A vector network analyser as specified in Table 3 shall be used to record the frequency dependence of attenuation. The resulting record shall allow the determination of  $Q$  to a relative uncertainty of  $10^{-2}$ .

**Table 3 – Specifications for vector network analyzer**

|                           |              |
|---------------------------|--------------|
| Dynamic range of $S_{21}$ | above 60 dB  |
| Frequency resolution      | below 1 Hz   |
| Attenuation uncertainty   | below 0,1 dB |
| Input power limitation    | below 10 dBm |

The dielectric resonators shall be provided with two dielectric rods with low  $\tan \delta$  of less than  $10^{-6}$   $2 \times 10^{-7}$  at 77 K and a radius less than 1/3 of the superconducting specimen's radius. The best candidate for the rods is sapphire as specified in Table 4. Term definitions in Table 4 are shown in Figure 5.

**Table 4 – Specifications for sapphire rods**

|                   |                                                                                    |
|-------------------|------------------------------------------------------------------------------------|
| Diameter          | $\pm 0,05$ mm                                                                      |
| Height            | $\pm 0,05$ mm                                                                      |
| Flatness          | below 0,005 mm                                                                     |
| Surface roughness | top and bottom surface: below 10 nm RMS<br>cylindrical surface: below 0,001 mm RMS |
| Perpendicularity  | within 0,1 degree                                                                  |
| Axis              | parallel to c-axis within 0,3°                                                     |

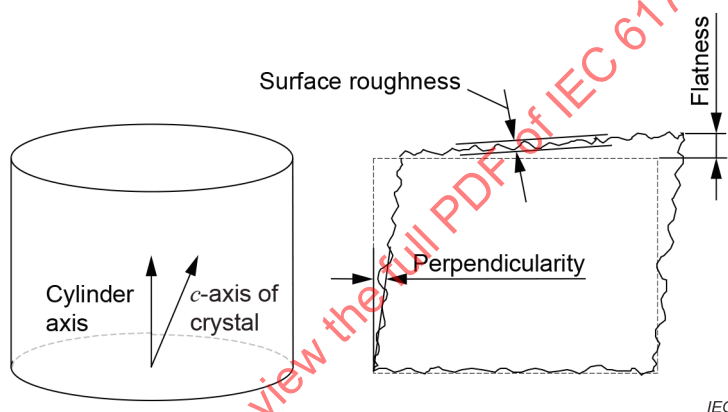


**Figure 5 – Term definitions in Table 4**

The technique as described assumes that single- and triple-height sapphire rods can be fabricated with the same  $\tan \delta$ . However, the variation of the  $\tan \delta$  between nominally identical rods, cut from the same boule and polished by the same technique, may be as large as two orders of magnitude. To date, the smallest variation in  $\tan \delta$  between nominally identical sapphire rods has been a factor of four [9]. Therefore, the uncertainty in the measured  $\tan \delta$  is large. The variation of  $\tan \delta$  of the present sapphire rod causes an additional uncertainty up to at least 10 % in the surface resistance measurement. This limits the target ~~precision~~ uncertainty of the present technique at ~~20~~ 5 %. If reproducibility of sapphire rods is improved, or a selection method for standard sapphire rods is established, a target ~~precision~~ uncertainty can be improved.

## 7.2 Temperature

The measurement apparatus is cooled down to the specified temperature by any means during testing. An easy choice would be to immerse the apparatus into a liquid cryogen. This technique is quick and simple and yields a known and stable temperature. Unfortunately, most HTS materials are damaged by the condensation of moisture that occurs when removing the sample from the cryogen. In addition, uncertainties generated by the presence of a gas/liquid mixture within the cavity, and the inability to measure  $R_s$  as a function of temperature support the use of other cooling methods. These limitations can be circumvented by the immersion of a vacuum can into a liquid cryogen. If the vacuum can is backfilled with gas, then rapid cooling and uniform temperatures occur. If heaters are attached to the apparatus, then the temperature dependence of the HTS material can be measured. A third and equally good choice is the use of a cryocooler. In this case, the resonator is under vacuum and cooled by conduction through the metallic

package. ~~Care must be taken to avoid~~ Temperature gradients with the apparatus shall be avoided.

A cryostat shall be provided with the necessary environment for measuring  $R_s$  and the specimen shall be measured while in a stable and isothermal state. The specimen temperature is assumed to be the same as the sample holder temperature. The holder temperature shall be reported to an accuracy of  $\pm 0,5$  K, measured by means of an appropriate temperature sensor.

The difference between the specimen temperature and the holder temperature shall be minimized by using shields with good thermal conductivity.

### 7.3 Specimen and holder support structure

The support structure shall provide adequate support for the specimen. ~~It is imperative that~~ The two films shall be parallel and mechanically stable throughout the measurement, especially in a cryocooler and over a wide temperature range. The parallelism of the two films can be achieved by using a sapphire rod satisfying the specifications described in Table 4.

### 7.4 Specimen protection

Condensation of moisture and scratching of the film deteriorate superconducting properties. Some protection measures should be provided for the specimens. Polytetrafluoroethylene (PTFE) or polymethylmethacrylate (PMMA) coating does not affect the measurements, thus they can be used for protection. A coating material thickness of less than several micrometers is recommended.

### 7.5 Uncertainty of surface resistance measured by standard two-resonator method

For the dielectric resonance method,  $\tan \delta$  of the  $TE_{011}$  mode and  $TE_{013}$  mode sapphire rods are assumed to be absolutely equal. If  $\tan \delta$  of two sapphire rods is different, it is not possible to calculate the surface resistance using Equation (6). The effect of  $\tan \delta$  deviation on surface resistance was checked (see Annex B). Uncertainty in the microwave surface resistance of superconductors by dielectric resonator method depends on size, dielectric constant,  $\tan \delta$  of sapphire rods and uncertainty in measured  $Q$  of the resonator. The relative combined standard uncertainty is less than 20 % (see Annex B)

## 8 Test report

### 8.1 Identification of test specimen

The test specimen shall be identified, if possible, by the following:

- name of the manufacturer of the specimen;
- classification and/or symbol;
- lot number;
- chemical composition of the thin film and the substrate;
- thickness and roughness of the thin film;
- manufacturing process technique.

### 8.2 Report of $R_s$ values

The  $R_s$  values at the measured frequency, and that scaled to 10 GHz, together with their corresponding  $f_{01}$ ,  $f_{03}$ ,  $Q_{u1}$ ,  $Q_{u3}$ ,  $IA$  and/or  $(\beta_1, \beta_2)$ ,  $\epsilon'$  and  $\tan \delta$  values, and their temperature dependence shall be reported.

### 8.3 Report of test conditions

The following test conditions shall be reported:

- a) test frequency and resolution of frequency;
- b) test maximum RF power;
- c) test temperature, accuracy of temperature and temperature difference in two plates;
- d) sample history with temperature variation.

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## Annex A (informative)

### Additional information relating to Clauses 1 to 8

#### A.1 Scope

##### A.1.1 General

The establishment of the standard measurement method is needed to evaluate film quality of ~~high-Tc superconductor (HTS)~~ films having low surface resistance,  $R_s$ , values such as 0,1 mΩ at 10 GHz. Several resonance methods as shown in Figure A.1 have been proposed so far to measure them in microwave and millimetre wave range. These resonator structures are grouped into six types (see A.1.2 to A.1.7).

##### A.1.2 Cylindrical cavity method ~~[4]<sup>2)</sup>~~ [10] [17]

Figure A.1 a) shows a cavity structure using the  $TE_{011}$  mode, which is constructed from a copper cylinder and two HTS films. In the microwave range below 30 GHz, the  $R_s$  measurement precision of this method is rather low, because the  $R_s$  value of the copper cylinder is 100 times higher than that of HTS films. This method is suitable in the millimetre wave region, because the  $R_s$  values increase with  $f^2$  of HTS films and  $f^{1/2}$  for copper.

##### A.1.3 Parallel-plates resonator method ~~[2]~~ [18] [19]

Figure A.1 b) shows a structure of a parallel-plates resonator using the  $TM_{nm0}$  mode, which is constructed by inserting a thin low loss dielectric spacer between two rectangular HTS films. This method offers the possibility of measuring extremely small  $R_s$  values, but from the viewpoint of the absolute estimation of  $R_s$  there are some problems, such as low measurement precision of thickness and  $\tan \delta$  of the dielectric spacer, uncertain estimations of radiation loss and an air-gap effect between the plates and the spacer, and critical excitation technique of the resonance modes.

##### A.1.4 Microstrip-line resonance method ~~[4], [3]~~ [20] [21]

Figure A.1 (c) shows a structure of a microstrip-line resonator using the  ~~$TEM_n$~~   $TE_{0mp}$  mode, which is fabricated by a pattern fabrication process and is close to the real microwave passive devices. However, this method is not suitable for the HTS film estimation because it includes an uncertain influence of the pattern fabrication process.

##### A.1.5 Dielectric resonator method ~~[4], [5] [7]~~ [22] [23] [24] [25]

Figure A.1 d) shows a structure of a dielectric resonator using a  $TE_{011}$  mode, where a low loss sapphire rod is placed between two parallel HTS films. For the  $TE_{0mp}$  mode, we can eliminate the air-gap effects, because the normal component of electric field does not exist on the HTS films. In this method the  $R_s$  values of the HTS films have been measured by ignoring the effect of  $\tan \delta$  on the assumption of  $\tan \delta < 1 \times 10^{-8}$  for single-crystal sapphire ~~[4]~~ [24]. However, the  $\tan \delta$  values measured for sapphire at 10 GHz and near 50 K, as is well known, take values between  $10^{-6}$  to  $10^{-8}$  due to quantity of lattice defect. Therefore, preparation of very-low-loss sapphire rods with  $\tan \delta < 1 \times 10^{-8} < 2 \times 10^{-7}$  (at 80 K and at 10 GHz) is essential for this method.

<sup>2)</sup> Numbers in brackets in this annex refer to the reference documents in Clause A.9

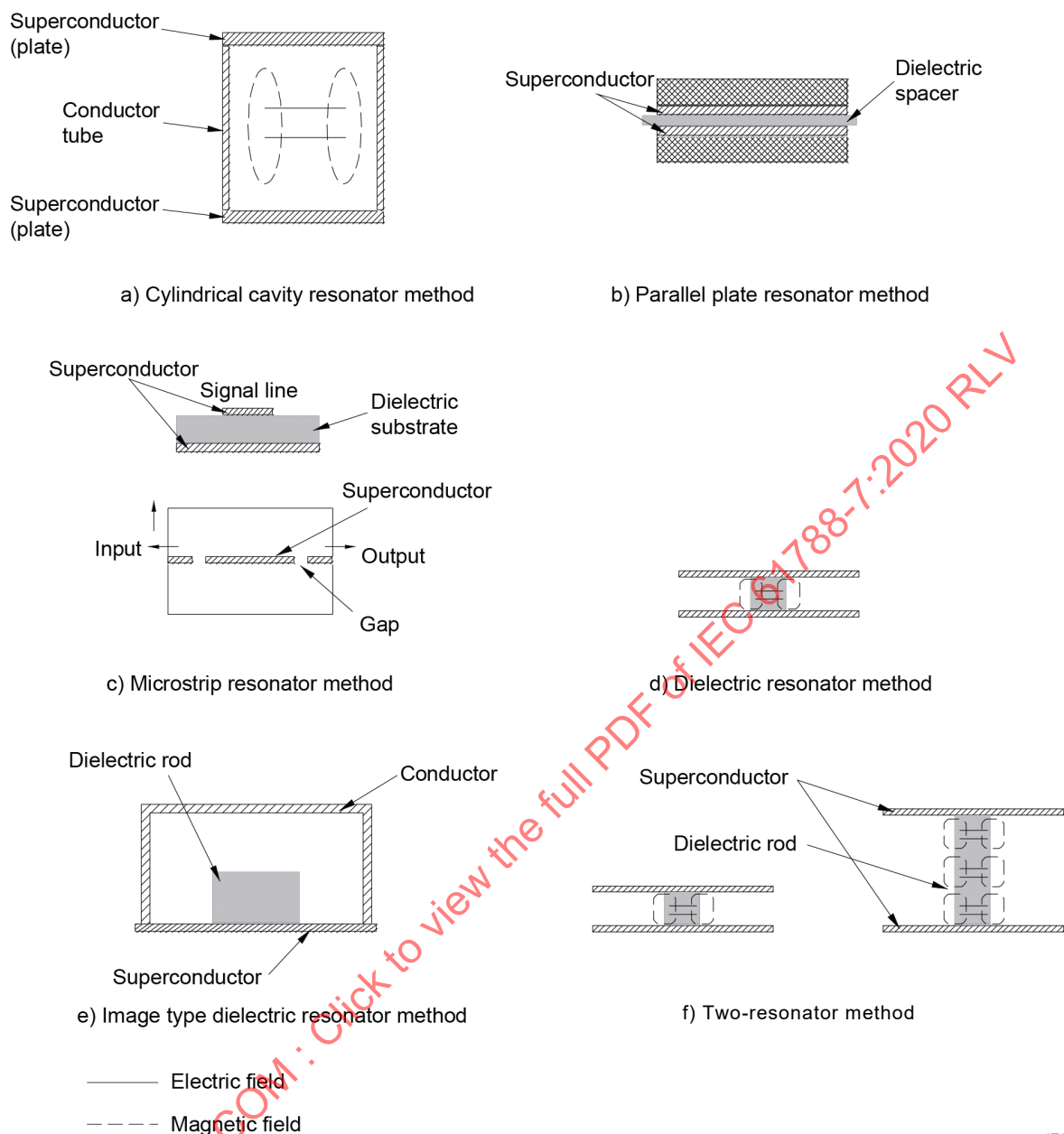


**Figure A.1 – Schematic configuration of several measurement methods for the surface resistance**

#### A.1.6 Image-type dielectric resonator method [8] [26] [27]

Figure A.1 e) shows a structure of an image-type dielectric resonator using the  $TE_{01\delta}$  mode. This structure is available to measure only one HTS film. However, preparation of very-low-loss sapphire rods is essential also for this method, because the  $R_s$  is measured by ignoring the effect of  $\tan \delta$ .

~~In addition, complicated and tedious numerical calculations are needed to determine the  $R_s$  values from the measured resonant frequency and unloaded  $Q$ .~~

In an improved image-type sapphire rod resonator method,  $R_s$  can be obtained with simple calibration process. In this method, the exact  $R_s$  of a single HTS film can be obtained by one measurement under the 20 % limitation of variation coefficient.

#### A.1.7 Two-resonator method [9], [10] [28] [29]

In this method, two sapphire rod resonators with the same  $\tan \delta$  values are used; one is a  $TE_{011}$  mode resonator and the other is a  $TE_{013}$  mode resonator, as shown in Figure A.1 f). Similarly to the dielectric resonator method, the air-gap effects can be eliminated in this method. The  $\tan \delta$  value of the sapphire rods and the  $R_s$  value of the HTS films can be determined separately from the resonant frequencies and unloaded  $Q$ -values measured for these resonators by using simple formulas derived from the rigorous analysis based on the mode matching method. Thus this method can eliminate the ambiguity of the  $\tan \delta$  affected to the  $R_s$  measurements. Actually, the results of  $R_s$  measured for six YBCO films with  $R_s = 0,1 \text{ m}\Omega$  at 12 GHz have verified that the measurement precision uncertainty of  $\pm 20 \%$  is realized by this method [10] [22]. However, if there is a difference between two  $\tan \delta$  values ( $\Delta \tan \delta$ ), the errors of uncertainty in  $R_s$  due to  $\Delta \tan \delta$  must be taken into account. This effect will can be estimated from results of the inter-laboratory round robin test of the same HTS films by this method. Recently, the  $R_s$  of YBCO film was measured three times and its deviation was less than 20 % (see Figure A.11).

As a result of comparisons among the six methods described above, the two-resonator method is recommended as the standard measurement method of  $R_s$  of HTS films, due to the following two advantages:

- absolute measurement of  $R_s$  is possible;
- the numerical treatment is simple and easy.

### A.2 Requirements

Higher measurement frequencies are desirable for determination of lower  $R_s$  because  $R_s$  of superconductor films increases with the frequency according to the  $f^2$  rule. The size of the resonators also can be made smaller by using higher measurement frequencies. However, it becomes difficult to set up a microwave measurement system as the measurement frequency becomes higher.

For the measurement temperatures of below  $\sim 10 \text{ K}$  or above  $80 \text{ K}$ , this test method is sufficiently applicable, where some new cooling techniques may be required.

### A.3 Theory and calculation equations

Figure A.2 shows the configuration of the  $TE_{0mp} TE_{0mn}$  mode resonator, which is used to eliminate the air-gap effects. A cylindrical dielectric rod with diameter,  $d$ , and height,  $h$ , is short-circuited at both ends by surfaces of two parallel superconductor films deposited on dielectric substrates with diameter,  $d'$ , thus constituting a resonator. These superconductor films are required to have the same value of  $R_s$ . The value of  $R_s$  is calculated from the measured resonant frequency  $f_0$  and unloaded quality factor  $Q_u$  for the  $TE_{0mp} TE_{0mn}$  resonance mode. When the two superconductor films have different values of  $R_s$ , the measured  $R_s$  value corresponds to the average value of these two films.

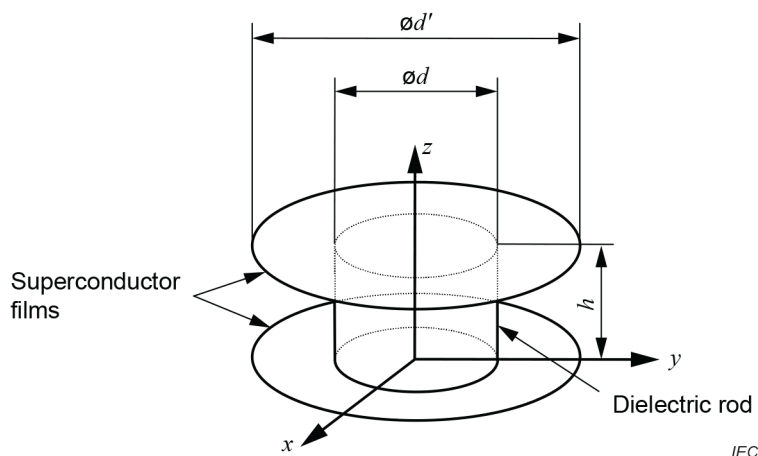


**Figure A.2 – Configuration of a cylindrical dielectric rod resonator short-circuited at both ends by two parallel superconductor films deposited on dielectric substrates**

The value of  $R_s$  is given by [25]

$$R_s = \frac{1}{B} \left( \frac{A}{Q_u} - \tan \delta \right) \quad (\text{A.1})$$

where

$$A = 1 + \frac{W}{\varepsilon'} \quad (\text{A.2})$$

$$B = p^2 \left( \frac{\lambda_0}{2h} \right)^3 \frac{1+W}{30\pi^2 \varepsilon'}, p = 1, 2, \dots, \quad (\text{A.3})$$

$$\lambda_0 = \frac{c}{f_0} \quad (\text{A.4})$$

$$W = \frac{J_1^2(u) K_0(v) K_2(v) - K_1^2(v)}{K_1^2(v) J_1^2(u) - J_0(u) J_2(u)} \quad (\text{A.5})$$

$$v^2 = \left( \frac{\pi d}{\lambda_0} \right)^2 \left[ \left( \frac{p \lambda_0}{2h} \right)^2 - 1 \right] \quad (\text{A.6})$$

$$v^2 = \left( \frac{\pi d}{\lambda_0} \right)^2 \left[ \left( \frac{3 \lambda_0}{2h} \right)^2 - 1 \right] \quad (\text{A.6})$$

$$u \frac{J_0(u)}{J_1(u)} = -v \frac{K_0(v)}{K_1(v)} \quad (\text{A.7})$$

In Equations (A.1) and (A.2),  $\varepsilon'$  and  $\tan \delta$  are the relative permittivity and the loss factor of the dielectric rod, respectively. In Equations (A.3) and (A.4),  $\lambda_0$  is the free space resonant wavelength, and  $c$  is the ~~velocity~~ speed of light in vacuum ( $c = 2,9979 \times 10^8$  m/s). The function  $W/\varepsilon'$  equals the ratio of electric-field energy stored outside to that stored inside the dielectric rod. If all of the electric field is concentrated inside the dielectric rod, the value  $W$  equals zero.

The value  $u^2$  is given by the transcendental Equation (A.7) using the value of  $v^2$ , where  $J_n(u)$  is the Bessel function of the first kind and  $K_n(v)$  is the modified Bessel function of the second kind, ~~respectively~~. For any value of  $v$ , the  $m$ -th solution  $u$  exists between  $u_{0m}$  and  $u_{1m}$ , where  $J_0(u_{0m}) = 0$  and  $J_1(u_{1m}) = 0$ . The first solution ( $m = 1$ ), which is used for easy mode identification, is shown in Figure A.3 by curve (A). The computed result of the  $W$ - $v$  relation for  $m = 1$  of  $TE_{0mp}$  resonance mode is shown in Figure A.3 by curve (B).

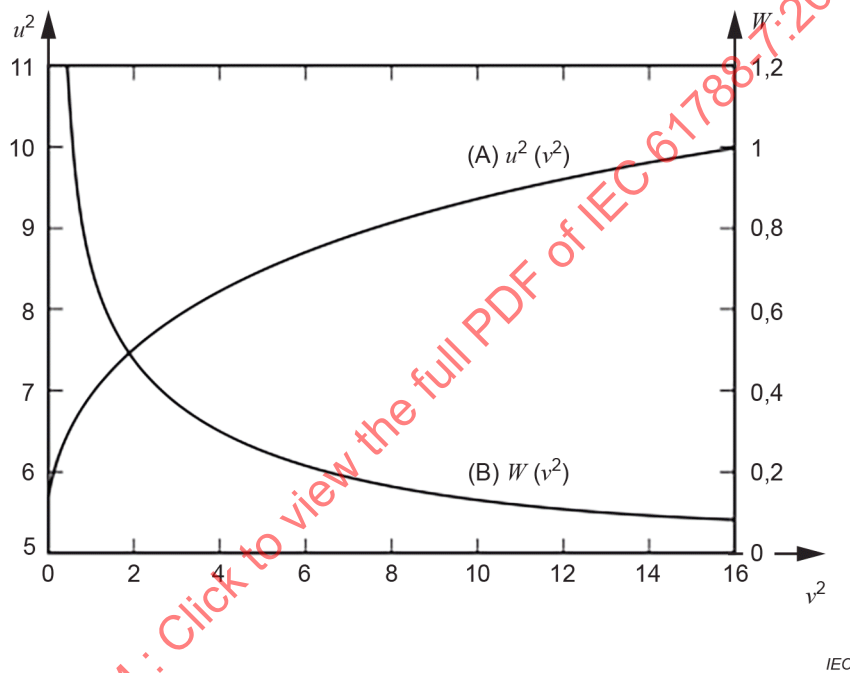


**Figure A.3 – Computed results of the  $u$ - $v$  and  $W$ - $v$  relations for  $TE_{01p}$  mode**

The value of  $\varepsilon'$  is given by

$$\varepsilon' = \left( \frac{\lambda_0}{\pi d} \right)^2 (u^2 + v^2) + 1 \quad (\text{A.8})$$

using the value of  $v^2$  and  $u^2$ .

In the two-resonator method, a pair of dielectric rods, which are called "standard dielectric rods", are used. These two rods have the same diameter but have different heights. The rod heights are such that one rod is  $p$  times the height of the other;  $p$  is commonly set equal to three. They are required to have the same values of  $\varepsilon'$  and  $\tan \delta$ .

Figure A.4 shows the configuration of the standard dielectric rods in the case of  $p = 3$ . To avoid confusion, the height of the short standard dielectric rod is denoted by  $h_0$ . Each resonator is called "TE<sub>011</sub> resonator" and "TE<sub>013</sub> resonator", respectively. The same superconductor films are used in these resonators. The values of  $f_0$  and  $Q_u$  for the TE<sub>011</sub> mode are measured using the TE<sub>011</sub> resonator, and those for the TE<sub>01p</sub> mode are measured using the TE<sub>01p</sub> resonator. We denote the  $f_0$  and  $Q_u$  for each resonator by using the subscripts 1 and  $p$ , respectively:  $f_{01}$  and  $Q_{u1}$  for TE<sub>011</sub> resonator, and  $f_{0p}$  and  $Q_{up}$  for TE<sub>01p</sub> resonator.

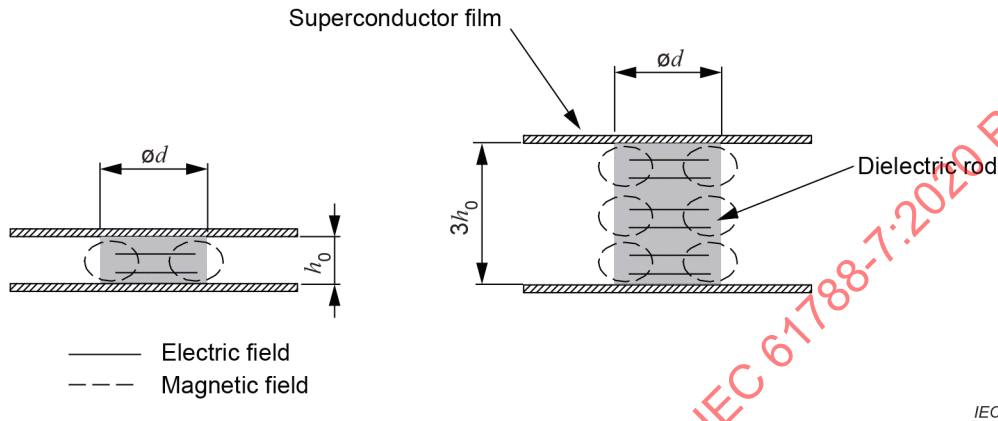


**Figure A.4 – Configuration of standard dielectric rods for measurement of  $R_s$  and  $\tan \delta$**

The value of  $\tan \delta$  is given from the measured values of  $Q_u$ . When the TE<sub>01p</sub> resonator is precisely  $p$  times longer than the TE<sub>011</sub> resonator,  $f_{0p}$  coincides with  $f_{01}$ . However,  $Q_{up}$  is higher than  $Q_{u1}$  according to the different magnitude of the electric field energy stored in the two resonators. Because both dielectric rods are short-circuited at both ends by the same superconductor films, Equation (A.1) yields

$$\tan \delta = \frac{A}{(p-1)} \left( \frac{p}{Q_{up}} - \frac{1}{Q_{u1}} \right) \quad (\text{A.9})$$

$$\tan \delta = \frac{A}{(3-1)} \left( \frac{3}{Q_{up}} - \frac{1}{Q_{u1}} \right) \quad (\text{A.9})$$

As an alternative method, the value of  $R_s$  of superconductor films can be directly measured by

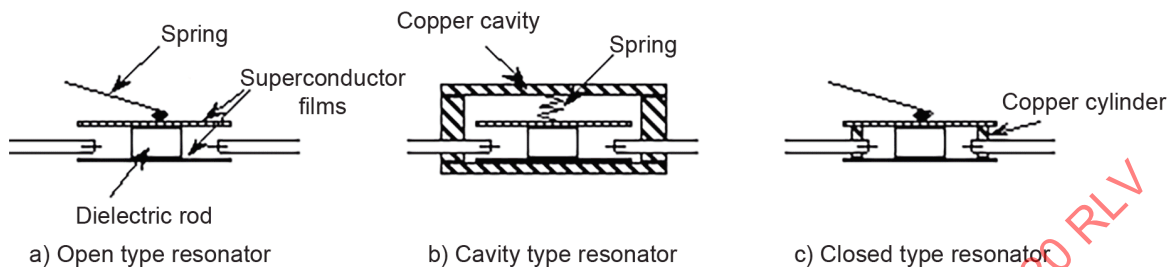
$$R_s = \frac{30\pi^2 p}{(p-1)} \left( \frac{2h_0}{\lambda_0} \right)^3 \frac{\epsilon' + W}{1 + W} \left( \frac{1}{Q_{u1}} - \frac{1}{Q_{up}} \right) \quad (\text{A.10})$$

$$R_s = \frac{30\pi^2 \times 3}{(3-1)} \left( \frac{2h_0}{\lambda_0} \right)^3 \frac{\epsilon' + W}{1 + W} \left( \frac{1}{Q_{u1}} - \frac{1}{Q_{up}} \right) \quad (\text{A.10})$$

where Equation (A.10) is derived by substituting Equation (A.9) into Equation (A.1).

## A.4 Apparatus

Unwanted parasitic coupling to the other mode reduces the high  $Q$ -value of the TE mode resonator. For suppressing the parasitic coupling, special attention is paid to design high  $Q$ -value resonators. Three types of resonators are proposed and shown in Figure A.5.



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**Figure A.5 – Three types of dielectric resonators**

- Open type resonator: a low loss dielectric rod is placed between two parallel superconductor films. Two semi-rigid cables for the RF input and output magnetic dipole coupling are attached on both sides of the resonator. In this configuration, the vertical position of the coupling cables should be carefully designed so as to prevent the radiation loss propagating along the coupling cables, which degrades the high  $Q$ -value of the  $TE_{0mp}$  mode and causes the increase in error for the  $R_s$  measurements. The coupling cables should be set as close as possible to the lower superconductor film.
- Cavity type resonator: the open type resonator shown in a) is placed in a conductor (copper) cavity.
- Closed type resonator: conductor (copper) cylinder is put between the superconductor films. In this configuration, the radiation loss along the coupling cable is strongly blocked by the copper cylinder. The vertical position of the coupling cables ( $z$ ) at the highest  $z$ -axis magnetic field component ( $H_z$ ), i.e.  $z = h/2$ , is recommended.

The measuring apparatus on the cryocooler is protected from mechanical and thermal disturbances, and installed in an X-Y and/or Z-axial manipulator for adjusting sample positions in the range of approximately  $\pm 1$  mm.

A loop length of the antenna is designed on the basis of the quarter-wavelength rule for achieving the maximum measuring sensitivity.

## A.5 Dimensions of the standard sapphire rods

Figure A.6 and Figure A.7 show the mode charts for designing the  $TE_{011}$  and  $TE_{013}$  mode resonators, respectively, short-circuited at both ends by parallel superconductor films, in which a uniaxial-anisotropic characteristic of the relative permittivity of the sapphire rod is taken into consideration [11] [28].  $\epsilon_z$  is the relative permittivity in the direction of the  $c$ -axis,  $\epsilon_r$  is that in the plane perpendicular to the  $c$ -axis,  $d$  is the diameter of the sapphire rod,  $h$  is the height of the sapphire rod, and  $\lambda_0$  is the free space resonant wavelength. As shown in Figure A.6 and Figure A.7,  $TE_{013}$  resonance mode is apt to be affected by TM or HE mode in comparison with  $TE_{011}$  resonance mode. Since the coupling between TE mode and other modes causes the degradation of unloaded  $Q$ , the  $(d/h)$  of the sapphire rods shall be selected so as to avoid the unwanted couplings.

As shown in Figure A.7, the value  $(d/h)^2$  for the  $TE_{013}$  resonator is selected from 0,24 to 0,46 in order that the  $TE_{013}$  resonance mode is not affected by the other modes. This value

$(d/h)^2 = 0,24$  to  $0,46$  leads to a value of  $(d/h)^2 = 2,2$  to  $4,1$  for the  $TE_{011}$  resonator. The  $TE_{011}$  resonance mode does not also couple with other modes when the value  $(d/h)^2$  is in the region of  $2,2$  to  $4,1$  as shown in Figure A.6.

As the resonant frequency of TE mode is a function of relative permittivity and dimensions of the sapphire rod, its diameter and height are selected so that the desired  $f_0$  is obtained.

From the curve of  $TE_{011}$  mode in Figure A.6, the value of  $\varepsilon_r (d/\lambda_0)^2$  can be determined for each  $(d/h)^2$  value. When the value  $(d/h)^2$  equals  $4,0$ , for example, the value of  $\varepsilon_r (d/\lambda_0)^2$  equals  $1,92$ . Thus, the resonant frequency of  $TE_{011}$  mode for the sapphire rod with dimension of  $(d/h)^2 = 4,0$  is calculated from Equation (A.11) by specifying  $d$  and  $\varepsilon_r$  of the sapphire rod:

$$\varepsilon_r (d / \lambda_0)^2 = \varepsilon_r (d \times f_0 / c)^2 = 1,92 \quad (A.11)$$

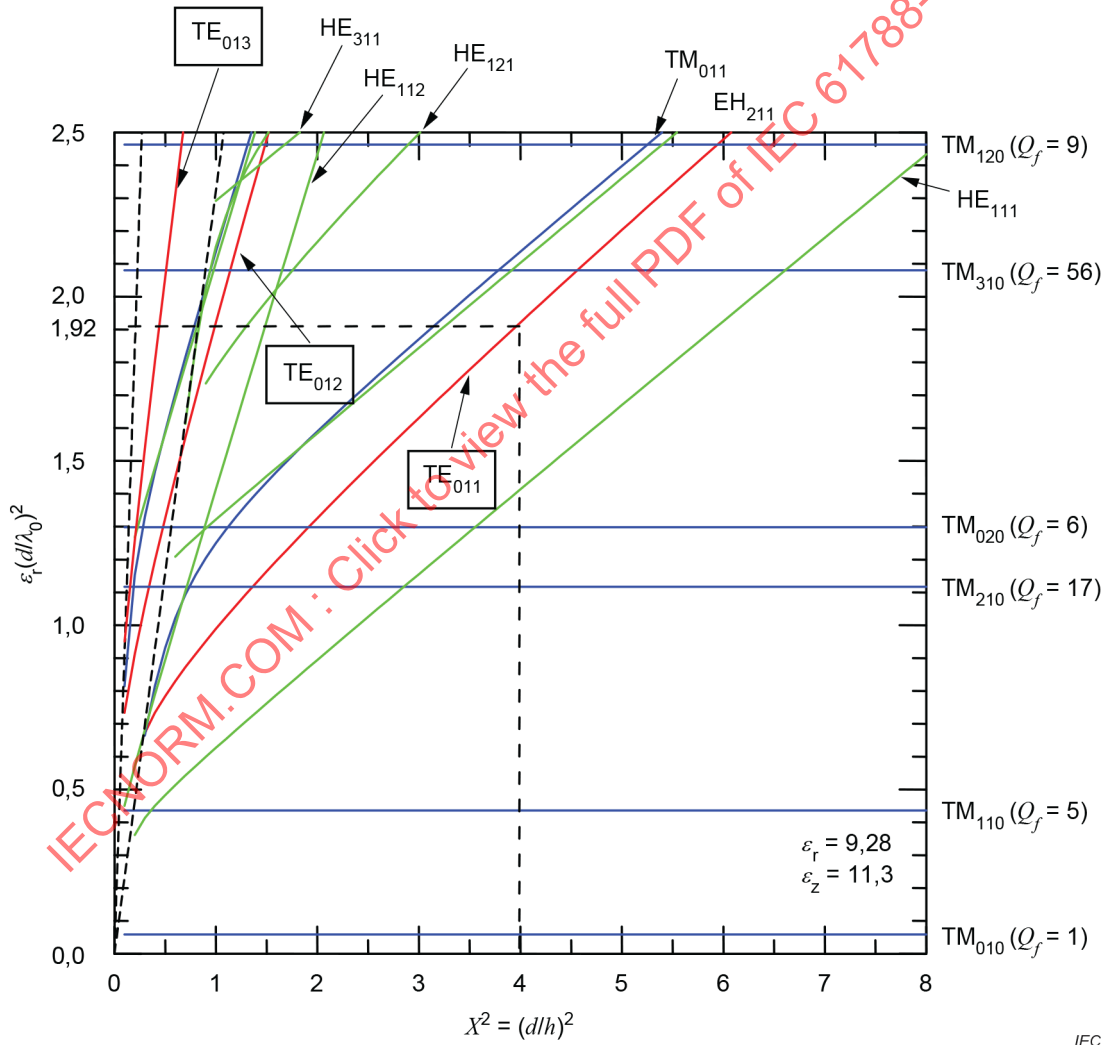


**Figure A.6 – Mode chart to design  $TE_{011}$  resonator short-circuited at both ends by parallel superconductor films [14] [28]**

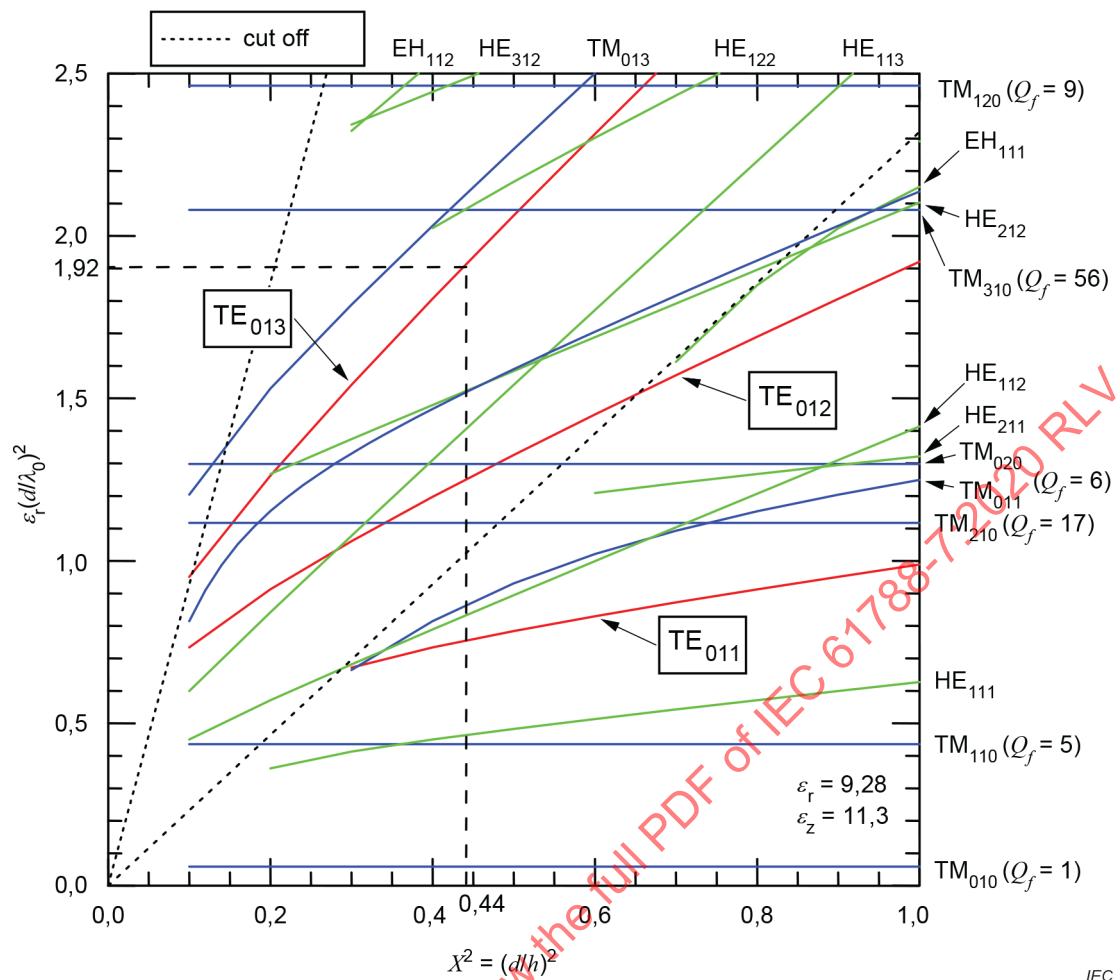


Figure A.7 – Mode chart to design TE<sub>013</sub> resonator short-circuited at both ends by parallel superconductor films [14] [28]

## A.6 Dimension of the closed type resonator

In the closed type resonator, a copper cylinder is put between the superconductor films and a sapphire rod is placed in the center of the copper cylinder (Figure A.5 c)). The resonant frequency of each mode changes with the inner diameter of the copper cylinder,  $D$ . Therefore,  $D$  shall be selected so as to avoid the unwanted coupling with the other modes. In Figure A.8 and Figure A.9, mode charts of the closed type resonators are shown for the short sapphire rod ( $(d/h)^2 = 4$ ) and the long sapphire rod ( $(d/h)^2 = 0.44$ ), respectively, as a function of  $S = D/d$  [14] [28]. The ranges of  $S$  to separate the TE<sub>011</sub> and the TE<sub>013</sub> modes simultaneously from the others are  $S = 1.8$  to  $2.8$ ,  $3.8$  to  $4.1$  and  $4.8$  to  $5.2$ . The value of  $S = D/d = 4$  is recommended because of the ease with which it can be treated.

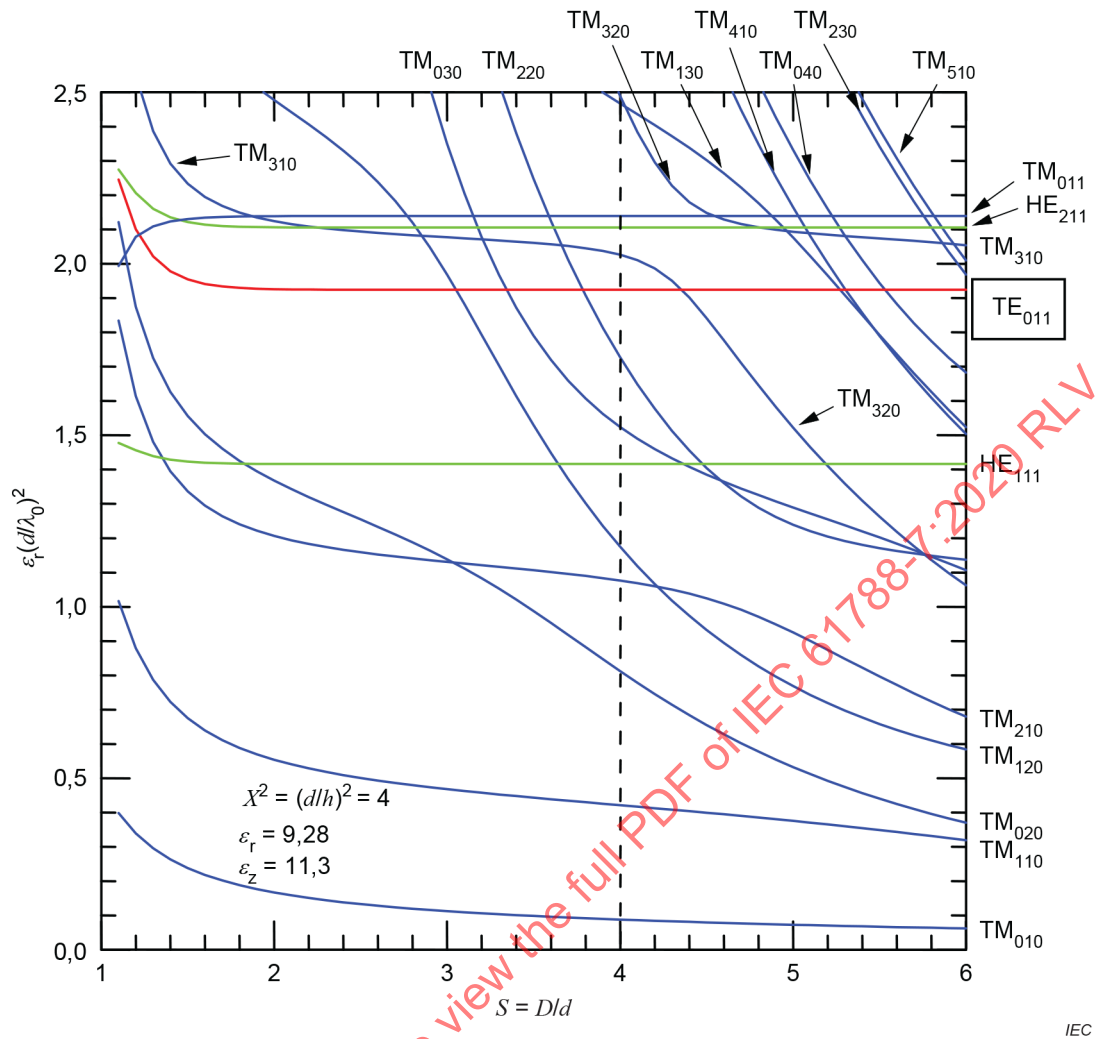


Figure A.8 – Mode chart for TE<sub>011</sub> closed-type resonator [28]

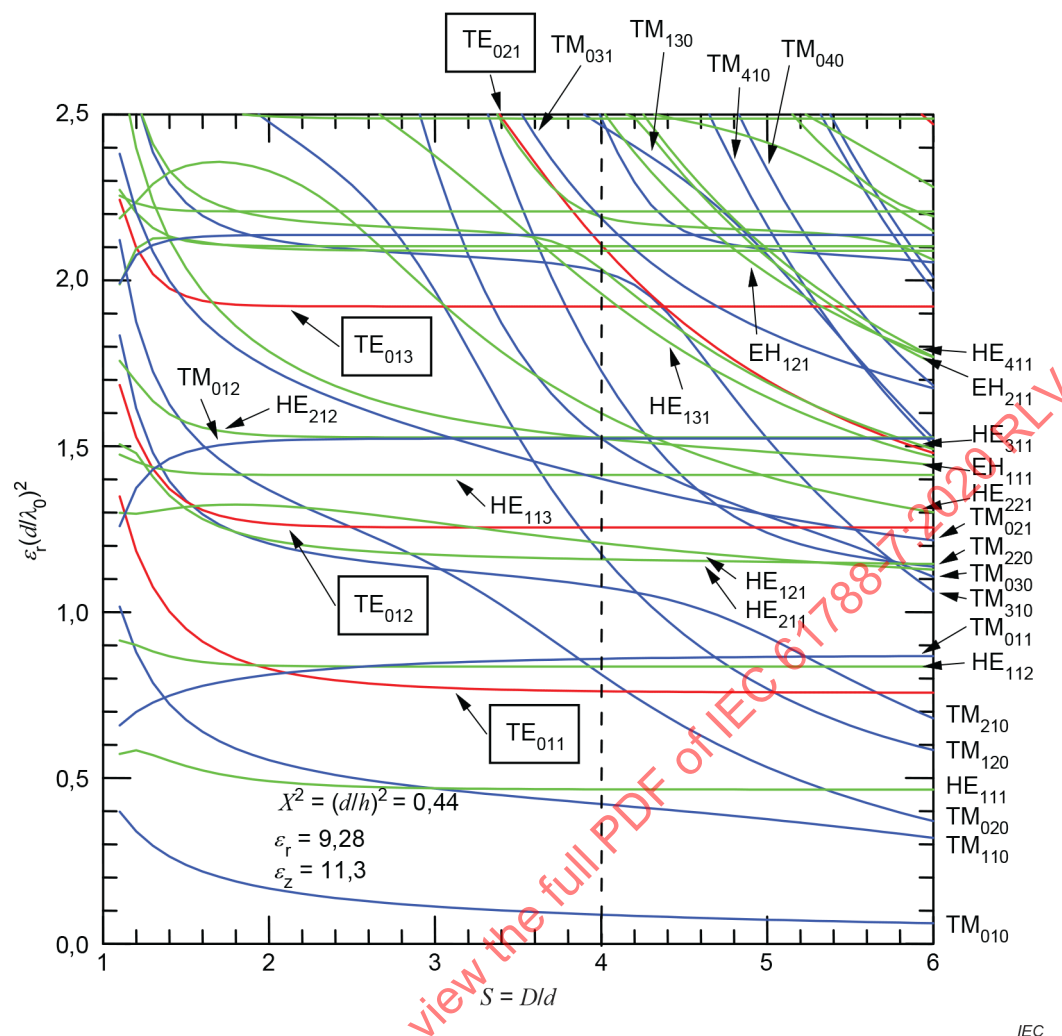


Figure A.9 – Mode chart for  $TE_{013}$  closed-type resonator [28]

## A.7 Precision and accuracy of the test method

Errors estimation [4][10], sensitivity, accuracy and repeatability for these methods can be obtained by the error analysis concerning  $R_s$  as well as by the round robin test.

## A.7 Sapphire rod reproducibility

Knowing the value of  $\tan \delta$  of the sapphire rod is a difficult problem. One approach based on the single- and triple-height rods involves the selection of a standard rod for each type. The first step is to compare a large number of sapphire rods by measuring them in a single HTS/sapphire resonator. The sapphire rod with the highest unloaded  $Q$ -value is the temporary label of standard. This procedure is repeated for a set of triple-height rods. The “standard” single- and triple-height rods are then used as described above to obtain  $\tan \delta$ . The electrical properties,  $\epsilon'$  and  $\tan \delta$ , of other rods can then be calibrated by a direct comparison with these standard rods. Using a calibrated single-height rod, it is then possible to extract the  $R_s$  values of superconductor films under test.

## A.8 Test results

Figure A.10 shows the temperature-dependent  $R_s$  of a YBCO film with a thickness of 500 nm and size of 25 mm square. The YBCO film was formed on MgO substrate by a co-evaporation method. The measurement was carried out at 21,8 GHz, which was converted to 10 GHz by the  $f^2$  rule.

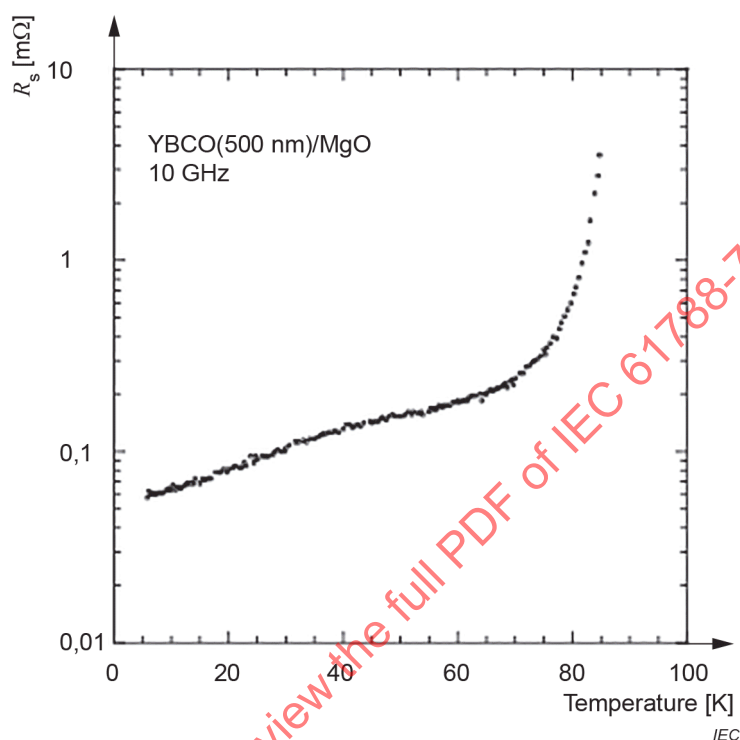


**Figure A.10 – Temperature-dependent  $R_s$  of YBCO film with a thickness of 500 nm and size of 25 mm square**

## A.9 Reproducibility of measurement method

In order to evaluate the reproducibility of the surface resistance measurement,  $R_s$  of the same sample was measured three times and the variation of  $R_s$  was examined. The sample was reset to the measurement cavity each time. Figure A.11 shows the results. Measurement was performed at a frequency of 21,8 GHz and converted to 10 GHz according to the  $f^2$  rule [30]. The variation in  $R_s$  was within 10 % in the temperature range of 10 K to 80 K.

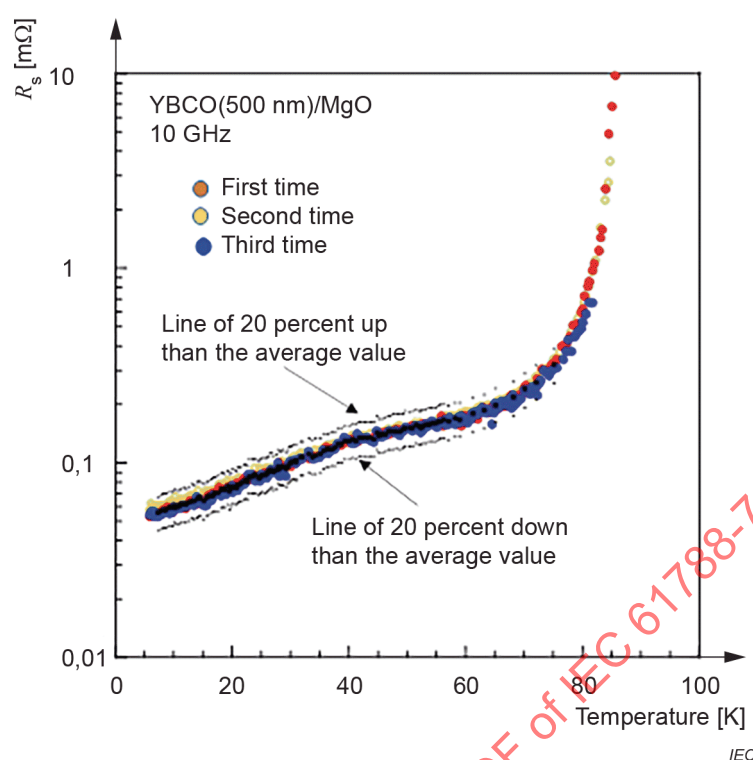


**Figure A.11 – Temperature dependent  $R_s$  of YBCO film when  $R_s$  was measured three times**

From the results, the standard deviation of each temperature can be calculated and its values are shown in Table A.1.

**Table A.1 – Standard deviation of the surface resistance calculated from the results of Figure A.11**

| Temperature (K)        | 20   | 40   | 60   | 80  |
|------------------------|------|------|------|-----|
| Standard deviation (%) | 0,32 | 0,23 | 0,90 | 6,9 |

#### A.10 $\tan \delta$ deviation effect of sapphire rods on surface resistance

For the two-resonator method,  $\tan \delta$  of the  $TE_{011}$  mode and  $TE_{013}$  sapphire rods are assumed to be absolutely equal. If  $\tan \delta$  of the two sapphire rods is different, it is not possible to calculate the surface resistance using Equation (6). Therefore, it is necessary to check the effect of  $\tan \delta$  deviation on surface resistance.  $\tan \delta$  of the high-purity sapphire rod used for the standard surface resistance measurement is extremely small, less than  $2 \times 10^{-7}$  [22]. Using such a sapphire rod, uncertainty in the surface resistance is quite small; however, if sapphire rods with a large  $\tan \delta$  are used, uncertainty in the surface resistance increases.  $\tan \delta_1$  of the sapphire rod for  $TE_{011}$  mode is assumed to be  $2 \times 10^{-7}$  and  $\tan \delta_3$  of the sapphire rod for  $TE_{013}$  mode changes according to that value. The difference in  $\tan \delta$  of the two sapphire rods is defined as in Equation (A.12) and the change in surface resistance as in Equation (A.13).

$$x = \frac{\tan \delta_1 - \tan \delta_3}{\tan \delta_1} \times 100 \quad [\%] \quad (\text{A.12})$$

$$y = \frac{R_s(x) - R_s(0)}{R_s(0)} \quad (\text{A.13})$$

$R_s$  can be calculated using Equation (A.14) when  $\tan \delta_1$  and  $\tan \delta_3$  are different. The relationship between  $x$  and  $y$  is shown in Table A.2. When the difference in  $\tan \delta$  of the two sapphire rods exceeds  $\pm 50$  %, the change in surface resistance exceeds  $\pm 18$  %.

$$R_s = \frac{1}{B_1} \left( \frac{A_1}{Q_{u1}} - \tan \delta_1 \right) = \frac{1}{B_3} \left( \frac{A_3}{Q_{u3}} - \tan \delta_3 \right) \quad (\text{A.14})$$

$$A_p = 1 + \frac{W}{\varepsilon_p'} \quad (\text{A.15})$$

$$B_p = p^2 \left( \frac{\lambda_0}{2h_p} \right)^3 \frac{1 + W}{30\pi^2 \varepsilon_p'}, (p = 1, 3) \quad (\text{A.16})$$

$$W = \frac{J_1^2(u) K_0(v) K_2(v) - K_1^2(v)}{K_1^2(v) J_1^2(u) - J_0(u) J_2(u)} \quad (\text{A.17})$$

$$v_0^2 = \left( \frac{\pi d_0}{\lambda_0} \right)^2 \left[ \left( \frac{\lambda_0}{2h_0} \right)^2 - 1 \right] \quad (\text{A.18})$$

$$u_0 \frac{J_0(u_0)}{J_1(u_0)} = -v_0 \frac{K_0(v_0)}{K_1(v_0)} \quad (\text{A.19})$$

**Table A.2 – Relationship between  $x$ , defined by Equation (A.12), and  $y$ , defined by Equation (A.13)**

| $x$ (%) | –50  | –40  | –30  | –20 | –10 | 0 | +10  | +20  | +30   | +40   | +50   |
|---------|------|------|------|-----|-----|---|------|------|-------|-------|-------|
| $y$ (%) | 18,0 | 14,4 | 10,8 | 7,2 | 3,6 | 0 | –3,6 | –7,2 | –10,8 | –14,4 | –18,0 |

## A.9 — Reference documents

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- [11] ~~HASHIMOTO, T. and KOBAYASHI, Y. Two-Sapphire-Rod-Resonator method to measure the surface resistance of High-Tc superconductor films. *IEICE Trans. Electron.*, 2004, E87-C, No.5, p. 681.~~

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## Annex B (informative)

### Evaluation of relative combined standard uncertainty for surface resistance measurement

#### B.1 Practical surface resistance measurement

A superconductor shows a significantly increased surface resistance when irradiated by a high frequency current in the microwave range. There are several methods for measuring surface resistance, but the dielectric resonator method can measure surface resistance the most accurately. The method is described in Annex A. Figure B.1 shows these two resonators used to measure the frequency characteristics of TE<sub>011</sub> and TE<sub>013</sub> modes.

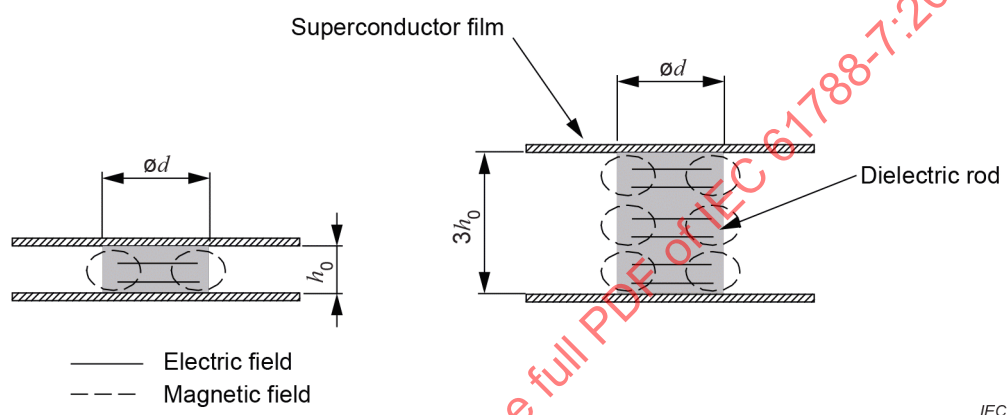


**Figure B.1 – Schematic diagram of TE<sub>011</sub> and TE<sub>013</sub> mode resonance**

Figure B.2 shows the typical frequency characteristics of TE<sub>011</sub> mode resonance.  $Q_{L1}$  is determined using the results of this measurement and  $Q_{u1}$  is calculated using Equation (B.2).

$$Q_{L1} = \frac{f_0}{\Delta f} \quad (B.1)$$

$$Q_{u1} = \frac{Q_{L1}}{1 - A_t}, A_t = 10^{-IA[\text{dB}]/20} \quad (B.2)$$

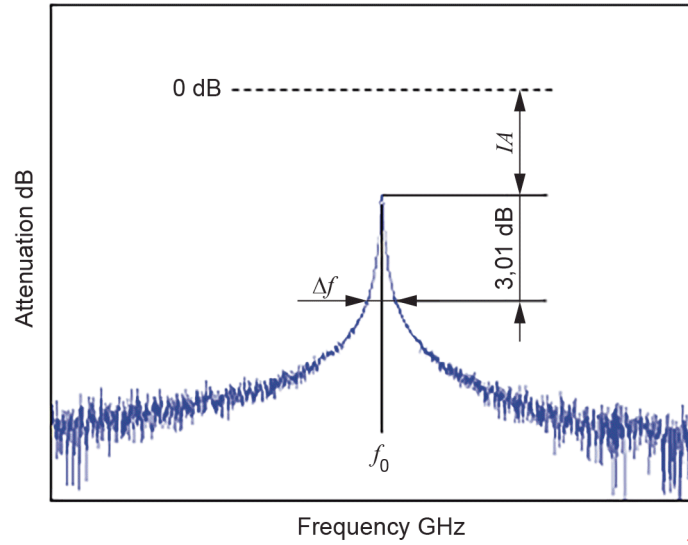


Figure B.2 – Typical frequency characteristics of TE<sub>011</sub> mode resonance

## B.2 Determination of surface resistance of the superconductor

The microwave surface resistance of the superconductor is obtained from Equations (B.3) to (B.8).

$$R_s = \frac{30\pi^2 \times 3}{3-1} \left[ \frac{2h_0}{\lambda_0} \right]^3 \frac{\varepsilon' + W}{1+W} \left[ \frac{1}{Q_{u1}} - \frac{1}{Q_{u3}} \right] \quad (\text{B.3})$$

$$\varepsilon' = \left( \frac{\lambda_0}{\pi d} \right)^2 (u^2 + v^2) + 1 \quad (\text{B.4})$$

$$W = \frac{J_1^2(u) K_0(v) K_2(v) - K_1^2(v)}{K_1^2(v) J_1^2(u) - J_0(u) J_2(u)} \quad (\text{B.5})$$

$$v^2 = \left( \frac{\pi d}{\lambda_0} \right)^2 \left[ \left( \frac{3\lambda_0}{2h_0} \right)^2 - 1 \right] \quad (\text{B.6})$$

$$u \frac{J_0(u)}{J_1(u)} = -v \frac{K_0(v)}{K_1(v)} \quad (\text{B.7})$$

$$\lambda_0 = \frac{c}{f_0} \quad (\text{B.8})$$

Here,  $d$  and  $h_0$  are the diameter and height of the sapphire rod, respectively,  $\varepsilon'$  is the effective relative permittivity of the sapphire rod,  $c$  is the speed of light in vacuum, and  $f_0$  is the resonant frequency of the resonator.

### B.3 Combined standard uncertainty

#### B.3.1 General

By partially differentiating the equation (B.3) with  $h_0$ ,  $\varepsilon'$ ,  $W$ ,  $Q_{u1}$ , and  $Q_{u3}$ , the equation of uncertainty shown in Equation (B.9) is obtained.

$$\begin{aligned}
 u_c^2 &= \frac{\delta R_s^2}{R_s^2} = \left( \frac{\partial R_s}{\partial h} \right)^2 \left( \frac{\delta h}{R_s} \right)^2 + \left( \frac{\partial R_s}{\partial \varepsilon'} \right)^2 \left( \frac{\delta \varepsilon'}{R_s} \right)^2 + \left( \frac{\partial R_s}{\partial W} \right)^2 \left( \frac{\delta W}{R_s} \right)^2 \\
 &+ \left( \frac{\partial R_s}{\partial Q_{u1}} \right)^2 \left( \frac{\delta Q_{u1}}{R_s} \right)^2 + \left( \frac{\partial R_s}{\partial Q_{u3}} \right)^2 \left( \frac{\delta Q_{u3}}{R_s} \right)^2 + c_{\text{unknown}}^2 u_{\text{unknown}}^2 \\
 &(\delta h = hu_1, \delta \varepsilon' = \varepsilon' u_2, \delta W = Wu_3, \delta Q_{u1} = Q_{u1} u_4, \delta Q_{u3} = Q_{u3} u_5) \\
 &= \left( \frac{\partial R_s}{\partial h} \right)^2 \left( \frac{h}{R_s} \right)^2 u_1^2 + \left( \frac{\partial R_s}{\partial \varepsilon'} \right)^2 \left( \frac{\varepsilon'}{R_s} \right)^2 u_2^2 + \left( \frac{\partial R_s}{\partial W} \right)^2 \left( \frac{W}{R_s} \right)^2 u_3^2 \\
 &+ \left( \frac{\partial R_s}{\partial Q_{u1}} \right)^2 \left( \frac{Q_{u1}}{R_s} \right)^2 u_4^2 + \left( \frac{\partial R_s}{\partial Q_{u3}} \right)^2 \left( \frac{Q_{u3}}{R_s} \right)^2 u_5^2 + c_{\text{unknown}}^2 u_{\text{unknown}}^2 \\
 &= c_1^2 u_1^2 + c_2^2 u_2^2 + c_3^2 u_3^2 + c_4^2 u_4^2 + c_5^2 u_5^2 + c_{\text{unknown}}^2 u_{\text{unknown}}^2
 \end{aligned} \tag{B.9}$$

The variables  $c_{\text{unknown}}$  and  $u_{\text{unknown}}$  in Equation (B.9) represent in the uncertainty of unknown factors of measurement system, for example, noise factor. The variables in Equation (B.9) are expressed by Equations (B.10) to (B.14).

$$c_1 = \frac{\partial R_s}{\partial h} \frac{h}{R_s} = \frac{3R_s}{h_0} \frac{h_0}{R_s} = 3 \tag{B.10}$$

$$c_2 = \frac{\partial R_s}{\partial \varepsilon'} \frac{\varepsilon'}{R_s} = \frac{\varepsilon'}{\varepsilon' + W} \tag{B.11}$$

$$c_3 = \frac{\partial R_s}{\partial W} \frac{W}{R_s} = \frac{(1 - \varepsilon')W}{(1 + W)(\varepsilon' + W)} \tag{B.12}$$

$$c_4 = \frac{\partial R_s}{\partial Q_{u1}} \frac{Q_{u1}}{R_s} = \frac{-Q_{u3}}{Q_{u3} - Q_{u1}} \tag{B.13}$$

$$c_5 = \frac{\partial R_s}{\partial Q_{u3}} \frac{Q_{u3}}{R_s} = \frac{Q_{u1}}{Q_{u3} - Q_{u1}} \tag{B.14}$$

#### B.3.2 Calculation of $c_2$ to $c_5$ (12 GHz resonance at 20 K)

When calculating uncertainty using the Equation (B.9), it is necessary to specify the resonant frequency. Here, we will discuss a typical 12 GHz resonator.

12 GHz resonator ( $f_0 = 12$  GHz,  $d = 11,4$  mm,  $h_0 = 5,7$  mm)

Using the above values, we can calculate  $v^2$  and  $u^2$  by Equations (B.6) and (B.7).

$$v^2 = 7,815, u^2 = 9,09 \quad (\text{B.15})$$

$\varepsilon'$  and  $W$  are determined by Equations (B.4) and (B.5).

$$\varepsilon' = 9,22, W = 0,16 \quad (\text{B.16})$$

Then  $c_2$  and  $c_3$  can be determined using Equations (B.11) and (B.12).

$$c_2 = 0,983, c_3 = -0,122 \quad (\text{B.17})$$

In order to determine  $c_4$  and  $c_5$ , we have to know the values of unloaded  $Q_{u1}$  and  $Q_{u3}$ . Y. Kobayashi reported  $Q_{u1}$  and  $Q_{u3}$  at 20 K, 12 GHz [28]. Their reported values were  $Q_{u1} = 2\,000\,000$  ( $Q_{L1} = 1\,800\,000$ ) and  $Q_{u3} = 7\,500\,000$  ( $Q_{L3} = 6\,750\,000$ ). Therefore,  $c_4$  and  $c_{5L}$  can be calculated.

$$c_4 = 1,364, c_5 = 0,3636 \quad (\text{B.18})$$

### B.3.3 Determination of $u_1$ to $u_5$

$u_1$  to  $u_5$ , which are derived from the uncertainty of the diameter, height and dielectric constant of sapphire rod and  $Q_{u1}$  and  $Q_{u3}$  of the cavity, are calculated by the following procedures.

#### 1) $u_1$

$u_1$  is determined by the uncertainty of the height of the sapphire rod. The height of the sapphire rod of the 12 GHz resonator is 5,7 mm, and its uncertainty is 50  $\mu\text{m}$ . Therefore,  $u_1$  is as follows.

$$u_1 = \frac{1}{\sqrt{3}} \frac{0,05}{5,7} = 0,005\,07 \quad (\text{B.19})$$

#### 2) $u_2$

$u_2$  is determined by the uncertainty in the effective dielectric constant  $\varepsilon'_\delta$  of the sapphire rod and can be calculated using Equation (B.20).

$$u_2 = \frac{1}{\sqrt{3}} \frac{\varepsilon' - \varepsilon'_\delta}{\varepsilon'} \quad (\text{B.20})$$

where  $\varepsilon'_\delta$  is the relative permittivity induced from uncertainty in the shape of the sapphire rod.

$$\varepsilon' = \left( \frac{\lambda_0}{\pi d_0} \right)^2 (u_0^2 + v_0^2) + 1 \quad (d_0 = 11,4 \text{ mm}, h_0 = 5,7 \text{ mm}) \quad (\text{B.21})$$

$$\varepsilon'_\delta = \left( \frac{\lambda_0}{\pi d} \right)^2 (u_{0\delta}^2 + v_{0\delta}^2) + 1 \quad (d_{0\delta} = 11,45 \text{ mm}, h_{0\delta} = 5,65 \text{ mm}) \quad (\text{B.22})$$

and  $u_0$ ,  $v_0$ ,  $u_{0\delta}$  and  $v_{0\delta}$  are calculated using Equations (B.23) and (B.24).

$$v_0^2 = \left( \frac{\pi d_0}{\lambda_0} \right)^2 \left[ \left( \frac{3\lambda_0}{2h_0} \right)^2 - 1 \right], v_{0\delta}^2 = \left( \frac{\pi d_{0\delta}}{\lambda_0} \right)^2 \left[ \left( \frac{3\lambda_0}{2h_{0\delta}} \right)^2 - 1 \right] \quad (\text{B.23})$$

$$u_0 \frac{J_0(u_0)}{J_1(u_0)} = -v_0 \frac{K_0(v_0)}{K_1(v_0)}, u_{0\delta} \frac{J_0(u_{0\delta})}{J_1(u_{0\delta})} = -v_{0\delta} \frac{K_0(v_{0\delta})}{K_1(v_{0\delta})} \quad (\text{B.24})$$

As a result, we find that  $\varepsilon' = 9,22$  and  $\varepsilon'_\delta = 9,29$ .

$$u_2 = 0,004\ 4 \quad (\text{B.25})$$

3)  $u_3$

$u_3$  can be determined using Equation (B.26).

$$u_3 = \frac{1}{\sqrt{3}} \frac{W - W_\delta}{W} \quad (\text{B.26})$$

$W$  is determined using Equation (B.5) and  $W_\delta$  comes from uncertainty in the shape of the sapphire rod and can be determined by using Equation (B.27).

$$W_\delta = \frac{J_1^2(u_\delta) K_0(v_\delta) K_2(v_\delta) - K_1^2(v_\delta)}{K_1^2(v_\delta) J_1^2(u_\delta) - J_0(u_\delta) J_2(u_\delta)} \quad (\text{B.27})$$

By calculating  $W$  and  $W_\delta$  using  $u_0, v_0, u_{0\delta}, v_{0\delta}$  in Equations (B.23) and (B.24),  $u_3$  turns out to have the following value.

$$u_3 = 0,014\ 3 \quad (\text{B.28})$$

4)  $u_4$  and  $u_5$

$u_4$  and  $u_5$  are determined by measuring the uncertainty in  $Q_{u1}$  and  $Q_{u3}$ . The measurement of the uncertainty in  $Q_{u1}$  and  $Q_{u3}$  has the most influence on the dynamic range uncertainty of the vector network analyzer and other factors are negligible. Since the dynamic range uncertainty in the recommended vector network analyzer is  $\pm 0,1$  dB,  $u_4$  and  $u_5$  are calculated using this value. Regarding the frequency characteristics of the resonator in Figure B.2, the frequency characteristic near the resonant frequency is assumed to be a Lorentz distribution [30].

$$y = \left| \frac{S_{12}(f)}{S_{12}(f_0)} \right| = \frac{1}{\left( 1 + Q^2 \Delta^2(f) \right)^{1/2}} = \frac{1}{\left( 1 + \left( \frac{f - f_0}{f_1} \right)^2 \right)^{1/2}},$$

$$\Delta(f) = 1 - \frac{f_0^2}{f^2} = \frac{2(f - f_0)}{f_0} \quad (\text{B.29})$$

The frequency characteristics are shown in Figure B.3 The curve can be approximated by Equation (B.29), where  $f_0$  is the resonant frequency and  $2f_1$  is the bandwidth at 3,01 dB. The frequency bandwidth which is 3,01 dB below the resonance peak is defined as  $\Delta f$  and it corresponds to the bandwidth across 0,707 in Figure B.3. The  $\pm 0,1$  dB of the dynamic range uncertainty corresponds to  $\pm 0,008$  in Figure B.3. Therefore,  $Q_{L1}$ ,  $Q_{L1\delta}$ ,  $Q_{L3}$ , and  $Q_{L3\delta}$

can be calculated.  $Q_{L1}$  and  $Q_{L3}$  are reported as  $1,80 \times 10^6$  and  $6,75 \times 10^6$ , respectively [28]. Using these values, we can calculate  $Q_{L1\delta}$  and  $Q_{L3\delta}$ .

$$Q_{L1} = 1,80 \times 10^6, \quad Q_{L1\delta} = 1,84 \times 10^6, \quad Q_{L3} = 6,75 \times 10^6, \quad Q_{L3\delta} = 6,90 \times 10^6$$

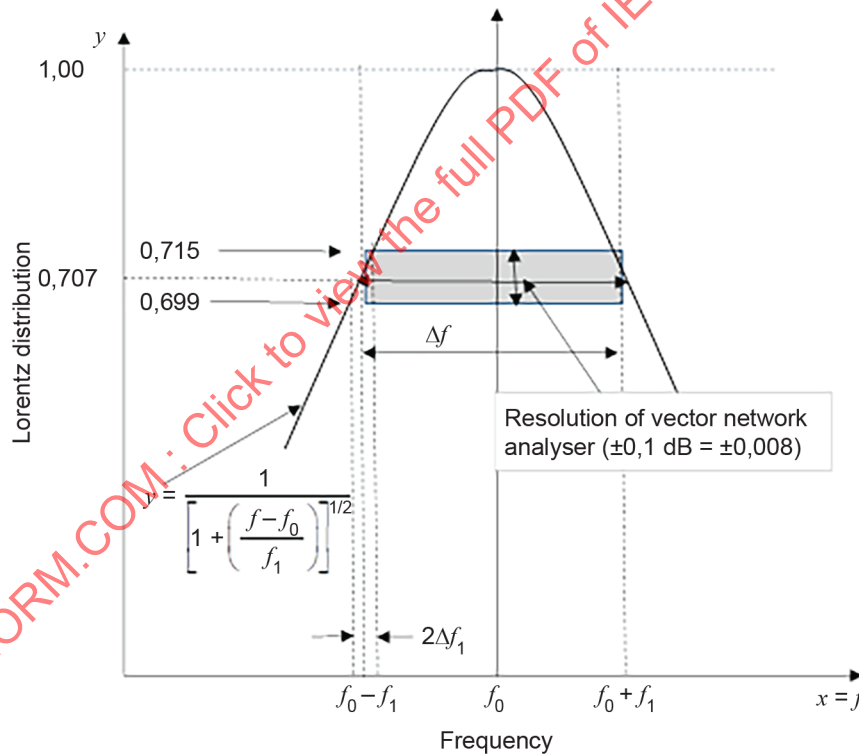
Assuming insertion attenuation ( $IA$ ) = 20dB,  $Q_{u1}$ ,  $Q_{u1\delta}$ ,  $Q_{u3}$ , and  $Q_{u3\delta}$  can be calculated.

$$Q_{u1} = 2,00 \times 10^6, \quad Q_{u1\delta} = 2,044 \times 10^6, \quad Q_{u3} = 7,5 \times 10^6, \quad Q_{u3\delta} = 7,67 \times 10^6$$

Through these calculations, the values of  $u_4$  and  $u_5$  are obtained.

$$u_4 = \frac{1}{\sqrt{3}} \frac{Q_{u1} - Q_{u1\delta}}{Q_{u1}} = -0,012 \quad (\text{B.30})$$

$$u_5 = \frac{1}{\sqrt{3}} \frac{Q_{u3} - Q_{u3\delta}}{Q_{u3}} = -0,013 \quad (\text{B.31})$$



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**Figure B.3 – Frequency characteristics of a resonator approximated by a Lorentz distribution**

#### B.3.4 Combined relative standard uncertainty

Uncertainties in  $c_{\text{cavity}}$  and  $u_{\text{cavity}}$  due to the loss of copper cavity is quite small, however  $c_{\text{unknown}}$  and  $u_{\text{unknown}}$  are not small. The combined standard uncertainty at 20 K is calculated as follows.

$$\begin{aligned}
 u_c &= \sqrt{c_1^2 u_1^2 + c_2^2 u_2^2 + c_3^2 u_3^2 + c_4^2 u_4^2 + c_5^2 u_5^2 + c_{\text{unknown}}^2 u_{\text{unknown}}^2} \\
 &= \sqrt{2,31 \times 10^{-4} + 0,187 \times 10^{-4} + 0,030 \times 10^{-4} + 2,68 \times 10^{-4} + 0,223 \times 10^{-4} + c_{\text{unknown}}^2 u_{\text{unknown}}^2} \quad (\text{B.32}) \\
 &= \sqrt{5,43 \times 10^{-4} + c_{\text{unknown}}^2 u_{\text{unknown}}^2}
 \end{aligned}$$

It is difficult to quantitatively evaluate  $c_{\text{unknown}} u_{\text{unknown}}$  in Equation (B.32), but its value can be estimated from the results of surface resistance measurement repeated three times. The variation observed when measuring the surface resistance of the same films repeatedly is believed to be due to the noise and temperature uncertainty of the measurement system. Therefore, from the results in Table A.1,  $c_{\text{unknown}} u_{\text{unknown}}$  can be estimated as about 0,32 % for 20 K, about 0,9 % for 60 K, and about 6,9 % for 80 K ( $c_{\text{unknown}} u_{\text{unknown}}$  increases as the measurement temperature increases). From the above results, the combined relative standard uncertainty of Equation (B.32) was about 2,4 % at 20 K and about 7,3 % at 80 K. The value is smaller than the target combined relative standard uncertainty.

When the measured temperature exceeds 70 K, large noise is superimposed on the resonance peak, and the uncertainty in  $R_s$  increases. In that case, it is difficult to express the resonance peak with Lorentz distribution. Therefore, the deviation of  $u_4$  and  $u_5$  have to be reviewed. However, as is clear from the results in Figure A.11 and Table A.1, the uncertainty of  $R_s$  measured by the standard dielectric resonator method is less than 10 % below 80 K.

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### **Superconductivity –**

### **Part 7: Electronic characteristic measurements – Surface resistance of high-temperature superconductors at microwave frequencies**

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### **Partie 7: Mesurages des caractéristiques électronique – Résistance de surface des supraconducteurs haute température critique aux hyperfréquences**

## CONTENTS

|                                                                                                                                        |    |
|----------------------------------------------------------------------------------------------------------------------------------------|----|
| FOREWORD .....                                                                                                                         | 5  |
| INTRODUCTION .....                                                                                                                     | 7  |
| 1 Scope .....                                                                                                                          | 8  |
| 2 Normative references .....                                                                                                           | 8  |
| 3 Terms and definitions .....                                                                                                          | 8  |
| 4 Requirements .....                                                                                                                   | 8  |
| 5 Apparatus .....                                                                                                                      | 9  |
| 5.1 Measurement system .....                                                                                                           | 9  |
| 5.2 Measurement apparatus for $R_s$ .....                                                                                              | 10 |
| 5.3 Dielectric rods .....                                                                                                              | 12 |
| 6 Measurement procedure .....                                                                                                          | 12 |
| 6.1 Specimen preparation .....                                                                                                         | 12 |
| 6.2 Set-up .....                                                                                                                       | 13 |
| 6.3 Measurement of reference level .....                                                                                               | 13 |
| 6.4 Measurement of the frequency response of resonators .....                                                                          | 14 |
| 6.5 Determination of surface resistance of the superconductor and $\varepsilon'$ and $\tan \delta$ of the standard sapphire rods ..... | 16 |
| 7 Uncertainty of the test method .....                                                                                                 | 17 |
| 7.1 Surface resistance .....                                                                                                           | 17 |
| 7.2 Temperature .....                                                                                                                  | 18 |
| 7.3 Specimen and holder support structure .....                                                                                        | 18 |
| 7.4 Specimen protection .....                                                                                                          | 19 |
| 7.5 Uncertainty of surface resistance measured by standard two-resonator method .....                                                  | 19 |
| 8 Test report .....                                                                                                                    | 19 |
| 8.1 Identification of test specimen .....                                                                                              | 19 |
| 8.2 Report of $R_s$ values .....                                                                                                       | 19 |
| 8.3 Report of test conditions .....                                                                                                    | 19 |
| Annex A (informative) Additional information relating to Clauses 1 to 8 .....                                                          | 20 |
| A.1 Scope .....                                                                                                                        | 20 |
| A.1.1 General .....                                                                                                                    | 20 |
| A.1.2 Cylindrical cavity method [10] [17] .....                                                                                        | 20 |
| A.1.3 Parallel-plates resonator method [18] [19] .....                                                                                 | 20 |
| A.1.4 Microstrip-line resonance method [20] [21] .....                                                                                 | 20 |
| A.1.5 Dielectric resonator method [22] [23] [24] [25] .....                                                                            | 20 |
| A.1.6 Image-type dielectric resonator method [26] [27] .....                                                                           | 21 |
| A.1.7 Two-resonator method [28] [29] .....                                                                                             | 22 |
| A.2 Requirements .....                                                                                                                 | 22 |
| A.3 Theory and calculation equations .....                                                                                             | 22 |
| A.4 Apparatus .....                                                                                                                    | 25 |
| A.5 Dimensions of the standard sapphire rods .....                                                                                     | 26 |
| A.6 Dimension of the closed type resonator .....                                                                                       | 28 |
| A.7 Sapphire rod reproducibility .....                                                                                                 | 30 |
| A.8 Test results .....                                                                                                                 | 30 |
| A.9 Reproducibility of measurement method .....                                                                                        | 31 |

|                                                                                                                                                                                 |                                                                             |    |
|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------|----|
| A.10                                                                                                                                                                            | $\tan \delta$ deviation effect of sapphire rods on surface resistance ..... | 32 |
| Annex B (informative) Evaluation of relative combined standard uncertainty for surface resistance measurement .....                                                             |                                                                             | 34 |
| B.1                                                                                                                                                                             | Practical surface resistance measurement .....                              | 34 |
| B.2                                                                                                                                                                             | Determination of surface resistance of the superconductor .....             | 35 |
| B.3                                                                                                                                                                             | Combined standard uncertainty .....                                         | 36 |
| B.3.1                                                                                                                                                                           | General .....                                                               | 36 |
| B.3.2                                                                                                                                                                           | Calculation of $c_2$ to $c_5$ (12 GHz resonance at 20 K) .....              | 36 |
| B.3.3                                                                                                                                                                           | Determination of $u_1$ to $u_5$ .....                                       | 37 |
| B.3.4                                                                                                                                                                           | Combined relative standard uncertainty .....                                | 39 |
| Bibliography .....                                                                                                                                                              |                                                                             | 41 |
| Figure 1 – Schematic diagram of measurement system for temperature dependence of $R_s$ using a cryocooler .....                                                                 |                                                                             | 9  |
| Figure 2 – Typical measurement apparatus for $R_s$ .....                                                                                                                        |                                                                             | 11 |
| Figure 3 – Insertion attenuation, $IA$ , resonant frequency, $f_0$ , and half power bandwidth, $\Delta f$ , measured at $T$ kelvin .....                                        |                                                                             | 14 |
| Figure 4 – Reflection scattering parameters ( $S_{11}$ and $S_{22}$ ) .....                                                                                                     |                                                                             | 16 |
| Figure 5 – Term definitions in Table 4 .....                                                                                                                                    |                                                                             | 18 |
| Figure A.1 – Schematic configuration of several measurement methods for the surface resistance .....                                                                            |                                                                             | 21 |
| Figure A.2 – Configuration of a cylindrical dielectric rod resonator short-circuited at both ends by two parallel superconductor films deposited on dielectric substrates ..... |                                                                             | 23 |
| Figure A.3 – Computed results of the $u$ - $v$ and $W$ - $v$ relations for $TE_{01p}$ mode .....                                                                                |                                                                             | 24 |
| Figure A.4 – Configuration of standard dielectric rods for measurement of $R_s$ and $\tan \delta$ .....                                                                         |                                                                             | 25 |
| Figure A.5 – Three types of dielectric resonators .....                                                                                                                         |                                                                             | 26 |
| Figure A.6 – Mode chart to design $TE_{011}$ resonator short-circuited at both ends by parallel superconductor films [28] .....                                                 |                                                                             | 27 |
| Figure A.7 – Mode chart to design $TE_{013}$ resonator short-circuited at both ends by parallel superconductor films [28] .....                                                 |                                                                             | 28 |
| Figure A.8 – Mode chart for $TE_{011}$ closed-type resonator [28] .....                                                                                                         |                                                                             | 29 |
| Figure A.9 – Mode chart for $TE_{013}$ closed-type resonator [28] .....                                                                                                         |                                                                             | 30 |
| Figure A.10 – Temperature-dependent $R_s$ of YBCO film with a thickness of 500 nm and size of 25 mm square .....                                                                |                                                                             | 31 |
| Figure A.11 – Temperature dependent $R_s$ of YBCO film when $R_s$ was measured three times .....                                                                                |                                                                             | 32 |
| Figure B.1 – Schematic diagram of $TE_{011}$ and $TE_{013}$ mode resonance .....                                                                                                |                                                                             | 34 |
| Figure B.2 – Typical frequency characteristics of $TE_{011}$ mode resonance .....                                                                                               |                                                                             | 35 |
| Figure B.3 – Frequency characteristics of a resonator approximated by a Lorentz distribution .....                                                                              |                                                                             | 39 |
| Table 1 – Typical dimensions of pairs of single-crystal sapphire rods for 12 GHz, 18 GHz and 22 GHz .....                                                                       |                                                                             | 12 |
| Table 2 – Dimensions of superconductor film for 12 GHz, 18 GHz, and 22 GHz .....                                                                                                |                                                                             | 13 |
| Table 3 – Specifications for vector network analyzer .....                                                                                                                      |                                                                             | 17 |

|                                                                                                                 |    |
|-----------------------------------------------------------------------------------------------------------------|----|
| Table 4 – Specifications for sapphire rods .....                                                                | 17 |
| Table A.1 – Standard deviation of the surface resistance calculated from the results of<br>Figure A.11 .....    | 32 |
| Table A.2 – Relationship between $x$ , defined by Equation (A.12), and $y$ , defined by<br>Equation (A.13)..... | 33 |

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Surface resistance of high-temperature  
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International Standard IEC 61788-7 has been prepared by IEC technical committee 90: Superconductivity.

This third edition cancels and replaces the second edition, published in 2006. This edition constitutes a technical revision.

This edition includes the following significant technical changes with respect to the previous edition:

- a) informative Annex B, relative combined standard uncertainty for surface resistance measurement has been added;
- b) precision and accuracy statements have been converted to uncertainty;
- c) reproducibility in surface resistant measurement has been added.

The text of this International Standard is based on the following documents:

| FDIS        | Report on voting |
|-------------|------------------|
| 90/447/FDIS | 90/452/RVD       |

Full information on the voting for the approval of this International Standard can be found in the report on voting indicated in the above table.

This document has been drafted in accordance with the ISO/IEC Directives, Part 2.

A list of all parts of the IEC 61788 series, published under the general title *Superconductivity*, can be found on the IEC website.

The committee has decided that the contents of this document will remain unchanged until the maintenance result date indicated on the IEC web site under "<http://webstore.iec.ch>" in the data related to the specific publication. At this date, the document will be

- reconfirmed;
- withdrawn;
- replaced by a revised edition, or
- amended.

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## INTRODUCTION

Since the discovery of some Perovskite-type Cu-containing oxides, extensive research and development (R & D) work on high-temperature superconductors (HTS) has been, and is being, done worldwide, and its application to high-field magnet machines, low-loss power transmission, electronics and many other technologies is in progress.

In various fields of electronics, especially in telecommunication fields, microwave passive devices such as filters using HTS are being developed and are undergoing on-site testing [1]<sup>1</sup> [2].

Superconductor materials for microwave resonators [3], filters [4], antennas [5] and delay lines [6] have the advantage of very low loss characteristics. The parameters of superconductor materials needed for the design of microwave low loss components are the surface resistance, ( $R_s$ ) and the temperature dependence of the  $R_s$ . Knowledge of this parameter is of primary importance for the development of new materials on the supplier side and for the design of superconductor microwave components on the customer side.

$R_s$  of high quality HTS films is generally several orders of magnitude lower than that of normal metals [7] [8] [9] [10], which has increased the need for a reliable characterization technique to measure this property. Traditionally, the  $R_s$  of niobium or any other low-temperature superconducting material was measured by first fabricating an entire three-dimensional resonant cavity and then measuring its  $Q$ -value [11]. The  $R_s$  could be calculated by solving the electro-magnetic field (EM) distribution inside the cavity. Another technique involves placing a small sample inside a larger cavity. This technique has many forms but usually involves the uncertainty introduced by extracting the loss contribution due to the HTS films from the experimentally measured total loss of the cavity.

The best HTS samples are epitaxial films grown on flat crystalline substrates and no high-quality films have been grown on any curved surface so far. What is needed is a technique that: can use these small flat samples; requires no sample preparation; does not damage or change the film; is highly repeatable; has great sensitivity (down to 1/1 000 the  $R_s$  of copper); has great dynamic range (up to the  $R_s$  of copper); can reach high internal powers with only modest input powers; and has broad temperature coverage (4,2 K to 150 K).

The dielectric resonator method is selected among several methods to determine the surface resistance at microwave frequencies because it is considered to be the most popular and practical at present. Especially, the sapphire resonator is an excellent tool for measuring the  $R_s$  of HTS materials [12] [13] [14]

The test method given in this document can also be applied to other superconductor bulk plates including low  $T_c$  materials.

This document is intended to provide an appropriate and agreeable technical base for the time being to engineers working in the fields of electronics and superconductivity technology.

The test method covered in this document is based on the VAMAS (Versailles Project on Advanced Materials and Standards) pre-standardization work on the thin film properties of superconductors.

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<sup>1</sup> Numbers in square brackets refer to the bibliography.

## SUPERCONDUCTIVITY –

### Part 7: Electronic characteristic measurements – Surface resistance of high-temperature superconductors at microwave frequencies

#### 1 Scope

This part of IEC 61788 describes measurement of the surface resistance ( $R_s$ ) of superconductors at microwave frequencies by the standard two-resonator method. The object of measurement is the temperature dependence of  $R_s$  at the resonant frequency.

The applicable measurement range of  $R_s$  for this method is as follows:

- Frequency: 8 GHz <  $f$  < 30 GHz
- Measurement resolution: 0,01 mΩ at 10 GHz

The  $R_s$  data at the measured frequency, and that scaled to 10 GHz, assuming the  $f^2$  rule for comparison, is reported.

#### 2 Normative references

The following documents are referred to in the text in such a way that some or all of their content constitutes requirements of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

IEC 60050-815, *International Electrotechnical Vocabulary (IEV) – Part 815: Superconductivity*

#### 3 Terms and definitions

For the purposes of this document, the terms and definitions given in IEC 60050-815 apply.

ISO and IEC maintain terminological databases for use in standardization at the following addresses:

- IEC Electropedia: available at <http://www.electropedia.org/>
- ISO Online browsing platform: available at <http://www.iso.org/obp>

#### 4 Requirements

The  $R_s$  of a superconductor film shall be measured by applying a microwave signal to a dielectric resonator with the superconductor film specimen and then measuring the attenuation of the resonator at each frequency. The frequency shall be swept around the resonant frequency as the centre, and the attenuation–frequency characteristics shall be recorded to obtain the  $Q$ -value, which corresponds to the loss.

The target relative combined standard uncertainty of this method is less than 20 % for the measurement temperature range from 20 K to 80 K.

It is the responsibility of the user of this document to establish appropriate safety and health practices and to determine the applicability of regulatory limitations prior to use.

Hazards exist in this type of measurement. The use of a cryogenic system is essential to cool the superconductors to allow transition into the superconducting state. Direct contact of skin with cold apparatus components can cause immediate freezing, as can direct contact with a spilled cryogen. The use of an RF generator is also essential to measure high-frequency properties of materials. If its power is too high, direct contact to human bodies can cause an immediate burn.

## 5 Apparatus

### 5.1 Measurement system

Figure 1 shows a schematic diagram of the system required for the microwave measurement. The system consists of a network analyzer system for transmission measurement, a measurement apparatus, and a thermometer for monitoring the measuring temperature.

An incident power generated from a suitable microwave source such as a synthesized sweeper is applied to the dielectric resonator fixed in the measurement apparatus. The transmission characteristics are shown on the display of the network analyzer. The measurement apparatus is fixed in a temperature-controlled cryocooler.

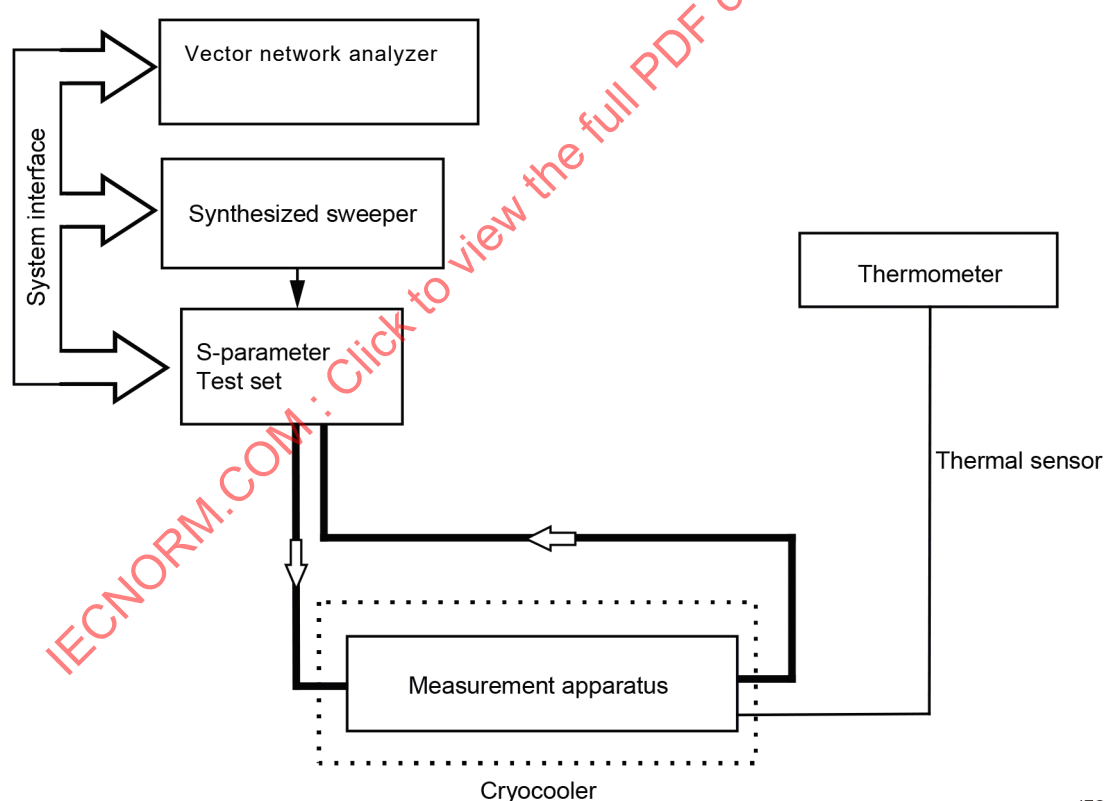


**Figure 1 – Schematic diagram of measurement system for temperature dependence of  $R_s$  using a cryocooler**

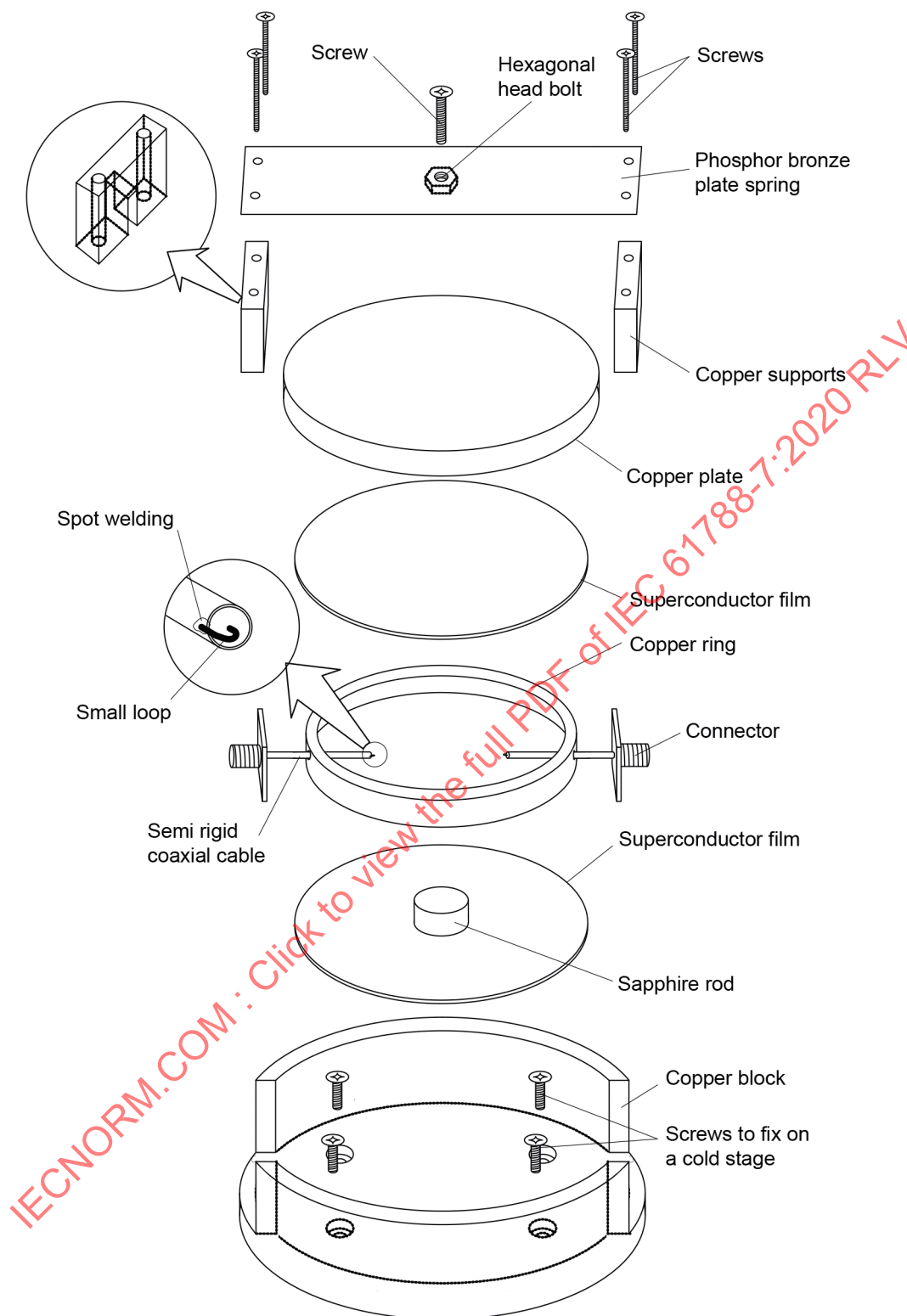
For the measurement of  $R_s$  for superconductor films, a vector network analyzer is recommended. A vector network analyzer has better measurement accuracy than a scalar network analyser due to its wide dynamic range. The performance requirements of the vector network analyzer are specified in 7.1.

## 5.2 Measurement apparatus for $R_s$

Figure 2 shows a schematic of a typical measurement apparatus (closed type resonator) for the  $R_s$  of HTS films deposited on a substrate with a flat surface. The upper HTS film is pressed down by a spring, which is made of phosphor bronze. The plate type spring should be used for the improvement of measurement uncertainty. This type of spring reduces the friction between the spring and the other part of the apparatus, and allows the smooth movement of superconductor films due to the thermal expansion of the dielectric rod. In order to minimize the measurement uncertainty, the sapphire rod and the copper ring shall be arranged coaxially.

Two semi-rigid cables for measuring transmission characteristics of the resonator shall be attached on both sides of the resonator in an axial symmetrical position ( $\phi = 0$  and  $\pi$ , where  $\phi$  is the rotational angle around the central axis of the sapphire rod). Each of the two semi-rigid cables shall have a small loop at the ends. The plane of the loop shall be set parallel to that of the superconductor films in order to suppress the unwanted Transverse Magnetic Wave Modes ( $TM_{mn0}$  modes). The coupling loops shall be carefully checked for cracks in the spot weld joint that may have developed upon repeated thermal cycling. These cables can move right and left to adjust the insertion attenuation ( $IA$ ). In this adjustment, coupling of unwanted cavity modes to the interested dielectric resonance mode shall be suppressed. Unwanted, parasitic coupling to the other modes reduces the high  $Q$ -value of the Transverse Electro-Magnetic Mode (TE mode) resonator. For suppressing the parasitic coupling, special attention shall be paid to designing high- $Q$  resonators. Two other types of resonators along with the closed type shown in Figure 2 can be used. They are explained in A.4.

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**Figure 2 – Typical measurement apparatus for  $R_s$**

A reference line made of a semi-rigid cable shall be used to measure the full transmission power level, i.e. the reference level. This cable has a length equal to the sum of the two cables of the measurement apparatus. Semi-rigid cable with an outer diameter of 1,20 mm is recommended.

In order to minimize the measurement uncertainty, two superconductor films shall be set to be parallel to each other. To ensure that the two superconductor films remain in tight contact with the ends of the sapphire rod, without any air gap, both of the surfaces of the films and the ends of the rod shall be cleaned carefully.

### 5.3 Dielectric rods

Two dielectric rods with the same relative permittivity,  $\varepsilon'$ , and loss factor,  $\tan \delta$ , preferably cut from one cylindrical dielectric rod, are required. These two rods, standard dielectric rods, shall have the same diameter but different heights: one shall have height three times longer than the other.

It is preferable to use dielectric rods with low  $\tan \delta$  to achieve the requisite measurement uncertainty on  $R_s$ . Recommended dielectric rods are single-crystal sapphire rods with  $\tan \delta$  less than  $2 \times 10^{-7}$  at 77 K. Specifications on the sapphire rods are described in 7.1. In order to minimize the measurement error in  $R_s$  of the superconductor films, both ends of the sapphire rods shall be polished parallel to each other and perpendicular to the axis. Specifications for the sapphire rods are given in Clause 7.

The diameter and the heights of the standard sapphire rods shall be carefully designed so that the  $TE_{011}$  and  $TE_{013}$  modes do not couple to other TM, HE and EH modes, since the coupling between TE mode and other modes causes the degradation of unloaded  $Q$ . A design guideline for the standard sapphire rods is described in Clause A.5. Table 1 shows typical examples of dimensions of the standard sapphire rods for 12 GHz, 18 GHz, and 22 GHz resonance. In the  $R_s$  measurement at 22 GHz, the required film diameter can be set to 20 mm, and the measured  $Q_L$  is small, therefore the effect of the dielectric loss of sapphire rod can be reduced.

**Table 1 – Typical dimensions of pairs of single-crystal sapphire rods for 12 GHz, 18 GHz and 22 GHz**

| Frequency<br>GHz |                                   | Diameter, $d$<br>mm | Height, $h$<br>mm |
|------------------|-----------------------------------|---------------------|-------------------|
| 12               | Short rod ( $TE_{011}$ resonator) | $11,40 \pm 0,05$    | $5,70 \pm 0,05$   |
|                  | Long rod ( $TE_{013}$ resonator)  | $11,40 \pm 0,05$    | $17,10 \pm 0,05$  |
| 18               | Short rod ( $TE_{011}$ resonator) | $7,60 \pm 0,05$     | $3,80 \pm 0,05$   |
|                  | Long rod ( $TE_{013}$ resonator)  | $7,60 \pm 0,05$     | $11,40 \pm 0,05$  |
| 22               | Short rod ( $TE_{011}$ resonator) | $6,20 \pm 0,05$     | $3,10 \pm 0,05$   |
|                  | Long rod ( $TE_{013}$ resonator)  | $6,20 \pm 0,05$     | $9,30 \pm 0,05$   |

## 6 Measurement procedure

### 6.1 Specimen preparation

From uncertainty estimation, the film diameter shall be about three times larger than that of the sapphire rods. In this configuration, the increase in uncertainty of  $R_s$  due to the different radiation losses between  $TE_{011}$  and  $TE_{013}$  mode can be considered negligible, given the target relative combined standard uncertainty of 20 %. The film thickness shall be about two times larger than the magnetic-field penetration depth value at the maximum temperature in the measurement temperature range. If the film thickness is much less than two times the magnetic-field penetration depth, the measured  $R_s$  should mean the effective surface resistance.

Table 2 shows dimensions of the superconductor films recommended for the standard sapphire rods of 12 GHz, 18 GHz, and 22 GHz.

**Table 2 – Dimensions of superconductor film for 12 GHz, 18 GHz, and 22 GHz**

| c-cut single-crystal sapphire rod |                     | Superconductor film  |                            |
|-----------------------------------|---------------------|----------------------|----------------------------|
| Frequency<br>GHz                  | Diameter, $d$<br>mm | Diameter, $d'$<br>mm | Thickness<br>$\mu\text{m}$ |
| 12                                | $11,40 \pm 0,05$    | $> 35$               | $\cong 0,5$                |
| 18                                | $7,60 \pm 0,05$     | $> 25$               | $\cong 0,5$                |
| 22                                | $6,20 \pm 0,05$     | $> 20$               | $\cong 0,5$                |

In case of using closed type resonators, the dimensions of the superconductor films shall also be designed taking into account the dimension of the copper cylinder between the superconductor films. A design guideline for the dimension of the copper cylinder of the closed type resonator is described in Clause A.6.

## 6.2 Set-up

Set up the measurement equipment as shown in Figure 1. All of the measurement apparatus, standard sapphire rods, and superconductor films shall be kept in a clean and dry state as high humidity may degrade the unloaded  $Q$ -value. The specimen and the measurement apparatus shall be fixed in a temperature-controlled cryocooler. The specimen chamber shall be totally evacuated. The temperatures of the superconductor films and standard sapphire rods shall be measured by a diode thermometer, or a thermocouple. The temperatures of the upper and lower superconductor films and standard sapphire rods shall not differ by more than 0,5 K. This can be achieved by covering the measurement apparatus with aluminium foil or filling the specimen chamber with helium gas.

## 6.3 Measurement of reference level

The level of full transmission power (reference level) shall be measured first. Fix the output power of the synthesized sweeper below 10 mW because the measurement uncertainty depends on the measuring signal level. Connect the reference line of semi-rigid cable between the input and output connectors. Then, measure the transmission power level over the entire measurement frequency and temperature range. The reference level can change several decibels when temperature of the apparatus is changed from room temperature to the lowest measurement temperature. Therefore, the temperature dependence of the reference level must be taken into account.

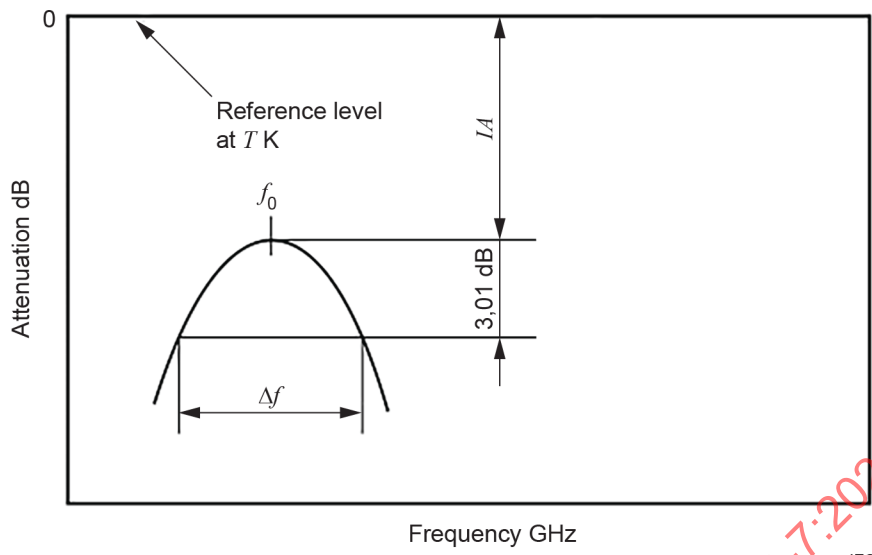


**Figure 3 – Insertion attenuation,  $IA$ , resonant frequency,  $f_0$ , and half power bandwidth,  $\Delta f$ , measured at  $T$  kelvin**

#### 6.4 Measurement of the frequency response of resonators

The temperature dependence of the  $R_s$  can be obtained through the measurements of resonant frequency,  $f_0$ , and unloaded quality factor,  $Q_u$ , for  $TE_{011}$  and  $TE_{013}$  resonators, which shall be measured as follows.

- Connect the measurement apparatus between the input and output connectors (Figure 1). Insert the standard short sapphire rod near the centre of the lower superconductor film and fix the distance between the rod and each of the loops of the semi-rigid cables to be equal to each other, so that this transmission-type resonator can be under-coupled equally to both loops. Put down the upper superconductor film gently to touch the top face of the rod. Be careful not to damage the surface of the superconductor films by excessive pressure. Evacuate and cool down the specimen chamber below the critical temperature.
- Find the  $TE_{011}$  mode resonance peak of this resonator at a frequency nearly equal to the designed value of  $f_0$ .
- Narrow the frequency span on the display so that only the resonance peak of  $TE_{011}$  mode can be shown (Figure 3). Confirm that the insertion attenuation,  $IA$ , of this mode is larger than 20 dB from the reference level, which depends strongly on the temperature.
- Measure the temperature dependence of  $f_0$  and the half power band width  $\Delta f$ . The loaded  $Q$ -value,  $Q_L$ , of the  $TE_{011}$  resonator is given by

$$Q_L = \frac{f_0}{\Delta f} \quad (1)$$

- The unloaded  $Q$ -value,  $Q_u$ , shall be extracted from the  $Q_L$  by at least one of the two following techniques.
  - One technique for extracting the unloaded  $Q$ -value involves measuring the insertion attenuation  $IA$ .  $Q_u$  is given by

$$Q_u = \frac{Q_L}{1 - A_t}, A_t = 10^{-IA[\text{dB}]/20} \quad (2)$$

The  $IA$  of each temperature is determined as follows. In the  $R_s$  measurement system shown in Figure 2, a semi-rigid cable is connected instead of the measurement apparatus, and the measurement system is short-circuited to determine the reference level. Measure the reference level at each temperature and use it to determine  $IA$  at each temperature.

This technique of using insertion attenuation assumes that the coupling on both sides of the resonator is identical. The coupling loops are difficult to fabricate, the orientation of the loop is difficult to control, and any movement of the sapphire rod during measurement is not known. These assembly-dependent effects are also temperature dependent. This potential asymmetry in coupling can result in large errors in calculating the coupling factor if the coupling is strong ( $IA < 10$  dB). If the coupling is weak enough ( $IA > 20$  dB), asymmetry in the coupling becomes less important.

- 2) Another technique for extracting the unloaded  $Q$ -value involves measuring the reflection scattering parameters at the resonant frequency of both sides of the resonator.

$$Q_u = Q_L (1 + \beta_1 + \beta_2) \quad (3)$$

$$\beta_1 = \frac{1 - |S_{11}|}{|S_{11}| + |S_{22}|} \quad (4)$$

$$\beta_2 = \frac{1 - |S_{22}|}{|S_{11}| + |S_{22}|} \quad (5)$$

In Equations (4) and (5),  $S_{11}$  and  $S_{22}$  are the reflection scattering parameters as shown in Figure 4, and are measured in linear units of power, not relative dB.  $\beta_1$  and  $\beta_2$  are the coupling coefficients.

This technique of using the reflection scattering parameters has two advantages. It does not require the additional step of calibration of the reference level and it gives a measurement of the coupling values for both sides of the resonator. This also has two disadvantages. It only works for a narrow band resonance (which is fortunately the case) and is limited by the dynamic range of the network analyzer in measuring the reflection coefficients [15] [16].

A combination of the two techniques is useful for a "double" check.

- f) The  $f_0$  and  $Q_u$  measured for this short rod are denoted as  $f_{01}$  and  $Q_{u1}$  for  $TE_{011}$  mode resonance. By slowly changing the temperature of the cryocooler the temperature dependence of  $f_{01}$  and  $Q_{u1}$  shall be measured.
- g) After the temperature dependence measurement of  $f_{01}$  and  $Q_{u1}$  is finished, the measurement apparatus shall be heated up to room temperature.
- h) Then, replace the  $TE_{011}$  resonator in the apparatus with the  $TE_{013}$  resonator at room temperature, cool down the apparatus to a temperature lower than the critical temperature, and measure the temperature dependence of  $f_0$  and  $Q_u$  of its  $TE_{013}$  resonance mode, denoted as  $f_{03}$  and  $Q_{u3}$ , in a similar way to the  $TE_{011}$  resonator case. When the length of the sapphire rod of the  $TE_{013}$  resonator is precisely three times longer than that of the  $TE_{011}$  resonator, the  $f_{03}$  of the  $TE_{013}$  resonator must coincide with  $f_{01}$  of the  $TE_{011}$  resonator. If carefully designed, the difference between  $f_{01}$  and  $f_{03}$  is usually very small ( $< 0,25$  %). We can consider that the  $f_0$  in equation (9) can be replaced by  $f_{01}$  or  $f_{03}$ .

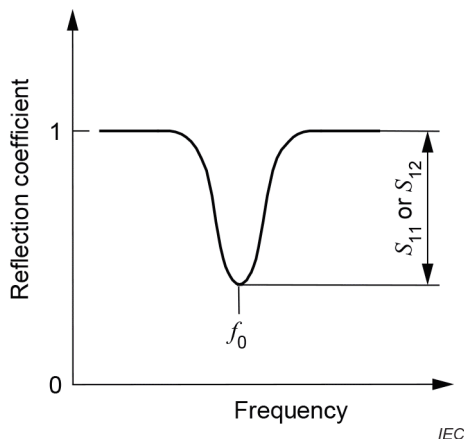


Figure 4 – Reflection scattering parameters ( $S_{11}$  and  $S_{22}$ )

### 6.5 Determination of surface resistance of the superconductor and $\varepsilon'$ and $\tan \delta$ of the standard sapphire rods

Calculate the temperature dependence of the  $R_s$  of the superconductor films, and  $\varepsilon'$  and  $\tan \delta$  of the standard sapphire rods using the temperature dependence of  $Q_{u1}$  and  $Q_{u3}$ .  $Q_{u1}$  and  $Q_{u3}$  can be calculated using equations (1) and (2). If the measured temperatures for  $Q_{u3}$  appear to be slightly different from those for  $Q_{u1}$ , interpolation can be used for preparing adjusted temperature values for the former at the same temperatures for the later. Equations (6) to (12) are established in the open type cavity, but when the superconductor film size is three times larger than sapphire rod diameter, these equations can be used for closed type cavity.

$$R_s = \frac{30\pi^2 \times 3}{(3-1)} \left( \frac{2h_0}{\lambda_0} \right)^3 \frac{\varepsilon' + W}{1+W} \left( \frac{1}{Q_{u1}} - \frac{1}{Q_{u3}} \right) \quad (6)$$

$$\varepsilon' = \left( \frac{\lambda_0}{\pi d} \right)^2 (u^2 + v^2) + 1 \quad (7)$$

$$\tan \delta = \frac{1 + \frac{W}{\varepsilon'}}{(3-1)} \left( \frac{3}{Q_{u3}} - \frac{1}{Q_{u1}} \right) \quad (8)$$

where

$$\lambda_0 = \frac{c}{f_0} \quad (9)$$

$$W = \frac{J_1^2(u) K_0(v) K_2(v) - K_1^2(v)}{K_1^2(v) J_1^2(u) - J_0(u) J_2(u)} \quad (10)$$

$$v^2 = \left( \frac{\pi d}{\lambda_0} \right)^2 \left[ \left( \frac{3\lambda_0}{2h_0} \right)^2 - 1 \right] \quad (11)$$

$$u \frac{J_0(u)}{J_1(u)} = -v \frac{K_0(v)}{K_1(v)} \quad (12)$$

In the equations,  $\lambda_0$  is the free space resonant wavelength,  $c$  is the speed of light in vacuum ( $c = 2,997\,9 \times 10^8$  m/s),  $h_0$  is the height of the short standard dielectric rod. The value  $u^2$  is given by the transcendental Equation (12) using the value of  $v^2$ , where  $J_n(u)$  is the Bessel function of the first kind, and  $K_n(v)$  is the modified Bessel function of the second kind. The derivations of the equations are described in Clause A.3.

Generally the thermal expansion coefficient of the rods must be known to determine the temperature dependence of their sizes. However, the thermal expansion effect of the sapphire rods can be neglected for the target relative standard uncertainty of  $R_s$  (20 %).

It is noted that the measured  $R_s$  means the effective surface resistance if the film thickness is less than two times the temperature-dependent penetration depth.

## 7 Uncertainty of the test method

### 7.1 Surface resistance

The surface resistance ( $R_s$ ) shall be determined from the  $Q$ -value measured with a dielectric resonator technique.

A vector network analyser as specified in Table 3 shall be used to record the frequency dependence of attenuation. The resulting record shall allow the determination of  $Q$  to a relative uncertainty of  $10^{-2}$ .

**Table 3 – Specifications for vector network analyzer**

|                           |              |
|---------------------------|--------------|
| Dynamic range of $S_{21}$ | above 60 dB  |
| Frequency resolution      | below 1 Hz   |
| Attenuation uncertainty   | below 0,1 dB |
| Input power limitation    | below 10 dBm |

The dielectric resonators shall be provided with two dielectric rods with low  $\tan \delta$  of less than  $2 \times 10^{-7}$  at 77 K and a radius less than 1/3 of the superconducting specimen's radius. The best candidate for the rods is sapphire as specified in Table 4. Term definitions in Table 4 are shown in Figure 5.

**Table 4 – Specifications for sapphire rods**

|                   |                                                                                    |
|-------------------|------------------------------------------------------------------------------------|
| Diameter          | $\pm 0,05$ mm                                                                      |
| Height            | $\pm 0,05$ mm                                                                      |
| Flatness          | below 0,005 mm                                                                     |
| Surface roughness | top and bottom surface: below 10 nm RMS<br>cylindrical surface: below 0,001 mm RMS |
| Perpendicularity  | within 0,1 degree                                                                  |
| Axis              | parallel to c-axis within $0,3^\circ$                                              |

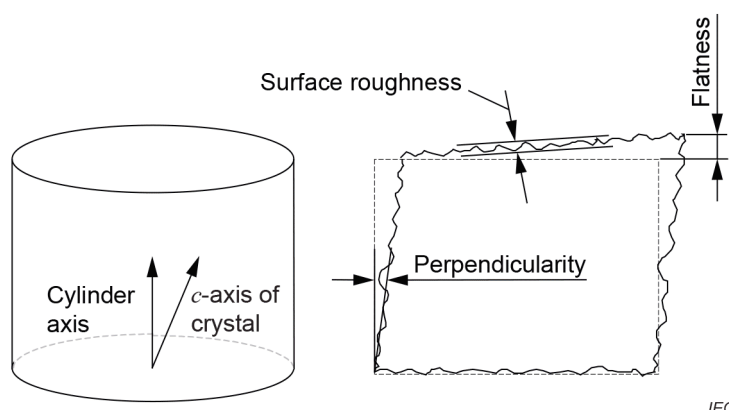


**Figure 5 – Term definitions in Table 4**

The technique as described assumes that single- and triple-height sapphire rods can be fabricated with the same  $\tan \delta$ . However, the variation of the  $\tan \delta$  between nominally identical rods, cut from the same boule and polished by the same technique, may be as large as two orders of magnitude. To date, the smallest variation in  $\tan \delta$  between nominally identical sapphire rods has been a factor of four. Therefore, the uncertainty in the measured  $\tan \delta$  is large. The variation of  $\tan \delta$  of the present sapphire rod causes an additional uncertainty up to at least 10 % in the surface resistance measurement. This limits the target uncertainty of the present technique at 5 %. If reproducibility of sapphire rods is improved, or a selection method for standard sapphire rods is established, a target uncertainty can be improved.

## 7.2 Temperature

The measurement apparatus is cooled down to the specified temperature by any means during testing. An easy choice would be to immerse the apparatus into a liquid cryogen. This technique is quick and simple and yields a known and stable temperature. Unfortunately, most HTS materials are damaged by the condensation of moisture that occurs when removing the sample from the cryogen. In addition, uncertainties generated by the presence of a gas/liquid mixture within the cavity, and the inability to measure  $R_s$  as a function of temperature support the use of other cooling methods. These limitations can be circumvented by the immersion of a vacuum can into a liquid cryogen. If the vacuum can is backfilled with gas, then rapid cooling and uniform temperatures occur. If heaters are attached to the apparatus, then the temperature dependence of the HTS material can be measured. A third and equally good choice is the use of a cryocooler. In this case, the resonator is under vacuum and cooled by conduction through the metallic package. Temperature gradients with the apparatus shall be avoided.

A cryostat shall be provided with the necessary environment for measuring  $R_s$  and the specimen shall be measured while in a stable and isothermal state. The specimen temperature is assumed to be the same as the sample holder temperature. The holder temperature shall be reported to an accuracy of  $\pm 0,5$  K, measured by means of an appropriate temperature sensor.

The difference between the specimen temperature and the holder temperature shall be minimized by using shields with good thermal conductivity.

## 7.3 Specimen and holder support structure

The support structure shall provide adequate support for the specimen. The two films shall be parallel and mechanically stable throughout the measurement, especially in a cryocooler and over a wide temperature range. The parallelism of the two films can be achieved by using a sapphire rod satisfying the specifications described in Table 4.

## 7.4 Specimen protection

Condensation of moisture and scratching of the film deteriorate superconducting properties. Some protection measures should be provided for the specimens. Polytetrafluoroethylene (PTFE) or polymethylmethacrylate (PMMA) coating does not affect the measurements, thus they can be used for protection. A coating material thickness of less than several micrometers is recommended.

## 7.5 Uncertainty of surface resistance measured by standard two-resonator method

For the dielectric resonance method,  $\tan \delta$  of the  $TE_{011}$  mode and  $TE_{013}$  mode sapphire rods are assumed to be absolutely equal. If  $\tan \delta$  of two sapphire rods is different, it is not possible to calculate the surface resistance using Equation (6). The effect of  $\tan \delta$  deviation on surface resistance was checked (see Annex B). Uncertainty in the microwave surface resistance of superconductors by dielectric resonator method depends on size, dielectric constant,  $\tan \delta$  of sapphire rods and uncertainty in measured  $Q$  of the resonator. The relative combined standard uncertainty is less than 20 % (see Annex B).

## 8 Test report

### 8.1 Identification of test specimen

The test specimen shall be identified, if possible, by the following:

- name of the manufacturer of the specimen;
- classification and/or symbol;
- lot number;
- chemical composition of the thin film and the substrate;
- thickness and roughness of the thin film;
- manufacturing process technique.

### 8.2 Report of $R_s$ values

The  $R_s$  values at the measured frequency, and that scaled to 10 GHz, together with their corresponding  $f_{01}$ ,  $f_{03}$ ,  $Q_{u1}$ ,  $Q_{u3}$ ,  $IA$  and/or  $(\beta_1, \beta_2)$ ,  $\varepsilon'$  and  $\tan \delta$  values, and their temperature dependence shall be reported.

### 8.3 Report of test conditions

The following test conditions shall be reported:

- test frequency and resolution of frequency;
- test maximum RF power;
- test temperature, accuracy of temperature and temperature difference in two plates;
- sample history with temperature variation.

## Annex A (informative)

### Additional information relating to Clauses 1 to 8

#### A.1 Scope

##### A.1.1 General

The establishment of the standard measurement method is needed to evaluate film quality of HTS films having low surface resistance,  $R_s$ , values such as 0,1 mΩ at 10 GHz. Several resonance methods as shown in Figure A.1 have been proposed so far to measure them in microwave and millimetre wave range. These resonator structures are grouped into six types (see A.1.2 to A.1.7).

##### A.1.2 Cylindrical cavity method [10] [17]

Figure A.1 a) shows a cavity structure using the  $TE_{011}$  mode, which is constructed from a copper cylinder and two HTS films. In the microwave range below 30 GHz, the  $R_s$  measurement precision of this method is rather low, because the  $R_s$  value of the copper cylinder is 100 times higher than that of HTS films. This method is suitable in the millimetre wave region, because the  $R_s$  values increase with  $f^2$  of HTS films and  $f^{1/2}$  for copper.

##### A.1.3 Parallel-plates resonator method [18] [19]

Figure A.1 b) shows a structure of a parallel-plates resonator using the  $TM_{nm0}$  mode, which is constructed by inserting a thin low loss dielectric spacer between two rectangular HTS films. This method offers the possibility of measuring extremely small  $R_s$  values, but from the viewpoint of the absolute estimation of  $R_s$  there are some problems, such as low measurement precision of thickness and  $\tan \delta$  of the dielectric spacer, uncertain estimations of radiation loss and an air-gap effect between the plates and the spacer, and critical excitation technique of the resonance modes.

##### A.1.4 Microstrip-line resonance method [20] [21]

Figure A.1 c) shows a structure of a microstrip-line resonator using the  $TE_{0mp}$  mode, which is fabricated by a pattern fabrication process and is close to the real microwave passive devices. However, this method is not suitable for the HTS film estimation because it includes an uncertain influence of the pattern fabrication process.

##### A.1.5 Dielectric resonator method [22] [23] [24] [25]

Figure A.1 d) shows a structure of a dielectric resonator using a  $TE_{011}$  mode, where a low loss sapphire rod is placed between two parallel HTS films. For the  $TE_{0mp}$  mode, we can eliminate the air-gap effects, because the normal component of electric field does not exist on the HTS films. In this method the  $R_s$  values of the HTS films have been measured by ignoring the effect of  $\tan \delta$  on the assumption of  $\tan \delta < 1 \times 10^{-8}$  for single-crystal sapphire [24]. However, the  $\tan \delta$  values measured for sapphire at 10 GHz and near 50 K, as is well known, take values between  $10^{-6}$  to  $10^{-8}$  due to quantity of lattice defect. Therefore, preparation of very-low-loss sapphire rods with  $\tan \delta < 2 \times 10^{-7}$  (at 80 K and at 10 GHz) is essential for this method.

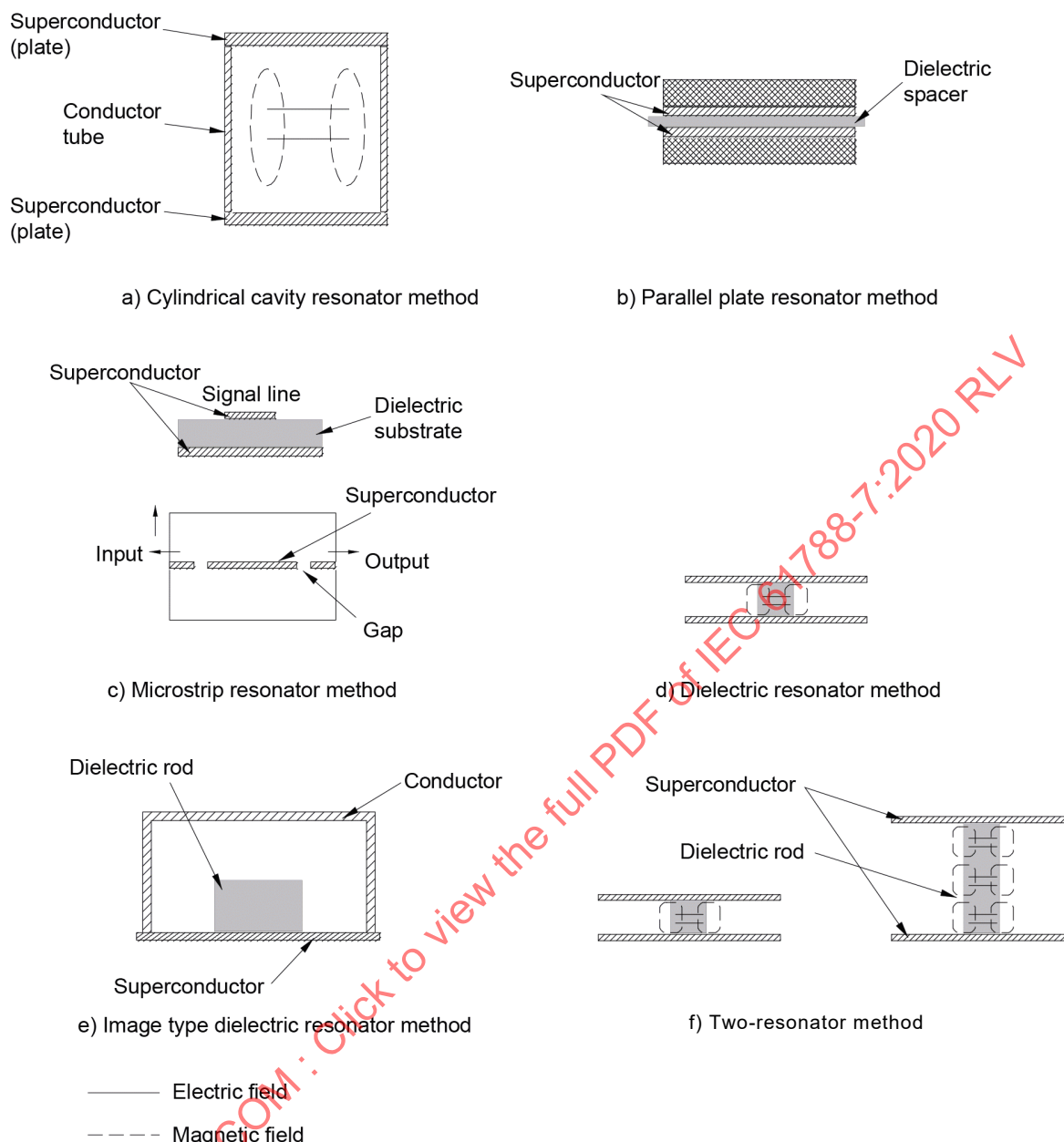


**Figure A.1 – Schematic configuration of several measurement methods for the surface resistance**

#### A.1.6 Image-type dielectric resonator method [26] [27]

Figure A.1 e) shows a structure of an image-type dielectric resonator using the  $TE_{01\delta}$  mode. This structure is available to measure only one HTS film. However, preparation of very-low-loss sapphire rods is essential also for this method, because the  $R_s$  is measured by ignoring the effect of  $\tan \delta$ .

In an improved image-type sapphire rod resonator method,  $R_s$  can be obtained with simple calibration process. In this method, the exact  $R_s$  of a single HTS film can be obtained by one measurement under the 20 % limitation of variation coefficient.

### A.1.7 Two-resonator method [28] [29]

In this method, two sapphire rod resonators with the same  $\tan \delta$  values are used; one is a  $TE_{011}$  mode resonator and the other is a  $TE_{013}$  mode resonator, as shown in Figure A.1 f). Similarly to the dielectric resonator method, the air-gap effects can be eliminated in this method. The  $\tan \delta$  value of the sapphire rods and the  $R_s$  value of the HTS films can be determined separately from the resonant frequencies and unloaded  $Q$ -values measured for these resonators by using simple formulas derived from the rigorous analysis based on the mode matching method. Thus this method can eliminate the ambiguity of the  $\tan \delta$  affected to the  $R_s$  measurements. Actually, the results of  $R_s$  measured for six YBCO films with  $R_s = 0,1 \text{ m}\Omega$  at 12 GHz have verified that the measurement uncertainty of 20 % is realized by this method [22]. However, if there is a difference between two  $\tan \delta$  values ( $\Delta \tan \delta$ ), the uncertainty in  $R_s$  due to  $\Delta \tan \delta$  must be taken into account. This effect can be estimated from results of the inter-laboratory round robin test of the same HTS films by this method. Recently, the  $R_s$  of YBCO film was measured three times and its deviation was less than 20 % (see Figure A.11).

As a result of comparisons among the six methods described above, the two-resonator method is recommended as the standard measurement method of  $R_s$  of HTS films, due to the following two advantages:

- absolute measurement of  $R_s$  is possible;
- the numerical treatment is simple and easy.

## A.2 Requirements

Higher measurement frequencies are desirable for determination of lower  $R_s$  because  $R_s$  of superconductor films increases with the frequency according to the  $f^2$  rule. The size of the resonators also can be made smaller by using higher measurement frequencies. However, it becomes difficult to set up a microwave measurement system as the measurement frequency becomes higher.

For the measurement temperatures of below 10 K or above 80 K, this test method is sufficiently applicable, where some new cooling techniques may be required.

## A.3 Theory and calculation equations

Figure A.2 shows the configuration of the  $TE_{0mn}$  mode resonator, which is used to eliminate the air-gap effects. A cylindrical dielectric rod with diameter,  $d$ , and height,  $h$ , is short-circuited at both ends by surfaces of two parallel superconductor films deposited on dielectric substrates with diameter,  $d'$ , thus constituting a resonator. These superconductor films are required to have the same value of  $R_s$ . The value of  $R_s$  is calculated from the measured resonant frequency  $f_0$  and unloaded quality factor  $Q_u$  for the  $TE_{0mn}$  resonance mode. When the two superconductor films have different values of  $R_s$ , the measured  $R_s$  value corresponds to the average value of these two films.

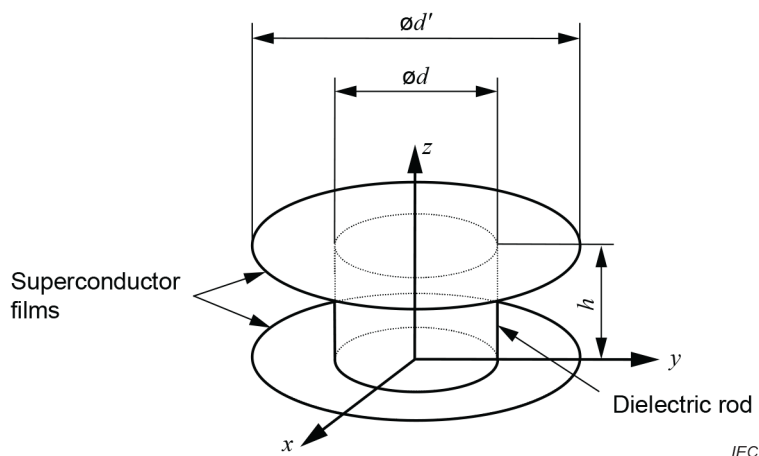


**Figure A.2 – Configuration of a cylindrical dielectric rod resonator short-circuited at both ends by two parallel superconductor films deposited on dielectric substrates**

The value of  $R_s$  is given by [25]

$$R_s = \frac{1}{B} \left( \frac{A}{Q_u} - \tan \delta \right) \quad (\text{A.1})$$

where

$$A = 1 + \frac{W}{\epsilon'} \quad (\text{A.2})$$

$$B = p^2 \left( \frac{\lambda_0}{2h} \right)^3 \frac{1+W}{30\pi^2 \epsilon'}, p = 1, 2, \dots, \quad (\text{A.3})$$

$$\lambda_0 = \frac{c}{f_0} \quad (\text{A.4})$$

$$W = \frac{J_1^2(u)}{K_1^2(v)} \frac{K_0(v)K_2(v) - K_1^2(v)}{J_1^2(u) - J_0(u)J_2(u)} \quad (\text{A.5})$$

$$v^2 = \left( \frac{\pi d}{\lambda_0} \right)^2 \left[ \left( \frac{3\lambda_0}{2h} \right)^2 - 1 \right] \quad (\text{A.6})$$

$$u \frac{J_0(u)}{J_1(u)} = -v \frac{K_0(v)}{K_1(v)} \quad (\text{A.7})$$

In Equations (A.1) and (A.2),  $\varepsilon'$  and  $\tan \delta$  are the relative permittivity and the loss factor of the dielectric rod, respectively. In Equations (A.3) and (A.4),  $\lambda_0$  is the free space resonant wavelength, and  $c$  is the speed of light in vacuum ( $c = 2,9979 \times 10^8$  m/s). The function  $W/\varepsilon'$  equals the ratio of electric-field energy stored outside to that stored inside the dielectric rod. If all of the electric field is concentrated inside the dielectric rod, the value  $W$  equals zero.

The value  $u^2$  is given by the transcendental Equation (A.7) using the value of  $v^2$ , where  $J_n(u)$  is the Bessel function of the first kind and  $K_n(v)$  is the modified Bessel function of the second kind. For any value of  $v$ , the  $m$ -th solution  $u$  exists between  $u_{0m}$  and  $u_{1m}$ , where  $J_0(u_{0m}) = 0$  and  $J_1(u_{1m}) = 0$ . The first solution ( $m = 1$ ), which is used for easy mode identification, is shown in Figure A.3 by curve (A). The computed result of the  $W$ - $v$  relation for  $m = 1$  of  $TE_{01p}$  resonance mode is shown in Figure A.3 by curve (B).

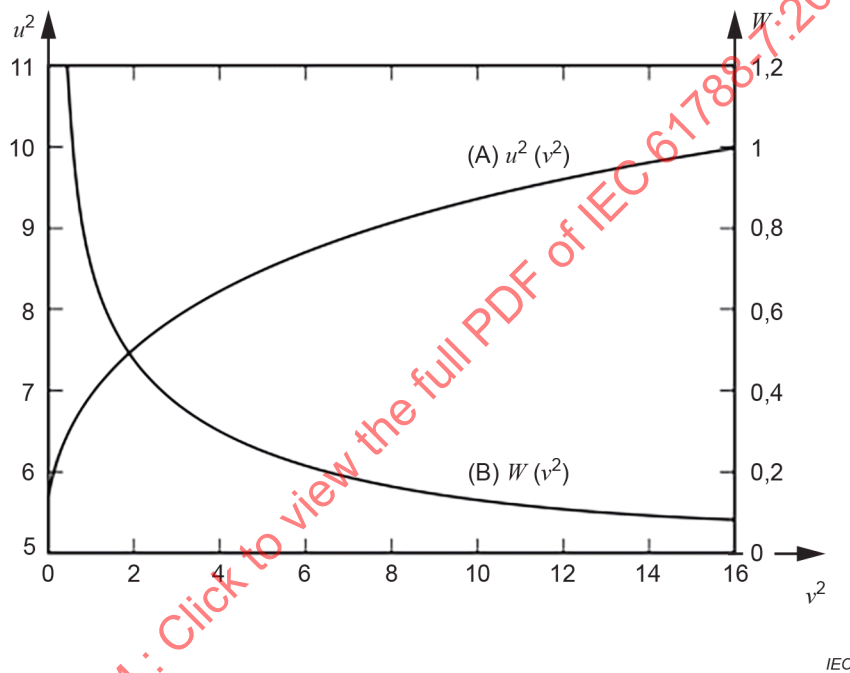


**Figure A.3 – Computed results of the  $u$ - $v$  and  $W$ - $v$  relations for  $TE_{01p}$  mode**

The value of  $\varepsilon'$  is given by

$$\varepsilon' = \left( \frac{\lambda_0}{\pi d} \right)^2 (u^2 + v^2) + 1 \quad (\text{A.8})$$

using the value of  $v^2$  and  $u^2$ .

In the two-resonator method, a pair of dielectric rods, which are called "standard dielectric rods", are used. These two rods have the same diameter but have different heights. The rod heights are such that one rod is  $p$  times the height of the other;  $p$  is commonly set equal to three. They are required to have the same values of  $\varepsilon'$  and  $\tan \delta$ .

Figure A.4 shows the configuration of the standard dielectric rods in the case of  $p = 3$ . To avoid confusion, the height of the short standard dielectric rod is denoted by  $h_0$ . Each resonator is called "TE<sub>011</sub> resonator" and "TE<sub>013</sub> resonator", respectively. The same superconductor films are used in these resonators. The values of  $f_0$  and  $Q_u$  for the TE<sub>011</sub> mode are measured using the TE<sub>011</sub> resonator, and those for the TE<sub>01p</sub> mode are measured using the TE<sub>01p</sub> resonator. We denote the  $f_0$  and  $Q_u$  for each resonator by using the subscripts 1 and  $p$ , respectively:  $f_{01}$  and  $Q_{u1}$  for TE<sub>011</sub> resonator, and  $f_{0p}$  and  $Q_{up}$  for TE<sub>01p</sub> resonator.

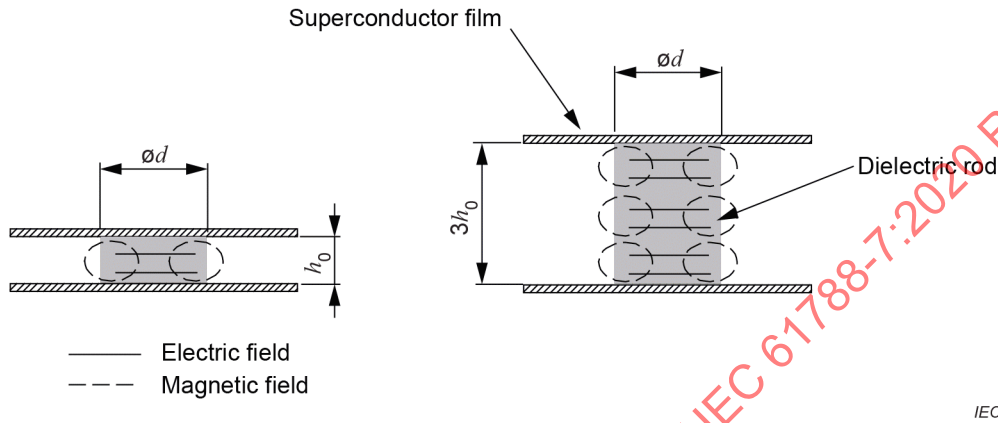


**Figure A.4 – Configuration of standard dielectric rods for measurement of  $R_s$  and  $\tan \delta$**

The value of  $\tan \delta$  is given from the measured values of  $Q_u$ . When the TE<sub>01p</sub> resonator is precisely  $p$  times longer than the TE<sub>011</sub> resonator,  $f_{0p}$  coincides with  $f_{01}$ . However,  $Q_{up}$  is higher than  $Q_{u1}$  according to the different magnitude of the electric field energy stored in the two resonators. Because both dielectric rods are short-circuited at both ends by the same superconductor films, Equation (A.1) yields

$$\tan \delta = \frac{A}{(3-1)} \left( \frac{3}{Q_{up}} - \frac{1}{Q_{u1}} \right) \quad (\text{A.9})$$

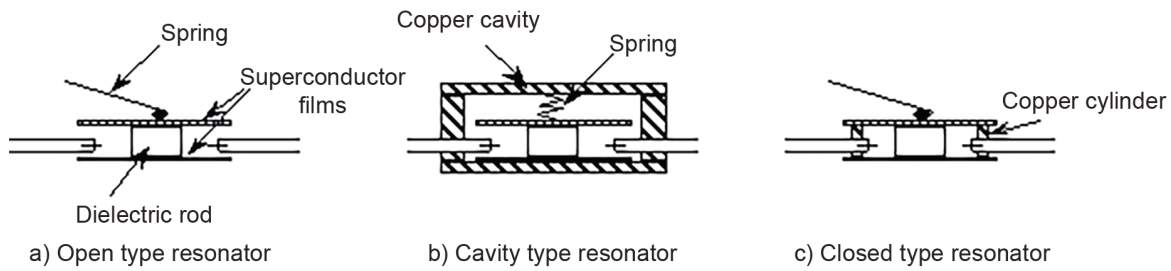
As an alternative method, the value of  $R_s$  of superconductor films can be directly measured by

$$R_s = \frac{30\pi^2 \times 3}{(3-1)} \left( \frac{2h_0}{\lambda_0} \right)^3 \frac{\varepsilon' + W}{1+W} \left( \frac{1}{Q_{u1}} - \frac{1}{Q_{up}} \right) \quad (\text{A.10})$$

where Equation (A.10) is derived by substituting Equation (A.9) into Equation (A.1).

#### A.4 Apparatus

Unwanted parasitic coupling to the other mode reduces the high  $Q$ -value of the TE mode resonator. For suppressing the parasitic coupling, special attention is paid to design high  $Q$ -value resonators. Three types of resonators are proposed and shown in Figure A.5.



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**Figure A.5 – Three types of dielectric resonators**

- a) Open type resonator: a low loss dielectric rod is placed between two parallel superconductor films. Two semi-rigid cables for the RF input and output magnetic dipole coupling are attached on both sides of the resonator. In this configuration, the vertical position of the coupling cables should be carefully designed so as to prevent the radiation loss propagating along the coupling cables, which degrades the high  $Q$ -value of the  $TE_{0mp}$  mode and causes the increase in error for the  $R_s$  measurements. The coupling cables should be set as close as possible to the lower superconductor film.
- b) Cavity type resonator: the open type resonator shown in a) is placed in a conductor (copper) cavity.
- c) Closed type resonator: conductor (copper) cylinder is put between the superconductor films. In this configuration, the radiation loss along the coupling cable is strongly blocked by the copper cylinder. The vertical position of the coupling cables ( $z$ ) at the highest  $z$ -axis magnetic field component ( $H_z$ ), i.e.  $z = h/2$ , is recommended.

The measuring apparatus on the cryocooler is protected from mechanical and thermal disturbances, and installed in an X-Y and/or Z axial manipulator for adjusting sample positions in the range of approximately  $\pm 1$  mm.

A loop length of the antenna is designed on the basis of the quarter-wavelength rule for achieving the maximum measuring sensitivity.

## A.5 Dimensions of the standard sapphire rods

Figure A.6 and Figure A.7 show the mode charts for designing the  $TE_{011}$  and  $TE_{013}$  mode resonators, respectively, short-circuited at both ends by parallel superconductor films, in which a uniaxial-anisotropic characteristic of the relative permittivity of the sapphire rod is taken into consideration [28].  $\varepsilon_z$  is the relative permittivity in the direction of the  $c$ -axis,  $\varepsilon_r$  is that in the plane perpendicular to the  $c$ -axis,  $d$  is the diameter of the sapphire rod,  $h$  is the height of the sapphire rod, and  $\lambda_0$  is the free space resonant wavelength. As shown in Figure A.6 and Figure A.7,  $TE_{013}$  resonance mode is apt to be affected by TM or HE mode in comparison with  $TE_{011}$  resonance mode. Since the coupling between TE mode and other modes causes the degradation of unloaded  $Q$ , the  $(d/h)$  of the sapphire rods shall be selected so as to avoid the unwanted couplings.

As shown in Figure A.7, the value  $(d/h)^2$  for the  $TE_{013}$  resonator is selected from 0,24 to 0,46 in order that the  $TE_{013}$  resonance mode is not affected by the other modes. This value  $(d/h)^2 = 0,24$  to 0,46 leads to a value of  $(d/h)^2 = 2,2$  to 4,1 for the  $TE_{011}$  resonator. The  $TE_{011}$  resonance mode does not also couple with other modes when the value  $(d/h)^2$  is in the region of 2,2 to 4,1 as shown in Figure A.6.

As the resonant frequency of TE mode is a function of relative permittivity and dimensions of the sapphire rod, its diameter and height are selected so that the desired  $f_0$  is obtained.

From the curve of TE<sub>011</sub> mode in Figure A.6, the value of  $\varepsilon_r (d/\lambda_0)^2$  can be determined for each  $(d/h)^2$  value. When the value  $(d/h)^2$  equals 4,0, for example, the value of  $\varepsilon_r (d/\lambda_0)^2$  equals 1,92. Thus, the resonant frequency of TE<sub>011</sub> mode for the sapphire rod with dimension of  $(d/h)^2 = 4,0$  is calculated from Equation (A.11) by specifying  $d$  and  $\varepsilon_r$  of the sapphire rod:

$$\varepsilon_r (d / \lambda_0)^2 = \varepsilon_r (d \times f_0 / c)^2 = 1,92 \quad (\text{A.11})$$

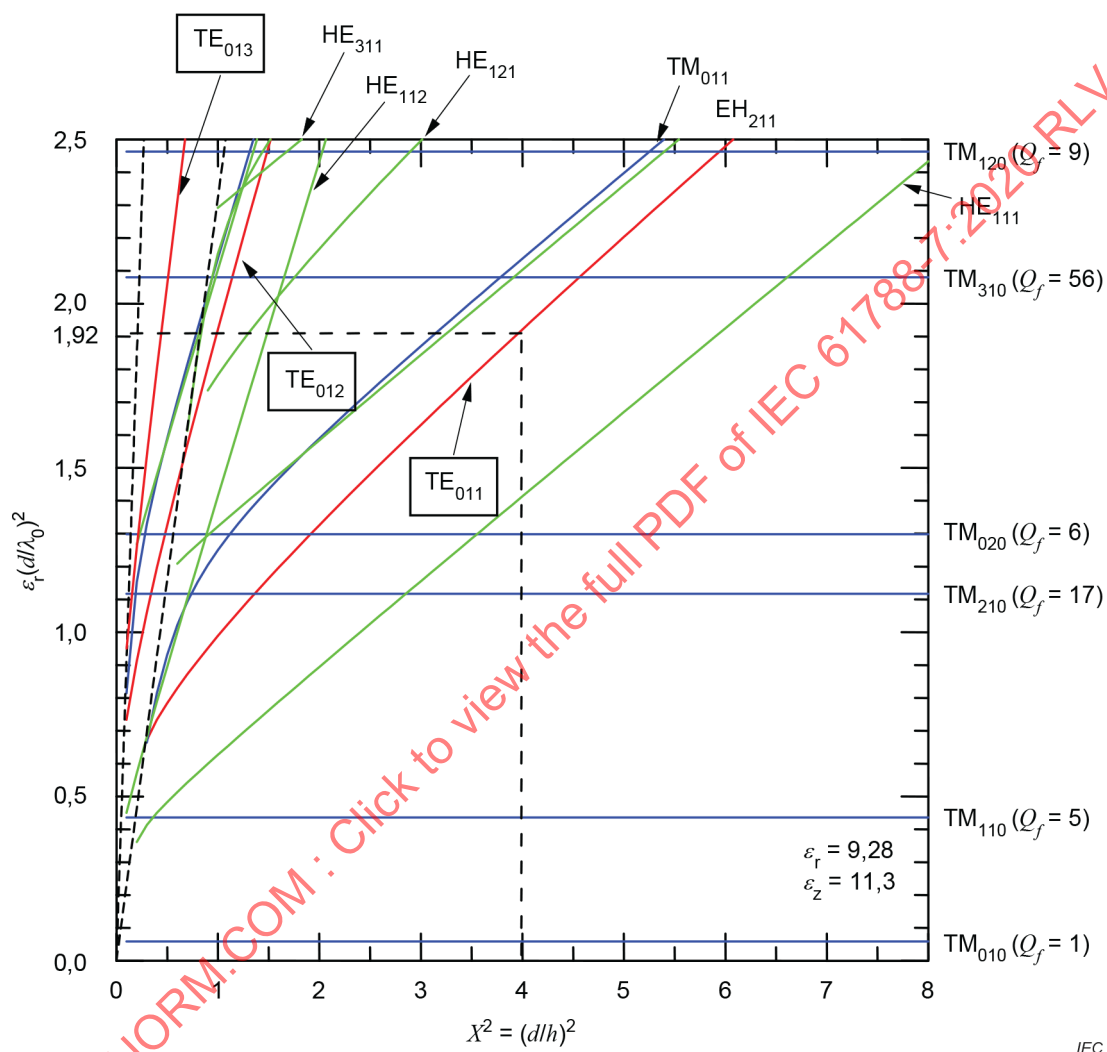


**Figure A.6 – Mode chart to design TE<sub>011</sub> resonator short-circuited at both ends by parallel superconductor films [28]**

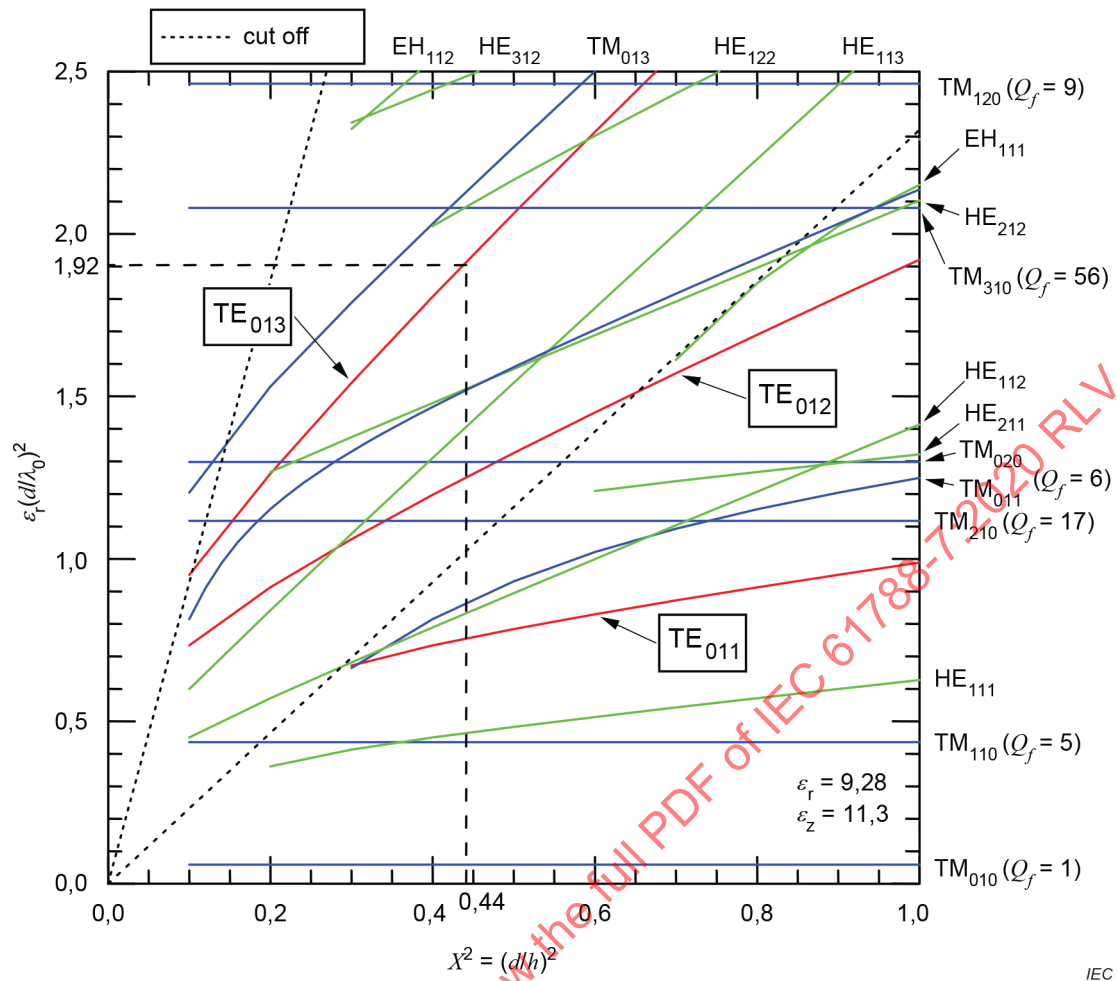


**Figure A.7 – Mode chart to design TE<sub>013</sub> resonator short-circuited at both ends by parallel superconductor films [28]**

## A.6 Dimension of the closed type resonator

In the closed type resonator, a copper cylinder is put between the superconductor films and a sapphire rod is placed in the center of the copper cylinder (Figure A.5 c)). The resonant frequency of each mode changes with the inner diameter of the copper cylinder,  $D$ . Therefore,  $D$  shall be selected so as to avoid the unwanted coupling with the other modes. In Figure A.8 and Figure A.9, mode charts of the closed type resonators are shown for the short sapphire rod ( $(d/h)^2 = 4$ ) and the long sapphire rod ( $(d/h)^2 = 0.44$ ), respectively, as a function of  $S = D/d$  [28]. The ranges of  $S$  to separate the TE<sub>011</sub> and the TE<sub>013</sub> modes simultaneously from the others are  $S = 1.8$  to  $2.8$ ,  $3.8$  to  $4.1$  and  $4.8$  to  $5.2$ . The value of  $S = D/d = 4$  is recommended because of the ease with which it can be treated.

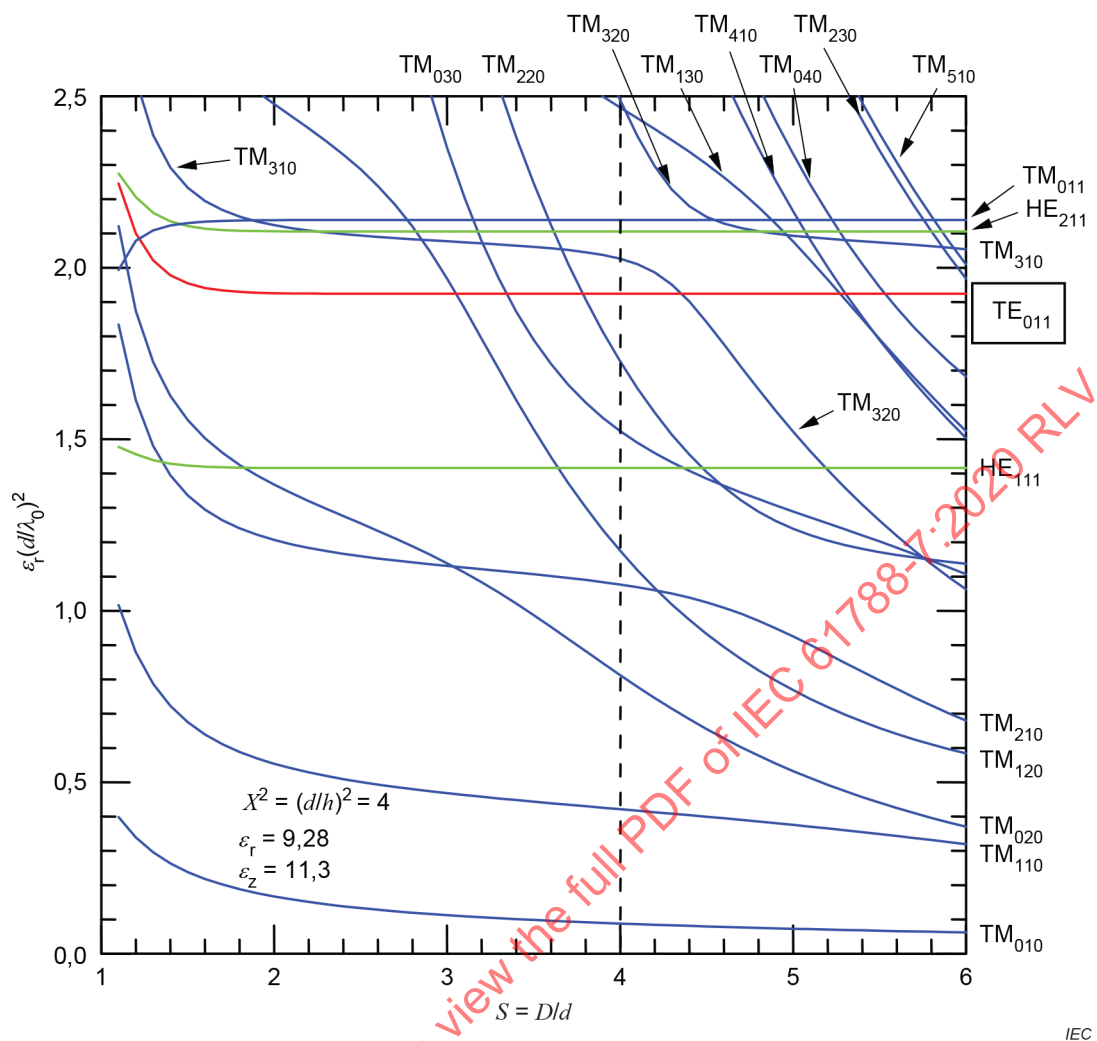


Figure A.8 – Mode chart for TE<sub>011</sub> closed-type resonator [28]

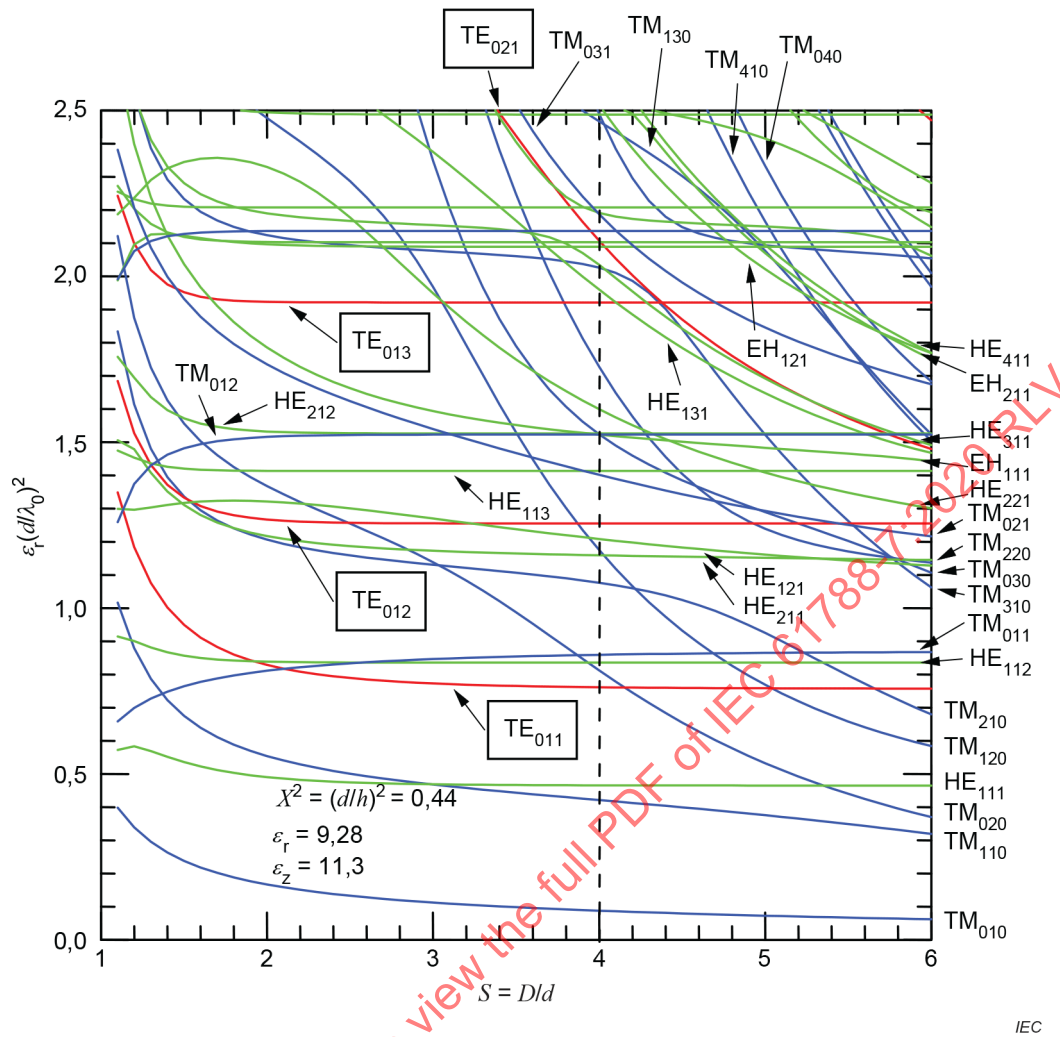


Figure A.9 – Mode chart for TE<sub>013</sub> closed-type resonator [28]

## A.7 Sapphire rod reproducibility

Knowing the value of  $\tan \delta$  of the sapphire rod is a difficult problem. One approach based on the single- and triple-height rods involves the selection of a standard rod for each type. The first step is to compare a large number of sapphire rods by measuring them in a single HTS/sapphire resonator. The sapphire rod with the highest unloaded  $Q$ -value is the temporary label of standard. This procedure is repeated for a set of triple-height rods. The “standard” single- and triple-height rods are then used as described above to obtain  $\tan \delta$ . The electrical properties,  $\epsilon'$  and  $\tan \delta$ , of other rods can then be calibrated by a direct comparison with these standard rods. Using a calibrated single-height rod, it is then possible to extract the  $R_s$  values of superconductor films under test.

## A.8 Test results

Figure A.10 shows the temperature-dependent  $R_s$  of a YBCO film with a thickness of 500 nm and size of 25 mm square. The YBCO film was formed on MgO substrate by a co-evaporation method. The measurement was carried out at 21,8 GHz, which was converted to 10 GHz by the  $f^2$  rule.

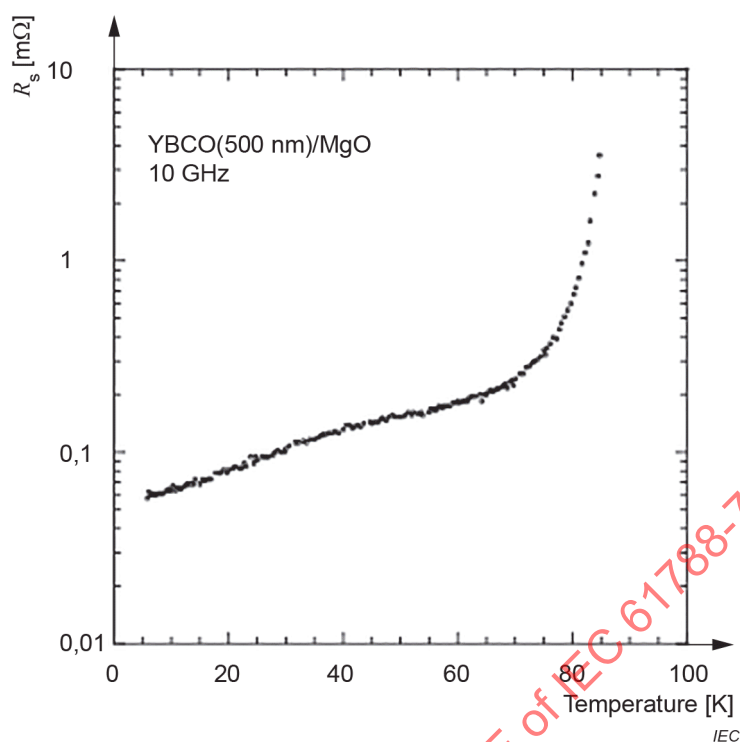


**Figure A.10 – Temperature-dependent  $R_s$  of YBCO film with a thickness of 500 nm and size of 25 mm square**

### A.9 Reproducibility of measurement method

In order to evaluate the reproducibility of the surface resistance measurement,  $R_s$  of the same sample was measured three times and the variation of  $R_s$  was examined. The sample was reset to the measurement cavity each time. Figure A.11 shows the results. Measurement was performed at a frequency of 21,8 GHz and converted to 10 GHz according to the  $f^2$  rule [30]. The variation in  $R_s$  was within 10 % in the temperature range of 10 K to 80 K.

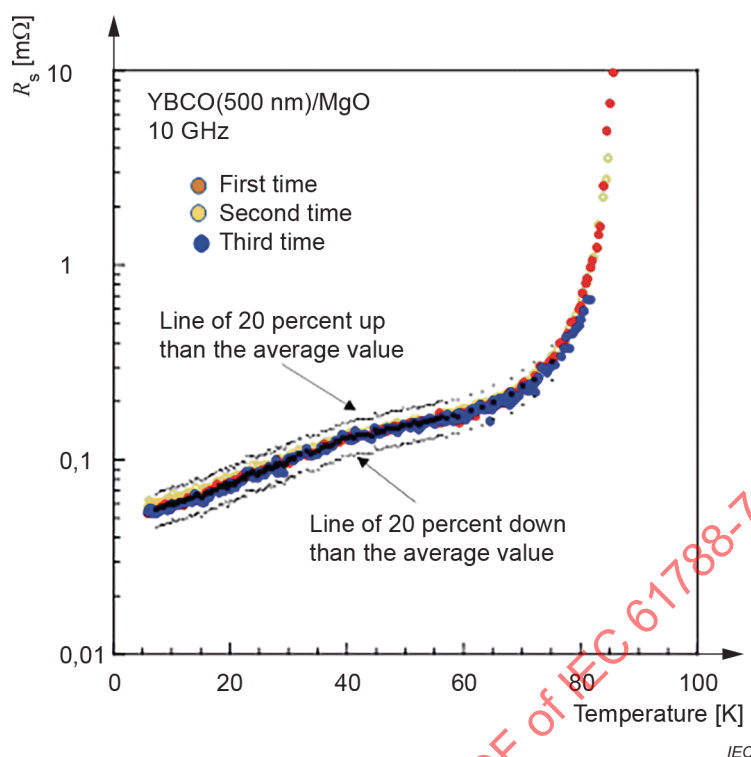


**Figure A.11 – Temperature dependent  $R_s$  of YBCO film when  $R_s$  was measured three times**

From the results, the standard deviation of each temperature can be calculated and its values are shown in Table A.1.

**Table A.1 – Standard deviation of the surface resistance calculated from the results of Figure A.11**

| Temperature (K)        | 20   | 40   | 60   | 80  |
|------------------------|------|------|------|-----|
| Standard deviation (%) | 0,32 | 0,23 | 0,90 | 6,9 |

#### A.10 $\tan \delta$ deviation effect of sapphire rods on surface resistance

For the two-resonator method,  $\tan \delta$  of the  $TE_{011}$  mode and  $TE_{013}$  sapphire rods are assumed to be absolutely equal. If  $\tan \delta$  of the two sapphire rods is different, it is not possible to calculate the surface resistance using Equation (6). Therefore, it is necessary to check the effect of  $\tan \delta$  deviation on surface resistance.  $\tan \delta$  of the high-purity sapphire rod used for the standard surface resistance measurement is extremely small, less than  $2 \times 10^{-7}$  [22]. Using such a sapphire rod, uncertainty in the surface resistance is quite small; however, if sapphire rods with a large  $\tan \delta$  are used, uncertainty in the surface resistance increases.  $\tan \delta_1$  of the sapphire rod for  $TE_{011}$  mode is assumed to be  $2 \times 10^{-7}$  and  $\tan \delta_3$  of the sapphire rod for  $TE_{013}$  mode changes according to that value. The difference in  $\tan \delta$  of the two sapphire rods is defined as in Equation (A.12) and the change in surface resistance as in Equation (A.13).

$$x = \frac{\tan \delta_1 - \tan \delta_3}{\tan \delta_1} \times 100 \quad [\%] \quad (\text{A.12})$$

$$y = \frac{R_s(x) - R_s(0)}{R_s(0)} \quad (\text{A.13})$$

$R_s$  can be calculated using Equation (A.14) when  $\tan \delta_1$  and  $\tan \delta_3$  are different. The relationship between  $x$  and  $y$  is shown in Table A.2. When the difference in  $\tan \delta$  of the two sapphire rods exceeds  $\pm 50$  %, the change in surface resistance exceeds  $\pm 18$  %.

$$R_s = \frac{1}{B_1} \left( \frac{A_1}{Q_{u1}} - \tan \delta_1 \right) = \frac{1}{B_3} \left( \frac{A_3}{Q_{u3}} - \tan \delta_3 \right) \quad (\text{A.14})$$

$$A_p = 1 + \frac{W}{\varepsilon_p} \quad (\text{A.15})$$

$$B_p = p^2 \left( \frac{\lambda_0}{2h_p} \right)^3 \frac{1+W}{30\pi^2 \varepsilon_p}, (p=1,3) \quad (\text{A.16})$$

$$W = \frac{J_1^2(u) K_0(v) K_2(v) - K_1^2(v)}{K_1^2(v) J_1^2(u) - J_0(u) J_2(u)} \quad (\text{A.17})$$

$$v_0^2 = \left( \frac{\pi d_0}{\lambda_0} \right)^2 \left[ \left( \frac{\lambda_0}{2h_0} \right)^2 - 1 \right] \quad (\text{A.18})$$

$$u_0 \frac{J_0(u_0)}{J_1(u_0)} = -v_0 \frac{K_0(v_0)}{K_1(v_0)} \quad (\text{A.19})$$

**Table A.2 – Relationship between  $x$ , defined by Equation (A.12), and  $y$ , defined by Equation (A.13)**

| $x$ (%) | -50  | -40  | -30  | -20 | -10 | 0 | +10  | +20  | +30   | +40   | +50   |
|---------|------|------|------|-----|-----|---|------|------|-------|-------|-------|
| $y$ (%) | 18,0 | 14,4 | 10,8 | 7,2 | 3,6 | 0 | -3,6 | -7,2 | -10,8 | -14,4 | -18,0 |

## Annex B (informative)

### Evaluation of relative combined standard uncertainty for surface resistance measurement

#### B.1 Practical surface resistance measurement

A superconductor shows a significantly increased surface resistance when irradiated by a high frequency current in the microwave range. There are several methods for measuring surface resistance, but the dielectric resonator method can measure surface resistance the most accurately. The method is described in Annex A. Figure B.1 shows these two resonators used to measure the frequency characteristics of  $TE_{011}$  and  $TE_{013}$  modes.

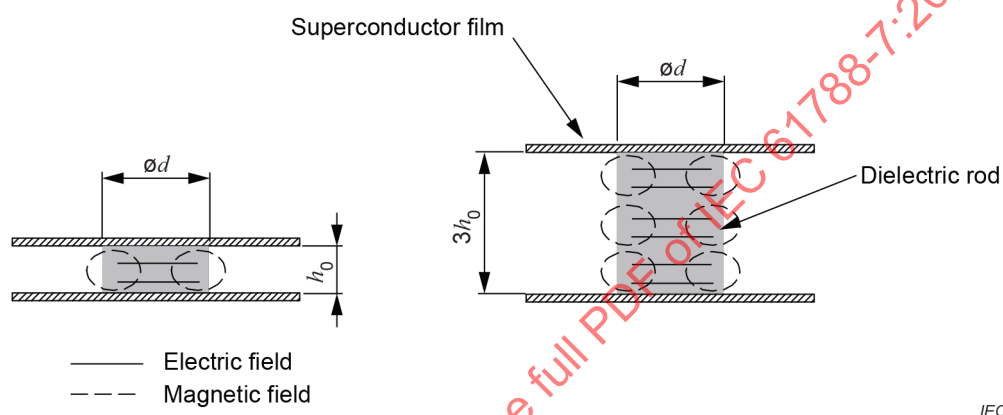


**Figure B.1 – Schematic diagram of  $TE_{011}$  and  $TE_{013}$  mode resonance**

Figure B.2 shows the typical frequency characteristics of  $TE_{011}$  mode resonance.  $Q_{L1}$  is determined using the results of this measurement and  $Q_{u1}$  is calculated using Equation (B.2).

$$Q_{L1} = \frac{f_0}{\Delta f} \quad (B.1)$$

$$Q_{u1} = \frac{Q_{L1}}{1 - A_t}, A_t = 10^{-IA[\text{dB}]/20} \quad (B.2)$$

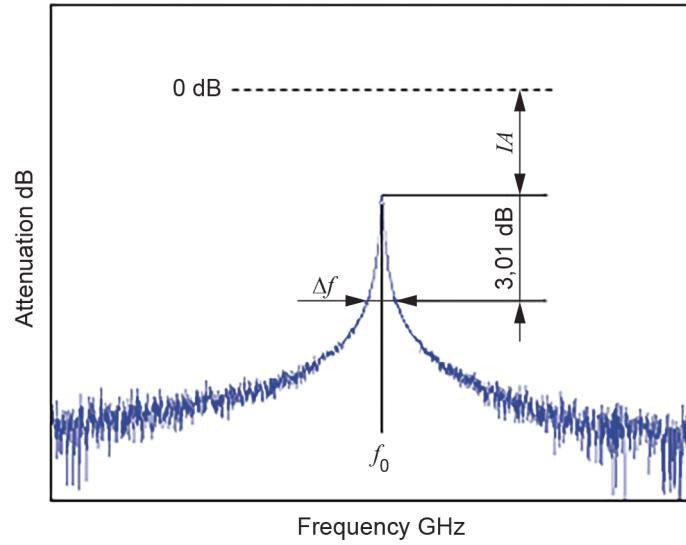


Figure B.2 – Typical frequency characteristics of TE<sub>011</sub> mode resonance

## B.2 Determination of surface resistance of the superconductor

The microwave surface resistance of the superconductor is obtained from Equations (B.3) to (B.8).

$$R_s = \frac{30\pi^2 \times 3}{3-1} \left[ \frac{2h_0}{\lambda_0} \right]^3 \frac{\varepsilon' + W}{1+W} \left[ \frac{1}{Q_{u1}} - \frac{1}{Q_{u3}} \right] \quad (\text{B.3})$$

$$\varepsilon' = \left( \frac{\lambda_0}{\pi d} \right)^2 (u^2 + v^2) + 1 \quad (\text{B.4})$$

$$W = \frac{J_1^2(u) K_0(v) K_2(v) - K_1^2(v)}{K_1^2(v) J_1^2(u) - J_0(u) J_2(u)} \quad (\text{B.5})$$

$$v^2 = \left( \frac{\pi d}{\lambda_0} \right)^2 \left[ \left( \frac{3\lambda_0}{2h_0} \right)^2 - 1 \right] \quad (\text{B.6})$$

$$u \frac{J_0(u)}{J_1(u)} = -v \frac{K_0(v)}{K_1(v)} \quad (\text{B.7})$$

$$\lambda_0 = \frac{c}{f_0} \quad (\text{B.8})$$

Here,  $d$  and  $h_0$  are the diameter and height of the sapphire rod, respectively,  $\varepsilon'$  is the effective relative permittivity of the sapphire rod,  $c$  is the speed of light in vacuum, and  $f_0$  is the resonant frequency of the resonator.

### B.3 Combined standard uncertainty

#### B.3.1 General

By partially differentiating the equation (B.3) with  $h_0$ ,  $\varepsilon'$ ,  $W$ ,  $Q_{u1}$ , and  $Q_{u3}$ , the equation of uncertainty shown in Equation (B.9) is obtained.

$$\begin{aligned}
 u_c^2 &= \frac{\delta R_s^2}{R_s^2} = \left( \frac{\partial R_s}{\partial h} \right)^2 \left( \frac{\delta h}{R_s} \right)^2 + \left( \frac{\partial R_s}{\partial \varepsilon'} \right)^2 \left( \frac{\delta \varepsilon'}{R_s} \right)^2 + \left( \frac{\partial R_s}{\partial W} \right)^2 \left( \frac{\delta W}{R_s} \right)^2 \\
 &\quad + \left( \frac{\partial R_s}{\partial Q_{u1}} \right)^2 \left( \frac{\delta Q_{u1}}{R_s} \right)^2 + \left( \frac{\partial R_s}{\partial Q_{u3}} \right)^2 \left( \frac{\delta Q_{u3}}{R_s} \right)^2 + c_{\text{unknown}}^2 u_{\text{unknown}}^2 \\
 &\quad (\delta h = hu_1, \delta \varepsilon' = \varepsilon' u_2, \delta W = Wu_3, \delta Q_{u1} = Q_{u1} u_4, \delta Q_{u3} = Q_{u3} u_5) \\
 &= \left( \frac{\partial R_s}{\partial h} \right)^2 \left( \frac{h}{R_s} \right)^2 u_1^2 + \left( \frac{\partial R_s}{\partial \varepsilon'} \right)^2 \left( \frac{\varepsilon'}{R_s} \right)^2 u_2^2 + \left( \frac{\partial R_s}{\partial W} \right)^2 \left( \frac{W}{R_s} \right)^2 u_3^2 \\
 &\quad + \left( \frac{\partial R_s}{\partial Q_{u1}} \right)^2 \left( \frac{Q_{u1}}{R_s} \right)^2 u_4^2 + \left( \frac{\partial R_s}{\partial Q_{u3}} \right)^2 \left( \frac{Q_{u3}}{R_s} \right)^2 u_5^2 + c_{\text{unknown}}^2 u_{\text{unknown}}^2 \\
 &= c_1^2 u_1^2 + c_2^2 u_2^2 + c_3^2 u_3^2 + c_4^2 u_4^2 + c_5^2 u_5^2 + c_{\text{unknown}}^2 u_{\text{unknown}}^2
 \end{aligned} \tag{B.9}$$

The variables  $c_{\text{unknown}}$  and  $u_{\text{unknown}}$  in Equation (B.9) represent in the uncertainty of unknown factors of measurement system, for example, noise factor. The variables in Equation (B.9) are expressed by Equations (B.10) to (B.14).

$$c_1 = \frac{\partial R_s}{\partial h} \frac{h}{R_s} = \frac{3R_s}{h_0} \frac{h_0}{R_s} = 3 \tag{B.10}$$

$$c_2 = \frac{\partial R_s}{\partial \varepsilon'} \frac{\varepsilon'}{R_s} = \frac{\varepsilon'}{\varepsilon' + W} \tag{B.11}$$

$$c_3 = \frac{\partial R_s}{\partial W} \frac{W}{R_s} = \frac{(1 - \varepsilon')W}{(1 + W)(\varepsilon' + W)} \tag{B.12}$$

$$c_4 = \frac{\partial R_s}{\partial Q_{u1}} \frac{Q_{u1}}{R_s} = \frac{-Q_{u3}}{Q_{u3} - Q_{u1}} \tag{B.13}$$

$$c_5 = \frac{\partial R_s}{\partial Q_{u3}} \frac{Q_{u3}}{R_s} = \frac{Q_{u1}}{Q_{u3} - Q_{u1}} \tag{B.14}$$

#### B.3.2 Calculation of $c_2$ to $c_5$ (12 GHz resonance at 20 K)

When calculating uncertainty using the Equation (B.9), it is necessary to specify the resonant frequency. Here, we will discuss a typical 12 GHz resonator.

12 GHz resonator ( $f_0 = 12$  GHz,  $d = 11,4$  mm,  $h_0 = 5,7$  mm)

Using the above values, we can calculate  $v^2$  and  $u^2$  by Equations (B.6) and (B.7).

$$v^2 = 7,815, u^2 = 9,09 \quad (\text{B.15})$$

$\varepsilon'$  and  $W$  are determined by Equations (B.4) and (B.5).

$$\varepsilon' = 9,22, W = 0,16 \quad (\text{B.16})$$

Then  $c_2$  and  $c_3$  can be determined using Equations (B.11) and (B.12).

$$c_2 = 0,983, c_3 = -0,122 \quad (\text{B.17})$$

In order to determine  $c_4$  and  $c_5$ , we have to know the values of unloaded  $Q_{u1}$  and  $Q_{u3}$ . Y. Kobayashi reported  $Q_{u1}$  and  $Q_{u3}$  at 20 K, 12 GHz [28]. Their reported values were  $Q_{u1} = 2\,000\,000$  ( $Q_{L1} = 1\,800\,000$ ) and  $Q_{u3} = 7\,500\,000$  ( $Q_{L3} = 6\,750\,000$ ). Therefore,  $c_4$  and  $c_{5L}$  can be calculated.

$$c_4 = 1,364, c_5 = 0,3636 \quad (\text{B.18})$$

### B.3.3 Determination of $u_1$ to $u_5$

$u_1$  to  $u_5$ , which are derived from the uncertainty of the diameter, height and dielectric constant of sapphire rod and  $Q_{u1}$  and  $Q_{u3}$  of the cavity, are calculated by the following procedures.

#### 1) $u_1$

$u_1$  is determined by the uncertainty of the height of the sapphire rod. The height of the sapphire rod of the 12 GHz resonator is 5,7 mm, and its uncertainty is 50  $\mu\text{m}$ . Therefore,  $u_1$  is as follows.

$$u_1 = \frac{1}{\sqrt{3}} \frac{0,05}{5,7} = 0,005\,07 \quad (\text{B.19})$$

#### 2) $u_2$

$u_2$  is determined by the uncertainty in the effective dielectric constant  $\varepsilon'_\delta$  of the sapphire rod and can be calculated using Equation (B.20).

$$u_2 = \frac{1}{\sqrt{3}} \frac{\varepsilon' - \varepsilon'_\delta}{\varepsilon'} \quad (\text{B.20})$$

where  $\varepsilon'_\delta$  is the relative permittivity induced from uncertainty in the shape of the sapphire rod.

$$\varepsilon' = \left( \frac{\lambda_0}{\pi d_0} \right)^2 (u_0^2 + v_0^2) + 1 \quad (d_0 = 11,4 \text{ mm}, h_0 = 5,7 \text{ mm}) \quad (\text{B.21})$$

$$\varepsilon'_\delta = \left( \frac{\lambda_0}{\pi d} \right)^2 (u_{0\delta}^2 + v_{0\delta}^2) + 1 \quad (d_{0\delta} = 11,45 \text{ mm}, h_{0\delta} = 5,65 \text{ mm}) \quad (\text{B.22})$$

and  $u_0$ ,  $v_0$ ,  $u_{0\delta}$  and  $v_{0\delta}$  are calculated using Equations (B.23) and (B.24).

$$v_0^2 = \left( \frac{\pi d_0}{\lambda_0} \right)^2 \left[ \left( \frac{3\lambda_0}{2h_0} \right)^2 - 1 \right], v_{0\delta}^2 = \left( \frac{\pi d_{0\delta}}{\lambda_0} \right)^2 \left[ \left( \frac{3\lambda_0}{2h_{0\delta}} \right)^2 - 1 \right] \quad (\text{B.23})$$

$$u_0 \frac{J_0(u_0)}{J_1(u_0)} = -v_0 \frac{K_0(v_0)}{K_1(v_0)}, u_{0\delta} \frac{J_0(u_{0\delta})}{J_1(u_{0\delta})} = -v_{0\delta} \frac{K_0(v_{0\delta})}{K_1(v_{0\delta})} \quad (\text{B.24})$$

As a result, we find that  $\varepsilon' = 9,22$  and  $\varepsilon'_\delta = 9,29$ .

$$u_2 = 0,004 \ 4 \quad (\text{B.25})$$

3)  $u_3$

$u_3$  can be determined using Equation (B.26).

$$u_3 = \frac{1}{\sqrt{3}} \frac{W - W_\delta}{W} \quad (\text{B.26})$$

$W$  is determined using Equation (B.5) and  $W_\delta$  comes from uncertainty in the shape of the sapphire rod and can be determined by using Equation (B.27).

$$W_\delta = \frac{J_1^2(u_\delta) K_0(v_\delta) K_2(v_\delta) - K_1^2(v_\delta)}{K_1^2(v_\delta) J_1^2(u_\delta) - J_0^2(u_\delta) J_2^2(u_\delta)} \quad (\text{B.27})$$

By calculating  $W$  and  $W_\delta$  using  $u_0, v_0, u_{0\delta}, v_{0\delta}$  in Equations (B.23) and (B.24),  $u_3$  turns out to have the following value.

$$u_3 = 0,014 \ 3 \quad (\text{B.28})$$

4)  $u_4$  and  $u_5$

$u_4$  and  $u_5$  are determined by measuring the uncertainty in  $Q_{u1}$  and  $Q_{u3}$ . The measurement of the uncertainty in  $Q_{u1}$  and  $Q_{u3}$  has the most influence on the dynamic range uncertainty of the vector network analyzer and other factors are negligible. Since the dynamic range uncertainty in the recommended vector network analyzer is  $\pm 0,1$  dB,  $u_4$  and  $u_5$  are calculated using this value. Regarding the frequency characteristics of the resonator in Figure B.2, the frequency characteristic near the resonant frequency is assumed to be a Lorentz distribution [30].

$$y = \left| \frac{S_{12}(f)}{S_{12}(f_0)} \right| = \frac{1}{\left( 1 + Q^2 \Delta^2(f) \right)^{1/2}} = \frac{1}{\left( 1 + \left( \frac{f - f_0}{f_1} \right)^2 \right)^{1/2}},$$

$$\Delta(f) = 1 - \frac{f_0^2}{f^2} = \frac{2(f - f_0)}{f_0} \quad (\text{B.29})$$

The frequency characteristics are shown in Figure B.3 The curve can be approximated by Equation (B.29), where  $f_0$  is the resonant frequency and  $2f_1$  is the bandwidth at 3,01 dB. The frequency bandwidth which is 3,01 dB below the resonance peak is defined as  $\Delta f$  and it corresponds to the bandwidth across 0,707 in Figure B.3. The  $\pm 0,1$  dB of the dynamic range uncertainty corresponds to  $\pm 0,008$  in Figure B.3. Therefore,  $Q_{L1}$ ,  $Q_{L1\delta}$ ,  $Q_{L3}$ , and  $Q_{L3\delta}$

can be calculated.  $Q_{L1}$  and  $Q_{L3}$  are reported as  $1,80 \times 10^6$  and  $6,75 \times 10^6$ , respectively [28]. Using these values, we can calculate  $Q_{L1\delta}$  and  $Q_{L3\delta}$ .

$$Q_{L1} = 1,80 \times 10^6, \quad Q_{L1\delta} = 1,84 \times 10^6, \quad Q_{L3} = 6,75 \times 10^6, \quad Q_{L3\delta} = 6,90 \times 10^6$$

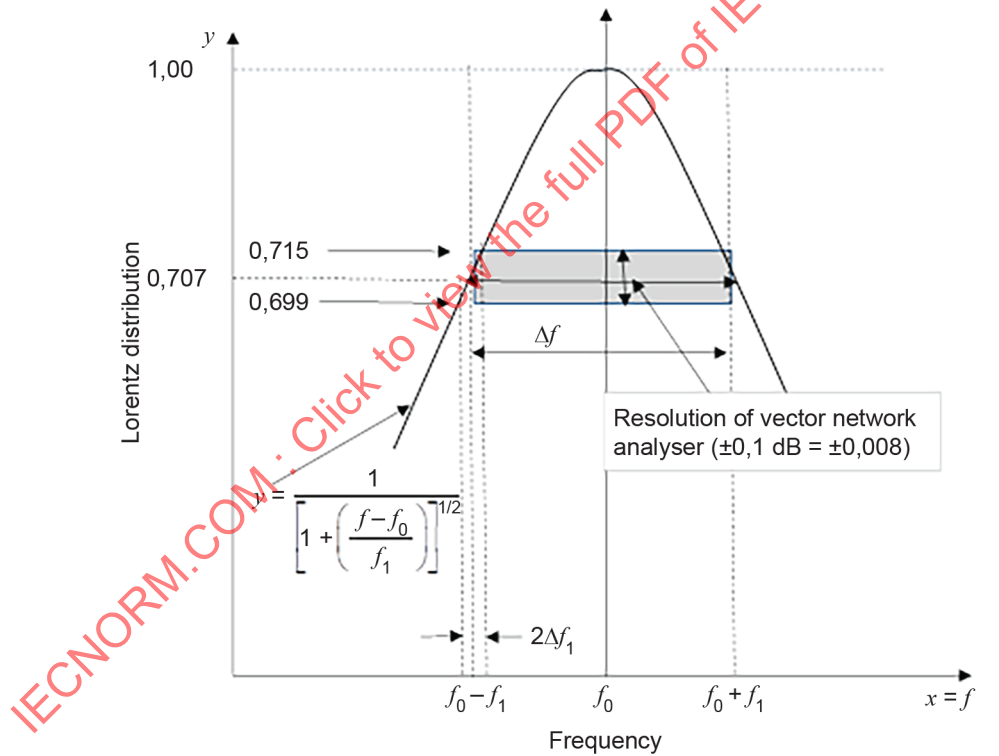
Assuming insertion attenuation ( $IA$ ) = 20dB,  $Q_{u1}$ ,  $Q_{u1\delta}$ ,  $Q_{u3}$ , and  $Q_{u3\delta}$  can be calculated.

$$Q_{u1} = 2,00 \times 10^6, \quad Q_{u1\delta} = 2,044 \times 10^6, \quad Q_{u3} = 7,5 \times 10^6, \quad Q_{u3\delta} = 7,67 \times 10^6$$

Through these calculations, the values of  $u_4$  and  $u_5$  are obtained.

$$u_4 = \frac{1}{\sqrt{3}} \frac{Q_{u1} - Q_{u1\delta}}{Q_{u1}} = -0,012 \quad (\text{B.30})$$

$$u_5 = \frac{1}{\sqrt{3}} \frac{Q_{u3} - Q_{u3\delta}}{Q_{u3}} = -0,013 \quad (\text{B.31})$$



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**Figure B.3 – Frequency characteristics of a resonator approximated by a Lorentz distribution**

#### B.3.4 Combined relative standard uncertainty

Uncertainties in  $c_{\text{cavity}}$  and  $u_{\text{cavity}}$  due to the loss of copper cavity is quite small, however  $c_{\text{unknown}}$  and  $u_{\text{unknown}}$  are not small. The combined standard uncertainty at 20 K is calculated as follows.

$$\begin{aligned}
 u_c &= \sqrt{c_1^2 u_1^2 + c_2^2 u_2^2 + c_3^2 u_3^2 + c_4^2 u_4^2 + c_5^2 u_5^2 + c_{\text{unknown}}^2 u_{\text{unknown}}^2} \\
 &= \sqrt{2,31 \times 10^{-4} + 0,187 \times 10^{-4} + 0,030 \times 10^{-4} + 2,68 \times 10^{-4} + 0,223 \times 10^{-4} + c_{\text{unknown}}^2 u_{\text{unknown}}^2} \quad (\text{B.32}) \\
 &= \sqrt{5,43 \times 10^{-4} + c_{\text{unknown}}^2 u_{\text{unknown}}^2}
 \end{aligned}$$

It is difficult to quantitatively evaluate  $c_{\text{unknown}} u_{\text{unknown}}$  in Equation (B.32), but its value can be estimated from the results of surface resistance measurement repeated three times. The variation observed when measuring the surface resistance of the same films repeatedly is believed to be due to the noise and temperature uncertainty of the measurement system. Therefore, from the results in Table A.1,  $c_{\text{unknown}} u_{\text{unknown}}$  can be estimated as about 0,32 % for 20 K, about 0,9 % for 60 K, and about 6,9 % for 80 K ( $c_{\text{unknown}} u_{\text{unknown}}$  increases as the measurement temperature increases). From the above results, the combined relative standard uncertainty of Equation (B.32) was about 2,4 % at 20 K and about 7,3 % at 80 K. The value is smaller than the target combined relative standard uncertainty.

When the measured temperature exceeds 70 K, large noise is superimposed on the resonance peak, and the uncertainty in  $R_s$  increases. In that case, it is difficult to express the resonance peak with Lorentz distribution. Therefore, the deviation of  $u_4$  and  $u_5$  have to be reviewed. However, as is clear from the results in Figure A.11 and Table A.1, the uncertainty of  $R_s$  measured by the standard dielectric resonator method is less than 10 % below 80 K.

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## SOMMAIRE

|                                                                                                                                              |    |
|----------------------------------------------------------------------------------------------------------------------------------------------|----|
| AVANT-PROPOS .....                                                                                                                           | 47 |
| INTRODUCTION.....                                                                                                                            | 49 |
| 1 Domaine d'application .....                                                                                                                | 51 |
| 2 Références normatives .....                                                                                                                | 51 |
| 3 Termes et définitions .....                                                                                                                | 51 |
| 4 Exigences.....                                                                                                                             | 51 |
| 5 Appareillage .....                                                                                                                         | 52 |
| 5.1 Système de mesure .....                                                                                                                  | 52 |
| 5.2 Appareil de mesure de $R_s$ .....                                                                                                        | 53 |
| 5.3 Tiges diélectriques.....                                                                                                                 | 55 |
| 6 Procédure de mesure .....                                                                                                                  | 55 |
| 6.1 Préparation de l'éprouvette .....                                                                                                        | 55 |
| 6.2 Montage.....                                                                                                                             | 56 |
| 6.3 Mesurage du niveau de référence .....                                                                                                    | 56 |
| 6.4 Mesurage de la réponse en fréquence des résonateurs .....                                                                                | 57 |
| 6.5 Détermination de la résistance de surface du supraconducteur et $\varepsilon'$ et $\tan \delta$<br>des tiges de saphir normalisées ..... | 59 |
| 7 Incertitude de la méthode d'essai .....                                                                                                    | 60 |
| 7.1 Résistance de surface .....                                                                                                              | 60 |
| 7.2 Température .....                                                                                                                        | 61 |
| 7.3 Structure de l'éprouvette et du support .....                                                                                            | 62 |
| 7.4 Protection de l'éprouvette .....                                                                                                         | 62 |
| 7.5 Incertitude de la résistance de surface mesurée par la méthode normalisée<br>à deux résonateurs .....                                    | 62 |
| 8 Rapport d'essai .....                                                                                                                      | 62 |
| 8.1 Identification de l'éprouvette d'essai .....                                                                                             | 62 |
| 8.2 Consignation des valeurs $R_s$ .....                                                                                                     | 62 |
| 8.3 Consignation des conditions d'essai.....                                                                                                 | 63 |
| Annexe A (informative) Informations supplémentaires relatives aux Articles 1 à 8.....                                                        | 64 |
| A.1 Domaine d'application.....                                                                                                               | 64 |
| A.1.1 Généralités.....                                                                                                                       | 64 |
| A.1.2 Méthode de cavité cylindrique [10] [17].....                                                                                           | 64 |
| A.1.3 Méthode du résonateur à plaques parallèles [18] [19] .....                                                                             | 64 |
| A.1.4 Méthode du résonateur microruban [20] [21].....                                                                                        | 64 |
| A.1.5 Méthode du résonateur diélectrique [22] [23] [24] [25] .....                                                                           | 64 |
| A.1.6 Méthode du résonateur diélectrique de type image [26] [27] .....                                                                       | 65 |
| A.1.7 Méthode à deux résonateurs [28] [29].....                                                                                              | 66 |
| A.2 Exigences .....                                                                                                                          | 66 |
| A.3 Théorie et équations de calcul .....                                                                                                     | 66 |
| A.4 Appareillage.....                                                                                                                        | 69 |
| A.5 Dimensions des tiges de saphir normalisées .....                                                                                         | 70 |
| A.6 Dimension du résonateur fermé .....                                                                                                      | 72 |
| A.7 Reproductibilité de la tige de saphir .....                                                                                              | 74 |
| A.8 Résultats d'essai.....                                                                                                                   | 74 |
| A.9 Reproductibilité de la méthode de mesure .....                                                                                           | 75 |

|                                                                                                                                                                                                   |    |
|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----|
| A.10 Effet de l'écart $\tan \delta$ des tiges de saphir sur la résistance de surface .....                                                                                                        | 76 |
| Annexe B (informative) Évaluation de l'incertitude type composée relative pour le<br>mesurage de la résistance de surface .....                                                                   | 78 |
| B.1 Mesurage pratique de la résistance de surface .....                                                                                                                                           | 78 |
| B.2 Détermination de la résistance de surface du supraconducteur .....                                                                                                                            | 79 |
| B.3 Incertitude type composée .....                                                                                                                                                               | 80 |
| B.3.1 Généralités .....                                                                                                                                                                           | 80 |
| B.3.2 Calcul de $c_2$ à $c_5$ (résonance 12 GHz à 20 K) .....                                                                                                                                     | 80 |
| B.3.3 Détermination de $u_1$ à $u_5$ .....                                                                                                                                                        | 81 |
| B.3.4 Incertitude type composée relative .....                                                                                                                                                    | 83 |
| Bibliographie .....                                                                                                                                                                               | 85 |
| Figure 1 – Schéma du système de mesure de la dépendance de la résistance de<br>surface $R_s$ vis-à-vis de la température à l'aide d'un cryoréfrigérateur .....                                    | 52 |
| Figure 2 – Appareil de mesure classique de $R_s$ .....                                                                                                                                            | 54 |
| Figure 3 – Affaiblissement d'insertion $IA$ , fréquence de résonance $f_0$ et bande<br>passante à mi-puissance $\Delta f$ , mesurés à $T$ kelvin .....                                            | 57 |
| Figure 4 – Facteurs de répartition de la réflexion ( $S_{11}$ et $S_{22}$ ) .....                                                                                                                 | 59 |
| Figure 5 – Définitions terminologiques du Tableau 4 .....                                                                                                                                         | 61 |
| Figure A.1 – Configuration schématique de plusieurs méthodes de mesure pour la<br>résistance de surface .....                                                                                     | 65 |
| Figure A.2 – Configuration d'un résonateur à tige diélectrique cylindrique court-circuité<br>aux deux extrémités par deux films supraconducteurs déposés sur des substrats<br>diélectriques ..... | 67 |
| Figure A.3 – Résultats calculés des relations $u$ - $v$ et $W$ - $v$ pour le mode $TE_{01p}$ .....                                                                                                | 68 |
| Figure A.4 – Configuration des tiges diélectriques normalisées pour le mesurage<br>de $R_s$ et $\tan \delta$ .....                                                                                | 69 |
| Figure A.5 – Trois types de résonateurs diélectriques .....                                                                                                                                       | 70 |
| Figure A.6 – Graphe de modes de conception du résonateur $TE_{011}$ court-circuité aux<br>deux extrémités par des films supraconducteurs parallèles [28] .....                                    | 71 |
| Figure A.7 – Graphe de modes de conception du résonateur $TE_{013}$ court-circuité aux<br>deux extrémités par des films supraconducteurs parallèles [28] .....                                    | 72 |
| Figure A.8 – Graphe de modes pour le résonateur fermé $TE_{011}$ [28] .....                                                                                                                       | 73 |
| Figure A.9 – Graphe de modes pour le résonateur fermé $TE_{013}$ [28] .....                                                                                                                       | 74 |
| Figure A.10 – Valeur $R_s$ dépendante de la température d'un film YBCO de 500 nm<br>d'épaisseur et de 25 mm carrés .....                                                                          | 75 |
| Figure A.11 – $R_s$ dépendant de la température d'un film YBCO lorsque $R_s$ a été<br>mesuré trois fois .....                                                                                     | 76 |
| Figure B.1 – Diagramme schématique de la résonance de mode $TE_{011}$ et $TE_{013}$ .....                                                                                                         | 78 |
| Figure B.2 – Caractéristiques de fréquences classiques de la résonance de<br>mode $TE_{011}$ .....                                                                                                | 79 |
| Figure B.3 – Caractéristiques de fréquence d'un résonateur approchée par une<br>distribution de Lorentz .....                                                                                     | 83 |
| Tableau 1 – Dimensions classiques de paires de tiges de saphir monocristallin<br>pour 12 GHz, 18 GHz et 22 GHz .....                                                                              | 55 |

|                                                                                                              |    |
|--------------------------------------------------------------------------------------------------------------|----|
| Tableau 2 – Dimensions du film supraconducteur pour 12 GHz, 18 GHz et 22 GHz .....                           | 56 |
| Tableau 3 – Spécifications pour l'analyseur de réseau vectoriel.....                                         | 60 |
| Tableau 4 – Spécifications pour les tiges de saphir.....                                                     | 61 |
| Tableau A.1 – Écart-type de la résistance de surface, calculé à partir des résultats de la Figure A.11 ..... | 76 |
| Tableau A.2 – Relation entre $x$ défini par l'Équation (A.12) et $y$ par l'Équation (A.13) .....             | 77 |

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## COMMISSION ÉLECTROTECHNIQUE INTERNATIONALE

## SUPRACONDUCTIVITÉ –

**Partie 7: Mesurages des caractéristiques électronique –  
Résistance de surface des supraconducteurs  
haute température critique aux hyperfréquences**

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La Norme internationale IEC 61788-7 a été établie par le comité d'études 90 de l'IEC: Supraconductivité.

Cette troisième édition annule et remplace la deuxième édition parue en 2006. Cette édition constitue une révision technique.

Cette édition inclut les modifications techniques majeures suivantes par rapport à l'édition précédente:

- a) l'ajout de l'Annexe B informative, incertitude type composée relative pour le mesurage de la résistance de surface;
- b) les déclarations de fidélité et d'exactitude ont été converties en incertitude;

c) l'ajout de la reproductibilité du mesurage de résistance de surface.

Le texte de cette Norme internationale est issu des documents suivants:

| FDIS        | Rapport de vote |
|-------------|-----------------|
| 90/447/FDIS | 90/452/RVD      |

Le rapport de vote indiqué dans le tableau ci-dessus donne toute information sur le vote ayant abouti à l'approbation de cette Norme internationale.

Ce document a été rédigé selon les Directives ISO/IEC, Partie 2.

Une liste de toutes les parties de la série IEC 61788, publiées sous le titre général *Supraconductivité*, peut être consultée sur le site web de l'IEC.

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## INTRODUCTION

Depuis la découverte de certains oxydes de cuivre de type Perovskite, un travail approfondi de recherche et développement (R et D) sur les supraconducteurs haute température (HTS – *high-temperature superconductors*) a été, et est toujours, réalisé dans le monde entier, et son application aux machines à aimant à effet de champ, à la transmission à faible perte de puissance, aux composants électroniques et à d'autres technologies est en cours.

Dans différents domaines de l'électronique, et plus particulièrement dans ceux des télécommunications, les dispositifs hyperfréquences passifs (des filtres utilisant des HTS, par exemple) ont été développés et font actuellement l'objet d'essais sur site [1]<sup>1</sup> [2].

Les matériaux supraconducteurs destinés aux résonateurs à hyperfréquences [3], aux filtres [4], aux antennes [5] et aux lignes à retard [6] ont l'avantage de présenter des caractéristiques à très faible perte. Les paramètres des matériaux supraconducteurs nécessaires à la conception des composants hyperfréquences à faible perte sont la résistance de surface ( $R_s$ ) et la dépendance de  $R_s$  vis-à-vis de la température. La connaissance de ce paramètre est d'une importance essentielle pour le développement de nouveaux matériaux côté fournisseur et pour la conception de composants hyperfréquences supraconducteurs côté client.

L'amplitude de la résistance de Surface  $R_s$  des films HTS de grande qualité est en général inférieure de plusieurs ordres à celle des métaux normaux [7] [8] [9] [10], ce qui a renforcé la nécessité d'une technique de caractérisation fiable pour mesurer cette propriété. Traditionnellement, la résistance de surface  $R_s$  du niobium (Nb) ou de tout autre matériau supraconducteur basse température est mesurée en fabriquant d'abord une cavité (optique) résonante à trois dimensions, puis en mesurant sa valeur  $Q$  [11]. La résistance de surface  $R_s$  peut être calculée en résolvant la distribution de champ électromagnétique (CEM) à l'intérieur de la cavité. Une autre technique consiste à placer un petit échantillon à l'intérieur d'une cavité plus grande. Cette technique prend de nombreuses formes, mais implique souvent l'incertitude introduite par le retrait de la contribution de la perte due aux films supraconducteurs à haute température de la perte totale mesurée de manière expérimentale de la cavité.

Les meilleurs échantillons HTS sont des films épitaxiaux formés sur des substrats cristallins plats, en effet aucun film de grande qualité n'a été jusqu'ici formé sur une surface arrondie. Il est donc nécessaire de disposer d'une technique qui peut utiliser ces petits échantillons plats, qui n'exige aucune préparation des échantillons, qui n'endommage ni n'altère le film, qui est hautement répétable, qui présente une grande sensibilité (jusqu'à 1/1 000e de la résistance de surface  $R_s$  du cuivre), qui présente une large plage dynamique (jusqu'à la résistance de surface  $R_s$  du cuivre), qui peut atteindre des puissances internes élevées avec de faibles puissances d'entrée et qui présente une large couverture de températures (4,2 K à 150 K).

La méthode du résonateur diélectrique a été choisie parmi plusieurs méthodes de détermination de la résistance de surface aux hyperfréquences, car elle s'est avérée la plus populaire et la plus pratique actuellement. Plus particulièrement, le résonateur saphir est un excellent outil de mesure de la résistance de surface  $R_s$  des matériaux supraconducteurs à haute température [12] [13] [14].

La méthode d'essai spécifiée dans le présent document peut également être appliquée à d'autres éléments supraconducteurs, y compris les matériaux à faible  $T_c$ .

Le présent document est destiné à fournir une base technique appropriée et convenable pour le moment aux ingénieurs qui travaillent dans le domaine de l'électronique et des technologies liées à la supraconductivité.

---

<sup>1</sup> Les chiffres entre crochets se réfèrent à la bibliographie.

La méthode d'essai couverte par le présent document repose sur le travail de normalisation préalable réalisé dans le cadre du Programme de Versailles sur les matériaux de pointe et les normes (VAMAS – Versailles Project on Advanced Materials and Standards) sur les propriétés des films fins supraconducteurs.

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## SUPRACONDUCTIVITÉ –

### Partie 7: Mesurages des caractéristiques électronique – Résistance de surface des supraconducteurs haute température critique aux hyperfréquences

#### 1 Domaine d'application

La présente partie de l'IEC 61788 décrit le mesurage de la résistance de surface ( $R_s$ ) des supraconducteurs aux hyperfréquences par la méthode normalisée à deux résonateurs. L'objet du mesurage est la dépendance de la résistance de surface  $R_s$  vis-à-vis de la température à la fréquence de résonance.

La plage de mesures applicable des résistances de surface  $R_s$  pour cette méthode est la suivante:

- Fréquence:  $8 \text{ GHz} < f < 30 \text{ GHz}$
- Résolution de mesure:  $0,01 \text{ m}\Omega$  à  $10 \text{ GHz}$

Les données de  $R_s$  à la fréquence mesurée, et celles mises à l'échelle à  $10 \text{ GHz}$ , en prenant pour hypothèse la règle de comparaison  $f^2$ , doivent être consignées.

#### 2 Références normatives

Les documents suivants cités dans le texte constituent, pour tout ou partie de leur contenu, des exigences du présent document. Pour les références datées, seule l'édition citée s'applique. Pour les références non datées, la dernière édition du document de référence s'applique (y compris les éventuels amendements).

IEC 60050-815, *Vocabulaire Électrotechnique International (IEV) – Partie 815: Supraconductivité*

#### 3 Termes et définitions

Pour les besoins du présent document, les termes et définitions de l'IEC 60050-815 s'appliquent.

L'ISO et l'IEC tiennent à jour des bases de données terminologiques destinées à être utilisées en normalisation, consultables aux adresses suivantes:

- IEC Electropedia: disponible à l'adresse <http://www.electropedia.org/>
- ISO Online browsing platform: disponible à l'adresse <http://www.iso.org/obp>

#### 4 Exigences

La résistance de surface  $R_s$  d'un film supraconducteur doit être mesurée en appliquant un signal hyperfréquences à un résonateur diélectrique avec l'éprouvette de film supraconducteur, puis en mesurant l'affaiblissement du résonateur à chaque fréquence. La fréquence doit être balayée autour de la fréquence de résonance au centre, et les caractéristiques de fréquence d'affaiblissement doivent être consignées afin d'obtenir une valeur  $Q$  correspondant à la perte.

L'incertitude type composée relative cible de cette méthode est inférieure à 20 % pour la plage de températures de mesure comprise entre 20 K et 80 K.

Il incombe à l'utilisateur du présent document d'établir, avant de l'utiliser, des pratiques d'hygiène et de sécurité appropriées et de déterminer l'applicabilité des restrictions réglementaires.

Ce type de mesure présente certains dangers. Il est essentiel d'utiliser un système cryogénique pour refroidir les supraconducteurs et permettre leur passage à l'état supraconducteur. Un contact direct de la peau avec des composants froids de l'appareillage peut provoquer une congélation immédiate, comme le peut un contact direct avec un produit cryogène qui s'est déversé. L'utilisation d'un générateur de radiofréquences est également essentielle au mesurage des propriétés haute fréquence des matériaux. Si sa puissance est trop élevée, un contact direct avec des personnes peut provoquer des brûlures immédiates.

## 5 Appareillage

### 5.1 Système de mesure

La Figure 1 présente un schéma du système exigé pour le mesurage aux hyperfréquences. Ce système est composé d'un système d'analyseurs de réseau pour la mesure de transmission, d'un appareil de mesure et d'un thermomètre pour surveiller la température de mesure.

Une puissance incidente générée par une source hyperfréquence adaptée (un analyseur synthétisé, par exemple) est appliquée au résonateur diélectrique fixé dans l'appareil de mesure. Les caractéristiques de transmission sont présentées sur l'écran de l'analyseur de réseau. L'appareil de mesure est placé dans un cryoréfrigérateur à régulation de température.

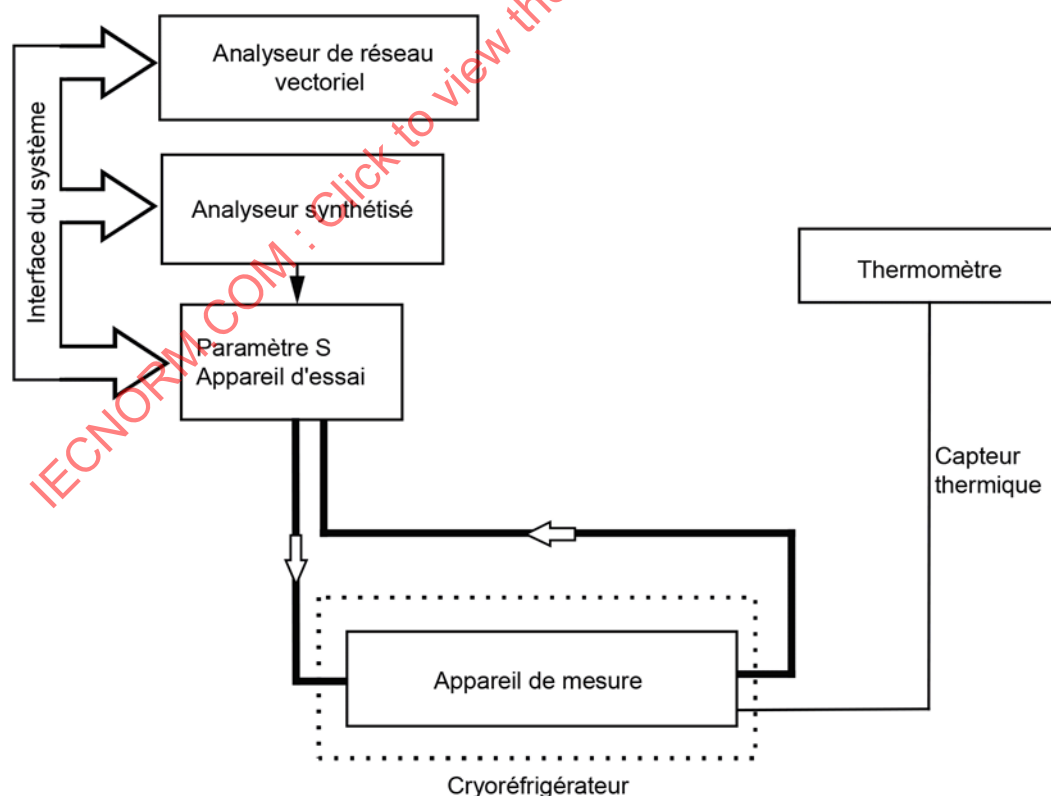


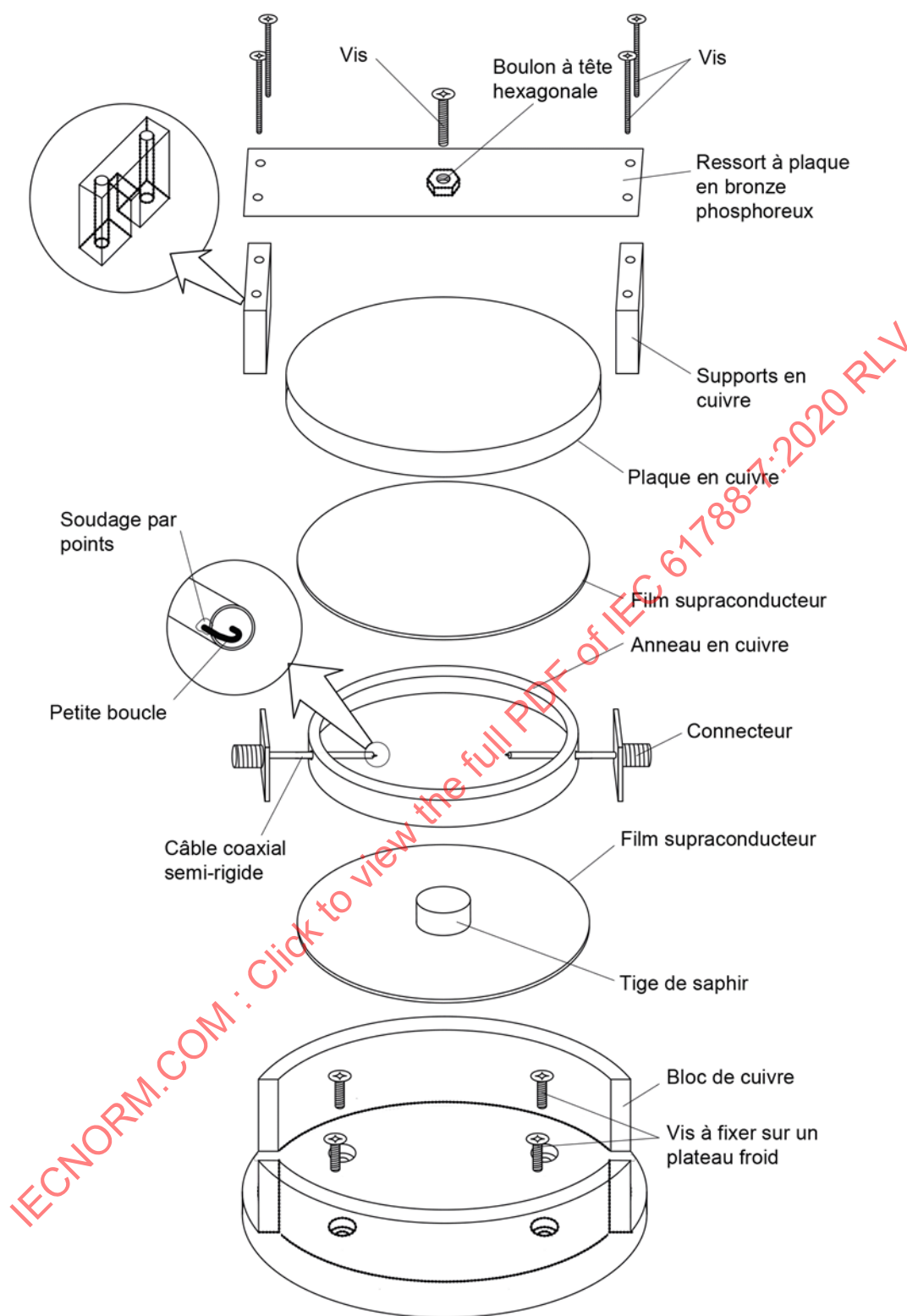
Figure 1 – Schéma du système de mesure de la dépendance de la résistance de surface  $R_s$  vis-à-vis de la température à l'aide d'un cryoréfrigérateur

Pour le mesurage de la résistance de surface  $R_s$  des films supraconducteurs, un analyseur de réseau vectoriel est recommandé. Un analyseur de réseau vectoriel présente une meilleure fidélité de mesure qu'un analyseur de réseau scalaire, en raison de sa large plage dynamique. Les exigences de performances de l'analyseur de réseau vectoriel sont présentées en 7.1.

## 5.2 Appareil de mesure de $R_s$

La Figure 2 présente le schéma d'un appareil de mesure classique (résonateur fermé) de la résistance de surface  $R_s$  des films HTS déposés sur un substrat avec une surface plane. Le film HTS supérieur est comprimé à l'aide d'un ressort en bronze phosphoreux. Il convient d'utiliser le ressort à plaque pour améliorer l'incertitude de mesure. Ce type de ressort permet de réduire le frottement entre le ressort et l'autre partie de l'appareil, et d'assurer la fluidité de mouvement des films supraconducteurs en raison de la dilatation thermique de la tige diélectrique. Pour réduire le plus possible l'incertitude de mesure, la tige de saphir et l'anneau en cuivre doivent être coaxiaux.

Deux câbles semi-rigides de mesure des caractéristiques de transmission du résonateur doivent être fixés des deux côtés du résonateur dans une position axiale symétrique ( $\phi = 0$  et  $\pi$ , où  $\phi$  est l'angle de rotation autour de l'axe central de la tige de saphir). L'extrémité de chacun des deux câbles semi-rigides doit comporter une petite boucle. Le plan de la boucle doit être parallèle à celui des films supraconducteurs afin de supprimer les modes d'ondes magnétiques transverses ( $TM_{mn0}$ ) non souhaités. Les boucles de couplage doivent être soigneusement vérifiées pour détecter des fissures dans le joint soudé par points qui peuvent s'être développées lors de cycles thermiques répétés. Ces câbles peuvent se déplacer vers la droite et la gauche pour ajuster l'affaiblissement d'insertion (24). Lors de cet ajustement, le couplage des modes de cavité non souhaités au mode de résonance diélectrique concerné doit être supprimé. Le couplage parasite non souhaité aux autres modes permet de réduire la valeur  $Q$  élevée du résonateur de mode électromagnétique transverse TE. Pour supprimer le couplage parasite, la conception des résonateurs  $Q$  élevés doit faire l'objet d'une attention particulière. Deux autres types de résonateurs, avec celui de type fermé représenté à la Figure 2, peuvent être utilisés. Ils sont expliqués en A.4.



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**Figure 2 – Appareil de mesure classique de  $R_s$**

Une ligne de référence composée d'un câble semi-rigide doit être utilisée pour mesurer le niveau de puissance de transmission totale, c'est-à-dire le niveau de référence. La longueur de ce câble est égale à la somme des deux câbles de l'appareil de mesure. Le câble semi-rigide de diamètre extérieur de 1,20 mm est recommandé.

Pour réduire le plus possible l'incertitude de mesure, deux films supraconducteurs doivent être placés en parallèle. Pour veiller à ce que les deux films supraconducteurs restent en contact étroit avec les extrémités de la tige de saphir, sans entrefer, les deux surfaces des films et les extrémités de la tige doivent être soigneusement nettoyées.

### 5.3 Tiges diélectriques

Deux tiges diélectriques présentant une permittivité relative identique,  $\varepsilon'$ , et un facteur de perte,  $\tan \delta$ , de préférence prélevés sur une tige diélectrique cylindrique, sont exigées. Ces deux tiges (tiges diélectriques normalisées) doivent présenter le même diamètre, mais des hauteurs différentes: l'une doit être trois fois supérieure à celle de l'autre.

Il est préférable d'utiliser des tiges diélectriques dont la valeur  $\tan \delta$  est faible afin d'obtenir l'incertitude de mesure exigée sur  $R_s$ . Les tiges diélectriques recommandées sont les tiges de saphir monocristallin dont  $\tan \delta$  est inférieur à  $2 \times 10^{-7}$  à 77 K. Les spécifications relatives aux tiges de saphir sont présentées en 7.1. Pour réduire le plus possible les erreurs de mesure de la résistance de surface  $R_s$  des films supraconducteurs, les deux extrémités des tiges de saphir doivent être polies parallèles l'une à l'autre et perpendiculaires à l'axe. Des spécifications relatives aux tiges de saphir sont données à l'Article 7.

Le diamètre et les hauteurs des tiges de saphir normalisées doivent être soigneusement conçus de manière à ne pas coupler les modes  $TE_{011}$  et  $TE_{013}$  à d'autres modes TM, HE et EH, étant donné que le couplage entre le mode TE et les autres modes provoque la dégradation de  $Q$  à vide. Des lignes directrices de conception pour les tiges de saphir normalisées sont données à l'Article A.5. Le Tableau 1 donne des exemples classiques de tiges de saphir normalisées pour une résonance de 12 GHz, de 18 GHz et de 22 GHz. Pour le mesurage de  $R_s$  à 22 GHz, le diamètre de film exigé peut être de 20 mm, et la valeur  $Q_L$  mesurée est faible, les effets de la perte diélectrique de la tige de saphir pouvant donc être réduits.

**Tableau 1 – Dimensions classiques de paires de tiges de saphir monocristallin pour 12 GHz, 18 GHz et 22 GHz**

| Fréquence<br>GHz |                                      | Diamètre, $d$<br>mm | Hauteur, $h$<br>mm |
|------------------|--------------------------------------|---------------------|--------------------|
| 12               | Tige courte (résonateur $TE_{011}$ ) | $11,40 \pm 0,05$    | $5,70 \pm 0,05$    |
|                  | Tige longue (résonateur $TE_{013}$ ) | $11,40 \pm 0,05$    | $17,10 \pm 0,05$   |
| 18               | Tige courte (résonateur $TE_{011}$ ) | $7,60 \pm 0,05$     | $3,80 \pm 0,05$    |
|                  | Tige longue (résonateur $TE_{013}$ ) | $7,60 \pm 0,05$     | $11,40 \pm 0,05$   |
| 22               | Tige courte (résonateur $TE_{011}$ ) | $6,20 \pm 0,05$     | $3,10 \pm 0,05$    |
|                  | Tige longue (résonateur $TE_{013}$ ) | $6,20 \pm 0,05$     | $9,30 \pm 0,05$    |

## 6 Procédure de mesure

### 6.1 Préparation de l'éprouvette

Pour l'estimation de l'incertitude, le diamètre du film doit être environ trois fois plus grand que celui des tiges de saphir. Dans cette configuration, l'augmentation de l'incertitude de  $R_s$  en raison des différentes pertes par rayonnement entre le mode  $TE_{011}$  et le mode  $TE_{013}$  peut être considérée comme étant négligeable, compte tenu de l'incertitude type composée relative cible de 20 %. L'épaisseur de film doit être environ deux fois plus grande que la valeur de profondeur de pénétration du champ magnétique à la température maximale dans la plage de températures

de mesure. Si l'épaisseur de film est bien inférieure à deux fois la profondeur de pénétration du champ magnétique, il convient que la  $R_s$  mesurée soit la résistance de surface efficace.

Le Tableau 2 donne les dimensions des films supraconducteurs des tiges de saphir normalisées de 12 GHz, 18 GHz et 22 GHz.

**Tableau 2 – Dimensions du film supraconducteur pour 12 GHz, 18 GHz et 22 GHz**

| Tige de saphir à découpe en c |                     | Film supraconducteur |                            |
|-------------------------------|---------------------|----------------------|----------------------------|
| Fréquence<br>GHz              | Diamètre, $d$<br>mm | Diamètre, $d'$<br>mm | Épaisseur<br>$\mu\text{m}$ |
| 12                            | $11,40 \pm 0,05$    | $> 35$               | $\approx 0,5$              |
| 18                            | $7,60 \pm 0,05$     | $> 25$               | $\approx 0,5$              |
| 22                            | $6,20 \pm 0,05$     | $> 20$               | $\approx 0,5$              |

Dans le cas des résonateurs fermés, les dimensions des films supraconducteurs doivent également être prévues en tenant compte de la dimension du cylindre en cuivre entre les films supraconducteurs. Des lignes directrices de conception pour la dimension du cylindre en cuivre du résonateur fermé sont présentées à l'Article A.6.

## 6.2 Montage

Monter le matériel de mesure comme représenté à la Figure 1. Tous les appareils de mesure, tiges de saphir normalisées et films supraconducteurs doivent rester propres et secs, une humidité importante pouvant dégrader la valeur  $Q$  à vide. L'éprouvette et l'appareil de mesure doivent être placés dans un cryoréfrigérateur à régulation de température. La chambre de l'éprouvette doit être complètement sous vide. Les températures des films supraconducteurs et des tiges de saphir normalisées doivent être mesurées par un thermomètre à diode ou un couple thermoélectrique. Les températures des films supraconducteurs supérieur et inférieur et les tiges de saphir normalisées ne doivent pas différer de plus de 0,5 K. Pour ce faire, couvrir l'appareil de mesure d'une feuille d'aluminium ou remplir la chambre de l'éprouvette avec de l'hélium.

## 6.3 Mesurage du niveau de référence

Le niveau de puissance de transmission totale (niveau de référence) doit être mesuré en premier. Fixer la puissance de sortie de l'analyseur synthétisé sous 10 mW, l'incertitude de mesure dépendant du niveau du signal de mesure. Connecter la ligne de référence du câble semi-rigide entre les connecteurs d'entrée et de sortie. Ensuite, mesurer le niveau de puissance de transmission sur l'ensemble de la fréquence de mesure et de la plage de températures. Le niveau de référence peut varier de plusieurs décibels si la température de l'appareil passe de la température ambiante à la température de mesure la plus basse. Par conséquent, la dépendance du niveau de référence vis-à-vis de la température doit être prise en considération.

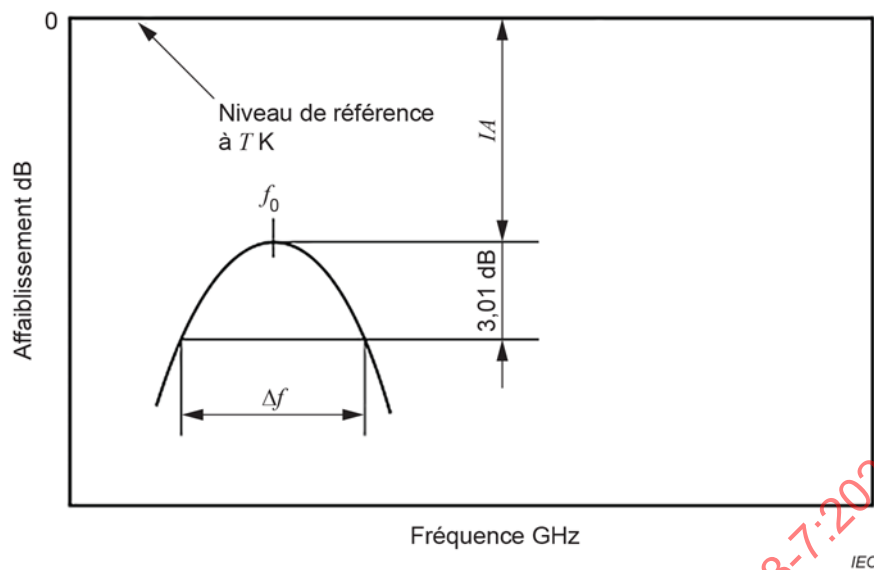


**Figure 3 – Affaiblissement d'insertion  $IA$ , fréquence de résonance  $f_0$  et bande passante à mi-puissance  $\Delta f$ , mesurés à  $T$  kelvin**

#### 6.4 Mesurage de la réponse en fréquence des résonateurs

La dépendance de la résistance de surface  $R_s$  vis-à-vis de la température peut être obtenue en mesurant la fréquence de résonance  $f_0$  et le facteur de qualité à vide  $Q_u$  pour les résonateurs  $TE_{011}$  et  $TE_{013}$ , qui doivent être mesurés comme suit.

- Connecter l'appareil de mesure entre les connecteurs d'entrée et de sortie (Figure 1). Insérer la courte tige de saphir normalisée à proximité du centre du film supraconducteur inférieur, et placer la tige et chacune des boucles des câbles semi-rigides à égale distance, de sorte que ce résonateur à transmission puisse être sous-couplé de manière égale aux autres boucles. Déposer doucement le film supraconducteur pour le faire entrer en contact avec la face supérieure de la tige. Veiller à ne pas appuyer trop fort pour ne pas endommager la surface du film supraconducteur. Faire le vide dans la chambre de l'éprouvette et la refroidir sous la température critique.
- Déterminer le pic de résonance du mode  $TE_{011}$  de ce résonateur à une fréquence pratiquement égale à la valeur de conception de  $f_0$ .
- Réduire l'intervalle de fréquence sur l'affichage de manière à ne pouvoir afficher que le pic de résonance du mode  $TE_{011}$  (Figure 3). Confirmer que l'affaiblissement d'insertion  $IA$  de ce mode est supérieur à 20 dB par rapport au niveau de référence, qui dépend fortement de la température.
- Mesurer la dépendance de  $f_0$  vis-à-vis de la température et la bande passante à mi-puissance  $\Delta f$ . La valeur  $Q$  à vide,  $Q_L$ , du résonateur  $TE_{011}$  est donnée par

$$Q_L = \frac{f_0}{\Delta f} \quad (1)$$

- La valeur  $Q$  à vide,  $Q_u$ , doit être extraite de  $Q_L$  selon au moins l'une des deux techniques décrites ci-dessous.

- Une technique d'extraction de la valeur  $Q$  à vide implique de mesurer l'affaiblissement d'insertion  $IA$ .  $Q_u$  est donné par

$$Q_u = \frac{Q_L}{1 - A_t}, A_t = 10^{-IA[\text{dB}]/20} \quad (2)$$

L'affaiblissement d'insertion  $IA$  de chaque température est déterminé comme suit. Dans le système de mesure  $R_s$  représenté à la Figure 2, un câble semi-rigide est connecté en lieu et place de l'appareil de mesure, et le système de mesure est court-circuité afin de déterminer le niveau de référence. Mesurer le niveau de référence à chaque température et l'utiliser pour déterminer  $IA$  à chaque température.

Cette technique d'utilisation de l'affaiblissement d'insertion prend pour hypothèse que le couplage est identique des deux côtés du résonateur. Les boucles de couplage sont difficiles à fabriquer, l'orientation de la boucle est difficile à contrôler et tous les mouvements de la tige de saphir pendant le mesurage ne sont pas connus. Ces effets dépendants de l'assemblage dépendent également de la température. Cette éventuelle asymétrie de couplage peut donner lieu à d'importantes erreurs de calcul du facteur de couplage si le couplage est important ( $IA < \sim 10$  dB). Si le couplage est suffisamment faible ( $IA > 20$  dB), l'asymétrie du couplage devient moins importante.

- 2) Une autre technique d'extraction de la valeur  $Q$  à vide implique de mesurer les facteurs de répartition de la réflexion à la fréquence de résonance des deux côtés du résonateur.

$$Q_u = Q_L (1 + \beta_1 + \beta_2) \quad (3)$$

$$\beta_1 = \frac{1 - |S_{11}|}{|S_{11}| + |S_{22}|} \quad (4)$$

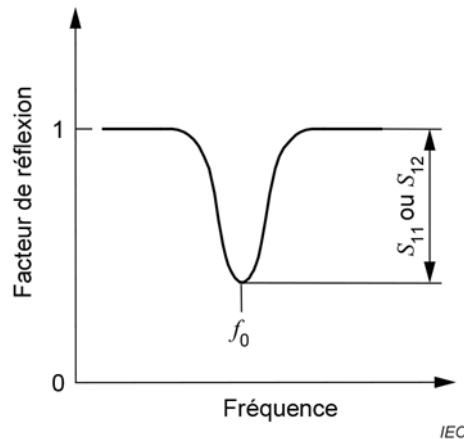
$$\beta_2 = \frac{1 - |S_{22}|}{|S_{11}| + |S_{22}|} \quad (5)$$

Dans les Équations (4) et (5),  $S_{11}$  et  $S_{22}$  sont les facteurs de répartition de la réflexion (voir la Figure 4) et sont mesurés en unités de puissance linéaires, pas en dB relatif.  $\beta_1$  et  $\beta_2$  sont les facteurs de couplage.

Cette technique d'utilisation des facteurs de répartition de la réflexion présente deux avantages. Elle n'exige pas d'étape supplémentaire d'étalonnage du niveau de référence et donne une mesure des valeurs de couplage des deux côtés du résonateur. Cette technique présente également deux inconvénients. Elle ne fonctionne que pour une résonance à bande étroite (ce qui est heureusement le cas) et est limitée par la plage dynamique de l'analyseur de réseau dans le mesurage des facteurs de réflexion [15] [16].

Une combinaison des deux techniques est utile pour «doubler» la vérification.

- f) Les valeurs  $f_0$  et  $Q_u$  mesurées pour cette courte tige sont appelées  $f_{01}$  et  $Q_{u1}$  pour la résonance du mode  $TE_{011}$ . En faisant lentement varier la température du cryoréfrigérateur, la dépendance vis-à-vis de la température de  $f_{01}$  et  $Q_{u1}$  doit être mesurée.
- g) À l'issue du mesurage de la dépendance vis-à-vis de la température de  $f_{01}$  et  $Q_{u1}$ , l'appareil de mesure doit être chauffé jusqu'à la température ambiante.
- h) Ensuite, remplacer le résonateur  $TE_{011}$  dans l'appareil par le résonateur  $TE_{013}$  à température ambiante, refroidir l'appareil à une température inférieure à la température critique, puis mesurer la dépendance vis-à-vis de la température de  $f_0$  et  $Q_u$  de son mode de résonance  $TE_{013}$ , appelés  $f_{03}$  et  $Q_{u3}$ , comme pour le cas du résonateur  $TE_{011}$ . Si la longueur de la tige de saphir du résonateur  $TE_{013}$  est précisément trois fois supérieure à celle du résonateur  $TE_{011}$ , la valeur  $f_{03}$  du résonateur  $TE_{013}$  doit coïncider avec la valeur  $f_{01}$  du résonateur  $TE_{011}$ . S'il est convenablement conçu, la différence entre  $f_{01}$  et  $f_{03}$  est souvent très faible ( $< \sim 0,25$  %). Il peut être considéré que  $f_0$  de l'équation (9) peut être remplacé par  $f_{01}$  ou  $f_{03}$ .

Figure 4 – Facteurs de répartition de la réflexion ( $S_{11}$  et  $S_{22}$ )

### 6.5 Détermination de la résistance de surface du supraconducteur et $\varepsilon'$ et $\tan \delta$ des tiges de saphir normalisées

Calculer la dépendance vis-à-vis de la température de la résistance de surface de  $R_s$  des films supraconducteurs, puis  $\varepsilon'$  et  $\tan \delta$  des tiges de saphir normalisées à l'aide de la dépendance vis-à-vis de la température de  $Q_{u1}$  et  $Q_{u3}$ .  $Q_{u1}$  et  $Q_{u3}$  peuvent être calculés à l'aide des équations (1) et (2). Si les températures mesurées pour  $Q_{u3}$  se révèlent être sensiblement différentes de celles de  $Q_{u1}$ , une interpolation peut être utilisée pour préparer des valeurs de température ajustées pour l'une aux mêmes températures pour l'autre. Les Équations (6) à (12) sont établies dans la cavité de type ouvert, mais si la taille du film supraconducteur est trois fois plus importante que le diamètre de la tige de saphir, ces équations peuvent être utilisées pour une cavité de type fermé.

$$R_s = \frac{30\pi^2 \times 3}{(3-1)} \left( \frac{2h_0}{\lambda_0} \right)^3 \frac{\varepsilon' + W}{1+W} \left( \frac{1}{Q_{u1}} - \frac{1}{Q_{u3}} \right) \quad (6)$$

$$\varepsilon' = \left( \frac{\lambda_0}{\pi d} \right)^2 (u^2 + v^2) + 1 \quad (7)$$

$$\tan \delta = \frac{1 + \frac{W}{\varepsilon'}}{(3-1)} \left( \frac{3}{Q_{u3}} - \frac{1}{Q_{u1}} \right) \quad (8)$$

où

$$\lambda_0 = \frac{c}{f_0} \quad (9)$$

$$W = \frac{J_1^2(u) K_0(v) K_2(v) - K_1^2(v)}{K_1^2(v) J_1^2(u) - J_0(u) J_2(u)} \quad (10)$$

$$v^2 = \left( \frac{\pi d}{\lambda_0} \right)^2 \left[ \left( \frac{3\lambda_0}{2h_0} \right)^2 - 1 \right] \quad (11)$$

$$u \frac{J_0(u)}{J_1(u)} = -v \frac{K_0(v)}{K_1(v)} \quad (12)$$

Dans les équations,  $\lambda_0$  est la longueur d'onde de résonance en espace libre,  $c$  est la vitesse de la lumière dans le vide ( $c = 2,997\,9 \times 10^8$  m/s),  $h_0$  est la hauteur de la courte tige diélectrique normalisée. La valeur  $u^2$  est donnée par l'Équation (12) transcendante utilisant la valeur de  $v^2$ , où  $J_n(u)$  est la fonction de Bessel de premier ordre, et  $K_n(v)$  la fonction de Bessel modifiée de second ordre. Les dérivées des équations sont décrites à l'Article A.3.

En règle générale, le facteur de dilatation thermique des tiges doit être connu pour déterminer la dépendance de leur taille vis-à-vis de la température. Toutefois, les effets de dilatation thermique des tiges de saphir peuvent être négligés pour l'incertitude type relative cible de la résistance de surface  $R_s$  (20 %).

Il est à noter que la résistance de surface  $R_s$  mesurée signifie qu'il s'agit de la résistance de surface efficace si l'épaisseur du film est deux fois inférieure à la profondeur de pénétration en fonction de la température.

## 7 Incertitude de la méthode d'essai

### 7.1 Résistance de surface

La résistance de surface ( $R_s$ ) doit être déterminée à partir de la valeur  $Q$  mesurée par la technique du résonateur diélectrique.

Un analyseur de réseau vectoriel (voir le Tableau 3) doit être utilisé pour enregistrer la dépendance de l'affaiblissement vis-à-vis de la fréquence. L'enregistrement obtenu doit permettre de déterminer  $Q$  selon une incertitude relative de  $10^{-2}$ .

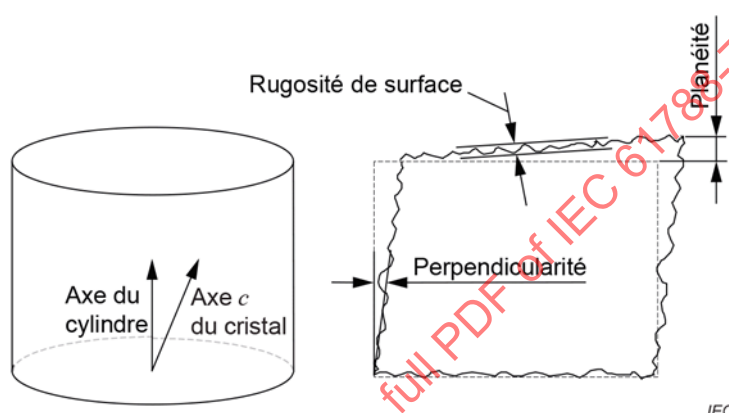
**Tableau 3 – Spécifications pour l'analyseur de réseau vectoriel**

|                                  |                     |
|----------------------------------|---------------------|
| Plage dynamique de $S_{21}$      | supérieure à 60 dB  |
| Résolution de fréquence          | inférieure à 1 Hz   |
| Incertainitude d'affaiblissement | inférieure à 0,1 dB |
| Limitation de puissance d'entrée | inférieure à 10 dBm |

Les résonateurs diélectriques doivent être équipés de deux tiges diélectriques avec un faible  $\tan \delta$  inférieur à  $2 \times 10^{-7}$  à 77 K et un rayon inférieur à 1/3 du rayon de l'éprouvette de supraconducteur. Le saphir est le meilleur candidat pour les tiges (voir le Tableau 4). Les définitions terminologiques du Tableau 4 sont représentées à la Figure 5.

**Tableau 4 – Spécifications pour les tiges de saphir**

|                     |                                                                                                                                          |
|---------------------|------------------------------------------------------------------------------------------------------------------------------------------|
| Diamètre            | $\pm 0,05$ mm                                                                                                                            |
| Hauteur             | $\pm 0,05$ mm                                                                                                                            |
| Planéité            | inférieure à 0,005 mm                                                                                                                    |
| Rugosité de surface | surface supérieure et inférieure: inférieure à 10 nm en valeur efficace<br>surface cylindrique: inférieure à 0,001 mm en valeur efficace |
| Perpendicularité    | dans les limites de 0,1 degré                                                                                                            |
| Axe                 | parallèle à l'axe c à 0,3° près                                                                                                          |

**Figure 5 – Définitions terminologiques du Tableau 4**

La technique décrite prend pour hypothèse qu'une hauteur simple et triple de tiges de saphir peut être fabriquée avec le même  $\tan \delta$ . Toutefois, la variation du  $\tan \delta$  entre des tiges identiques d'un point de vue nominal, découpées dans la même boule et polies selon la même technique, peut être large de deux ordres d'amplitude. À ce jour, la plus faible variation du  $\tan \delta$  entre des tiges de saphir identiques d'un point de vue nominal présente un facteur de quatre. Par conséquent, l'incertitude du  $\tan \delta$  mesuré est importante. La variation du  $\tan \delta$  de la présente tige de saphir est à l'origine d'une incertitude supplémentaire jusqu'à au moins 10 % dans le mesurage de la résistance de surface. Cela limite l'incertitude cible de la présente technique à 5 %. Si la reproductibilité des tiges de saphir est améliorée ou si une méthode de sélection des tiges de saphir normalisées est établie, une incertitude cible peut être améliorée.

## 7.2 Température

L'appareil de mesure est refroidi à la température spécifiée par tous les moyens lors de l'essai. Un choix pertinent consisterait à plonger l'appareil dans un cryogène liquide. Cette technique est rapide et simple, et permet d'obtenir une température connue et stable. Malheureusement, la plupart des matériaux HTS sont endommagés par la condensation de l'humidité qui se produit lorsque l'échantillon est retiré du cryogène. De plus, les incertitudes générées par la présence d'un mélange de gaz et de liquide à l'intérieur de la cavité, et l'incapacité à mesurer  $R_s$  en fonction de la température plaident en faveur d'autres méthodes de refroidissement. Ces limitations peuvent être contournées par l'immersion d'un caisson à vide dans le cryogène liquide. Si le caisson à vide peut être rempli avec du gaz, un refroidissement rapide et des températures uniformes sont obtenus. Si des éléments chauffants sont associés à l'appareil, la dépendance du matériau HTS vis-à-vis de la température peut être mesurée. Un troisième choix, très bon également, consiste à utiliser un cryoréfrigérateur. Dans ce cas, le résonateur est placé sous vide et refroidi par conduction à l'aide d'un boîtier métallique. Les gradients de température avec l'appareil doivent être évités.

Un cryostat doit être prévu avec l'environnement nécessaire à la mesure de  $R_s$ , et l'éprouvette doit être mesurée à l'état stable et isotherme. Par hypothèse, la température de l'éprouvette est identique à la température du porte-éprouvette. La température du porte-éprouvette doit être consignée à  $\pm 0,5$  K, mesurée au moyen d'un capteur de température approprié.

La différence entre la température de l'éprouvette et la température du porte-éprouvette doit être réduite le plus possible à l'aide de blindages présentant une bonne conductivité thermique.

### 7.3 Structure de l'éprouvette et du support

La structure du support doit assurer un maintien adapté de l'éprouvette. Les deux films doivent être parallèles et doivent présenter une stabilité mécanique tout au long du mesurage, plus particulièrement dans un cryoréfrigérateur et sur une plage de températures étendue. Le parallélisme des deux films peut être obtenu à l'aide d'une tige de saphir satisfaisant aux spécifications décrites dans le Tableau 4.

### 7.4 Protection de l'éprouvette

La condensation de l'humidité et les rayures du film détériorent les propriétés de supraconduction. Il convient de prévoir des mesures de protection pour les éprouvettes. Les revêtements en polytétrafluoroéthylène (PTFE) ou en polyméthylméthacrylate (PMMA) n'ont aucun impact sur les mesurages, et peuvent donc être utilisés pour la protection. Une épaisseur de matériau de revêtement inférieure à quelques micromètres est recommandée.

### 7.5 Incertitude de la résistance de surface mesurée par la méthode normalisée à deux résonateurs

Pour la méthode de résonance diélectrique, le  $\tan \delta$  des tiges de saphir du mode  $TE_{011}$  et celui du mode  $TE_{013}$  sont par hypothèse absolument égaux. Si le  $\tan \delta$  des deux tiges de saphir est différent, la résistance de surface ne peut pas être calculée à l'aide de l'Équation (6). Les effets d'un écart de  $\tan \delta$  sur la résistance de surface ont été vérifiés (voir l'Annexe B). L'incertitude de la résistance de surface hyperfréquences des supraconducteurs par la méthode du résonateur diélectrique dépend de la taille, de la constante diélectrique, du  $\tan \delta$  des tiges de saphir et de l'incertitude du  $Q$  mesuré du résonateur. L'incertitude type composée relative est inférieure à 20 % (voir l'Annexe B).

## 8 Rapport d'essai

### 8.1 Identification de l'éprouvette d'essai

L'éprouvette d'essai doit être identifiée, si possible, par les éléments suivants:

- a) nom du fabricant de l'éprouvette;
- b) classification et/ou symbole;
- c) numéro de lot;
- d) composition chimique du film fin et du substrat;
- e) épaisseur et rugosité du film fin;
- f) technique du processus de fabrication.

### 8.2 Consignation des valeurs $R_s$

Les valeurs  $R_s$  à la fréquence mesurée et celles échelonnées à 10 GHz, accompagnées de leurs valeurs  $f_{01}, f_{03}, Q_{u1}, Q_{u3}, IA$  et/ou  $(\beta_1, \beta_2), \epsilon'$  et  $\tan \delta$  correspondantes, et leur dépendance vis-à-vis de la température doivent être consignées.